Long-standing endeavors to synthesize wafer-scale single-crystal diamond have recently resulted in the successful demonstration of a disc with a diameter of about 3.5 inch and a total weight of 155 carat, created by heteroepitaxial nucleation and growth on Ir [YSZ/Si(001)] [1]. Parallel activities on (111)-oriented substrates have revealed that similar improvements in structural quality can be obtained by growth of thick samples also for this crystal direction (so far, on small areas only) [2]. In this presentation, we will discuss the fundamental ingredients for heteroepitaxial diamond nucleation on Ir surfaces and our current understanding of the underlying atomic processes will be briefly reviewed. Next, the structural improvement, i.e. the reduction in mosaic spread, dislocation density and Raman line width will be described, comparing directly the results obtained for (001)- and (111)-oriented growth. In both cases, the strategy of growing thick layers will reach its limits, which we currently estimate to be around 100 - 1000 nm [2]. To further improve the structural quality, modified concepts have to be explored. In the second part of the presentation, the influence of dislocations on material properties relevant for the performance of potential devices, and the perspectives of heteroepitaxial diamond for different applications, will be discussed. [1] M. Schreck, S. Gsell, R. Brescia, M. Fischer, Sci. Rep. 7, 44462 (2017). [2] B.-C. Gallheber et al.

9:15 AM *P1.02 Nanoscale Quantum Sensing Jörg Wrachtrup; Institute for Quantum Science and Technology, University of Stuttgart, Stuttgart, Germany.

The accuracy of measurements is limited by quantum mechanics. Ingenious demonstrations, like measuring gravitational fields or time have explored accuracy limits and reached fundamental obstructions. Yet, precision measurements so far are restricted to macroscale and dedicated environments. In the talk I will discuss spin quantum sensors comprising a single electron spin or multiple electron spins in either bulk or nanocrystalline diamond. With such a system we measure a variety of quantities including electric and magnetic fields, temperature, and force. We use advanced quantum control as well as signal analysis techniques to enhance our measurement accuracy [1-3]. I will present a variety of applications ranging from quantum simulators to imaging of cellular processes. [1] M. Schreck, S. Gsell, R. Brescia, M. Fischer, Sci. Rep. 7, 44462 (2017). [2] B.-C. Gallheber et al.
The negatively charged silicon-vacancy center (SiV) in diamond is a potential high-quality single-photon source of indistinguishable photons for quantum information processing and quantum electrodynamics (QED) applications. In contrast to the more common nitrogen-vacancy (NV) center in diamond, the SiV possesses bright narrow-band and spectrally stable optical transition concentrated (70% of the fluorescence) in its zero phonon line (ZPL) protected by inversion symmetry, even at room temperature. However, when embedded in bulk diamond, this photon source suffers from both, relatively low extraction efficiency attributed to total internal reflection as well as nondeterministic emitter location. On the other hand, the use of nanodiamonds or nanostructures prepared by a top-down approach can mitigate the issue of total internal reflection within the diamond, but inherently at the same time introduces additional decoherence mechanisms attributed to poor surface quality. Here we present and implement a robust and deterministic template-assisted bottom-up process for the creation of arrays of high quality nanoscale diamond pyramids (30 nm top diameter) incorporating SiVs. This method employs a predefinition of high-precision nanosized pillars by e-beam lithography and dry etching, and subsequent epitaxial diamond overgrowth by hot filament chemical vapor deposition (HFCVD) during which Si atoms are introduced into diamond. The overgrown layer that forms the diamond pyramid structures is epitaxial as confirmed by X-ray diffraction (XRD), transmission electron microscopy (TEM) and electron backscatter diffraction (EBSD) measurements. We carried out optical confocal scans for collecting the room temperature photoluminescence (PL) from the nano-pyramid array, filtered at the SiV ZPL (738 nm). A clear signature of the SiVs, can pave the way towards efficient single-photon source arrays.

The results show that diamond plasmonic devices are a viable contender for THz communication for Beyond 5G WI FI applications. This provides a strong motivation for analyzing the potential performance of the diamond plasmonic FET THz and far IR detectors. The potential performance of the diamond THz plasmonic device is determined by the transistor I-V characteristics. To this end, we measured and evaluated the diamond FET current-voltage characteristics using the Unified Charge Control Model (UCCM). The Ohmic contacts were fabricated on single crystal diamond substrates with 100 orientation. The substrates were provided by Element 6. After appropriate surface preparation, the contact area was hydrogenated, and Au contact metal was deposited. The extracted mobility of the 2DHG in the sub-surface channel is 34 cm²/Vs and the sheet carrier density is 3.4x10¹⁵ cm⁻² corresponding to the sheet resistance of 5.74 kΩ. The TLM measurements yielded ohmic contact resistance of 0.5 Ωmm. At such sheet resistance, the channel of 170 nm has the resistance equal to the contact resistance, which could be further reduced using the perforated gate structure. A relatively small contact resistance makes plasmonic operation realistic providing further motivation of our study. We evaluated the expected response to THz and sub-THz radiation for the values of the momentum relaxation time ranging from 0.01 to 6 ps for the gate lengths of 20 nm, 60 nm, and 100 nm. This was done using the compact analytical model (suitable for the device design and parameter extraction) and using a numerical solution of the hydrodynamic equations describing 2DHG. The computer simulations are in excellent agreement with the analytical model and show a small effect of the hole viscosity (in contrast to more conventional semiconductors used for THz applications, such as InGaAs). The results show that the plasma velocity is relatively small because the hole effective mass is large (as low as 10⁻³ m/s). This value is smaller than the hole saturation velocity in diamond, which is high because of the high optical phonon energy in diamond. This makes it possible to achieve the so-called “plasmonic boom” instability in the two-dimensional hole gas (2DHG) in p-diamond (this instability requires the drift velocity values to exceed the plasma velocity). The predicted performance of diamond plasmonic detectors shows that these devices are a viable contender for applications in including the 200 to 300 GHz and 600 GHz atmospheric windows that are of the special interest for the Beyond 5G WIFI THz communications. New design and approaches based on the diamond transistor physics are required to achieve the transistor performance with high hole field effect mobility and for minimizing the effect of parasitics, approaches such as the perforated channel, plasmonic crystal, and plasmonic ratchet designs.
analyses reveal that the carboxylated groups render the UDD more antibacterial properties, better than those of pristine UDD. The statistical MF method. The results indicate that the functionalized UDD has strong diffraction (XRD). Bacterial characterization was done using Coliscan infrared spectroscopy (FTIR) to confirm the functional groups and X-ray strong oxidation and amine addition. The samples were characterized with thereby enhancing the UDD efficiency as a water disinfection agent.

Coating the surfaces of inorganic nanoparticles with functional linker molecules is an important step in the development of many nanoparticle-based drug delivery systems. The efficiency with which drug molecules can be loaded on to nanoparticle surfaces is contingent on the concentration, distribution and stability of these coatings. For example, functionalization of nanodiamond with carboxyl is the first step in loading these materials with therapeutic agents, and the conjugation with proteins, cytochrome, antigen and DNA. Further, functionalisation with polyethylene glycol (PEG), a process known as PEGylation, has already been shown to facilitate greater control over the loading and stability of doxorubicin (DOX) for selective therapies while retaining the pH-sensitivity that is important for drug release. In this study results of high-throughput electronic structure computer simulations are used to map the distribution of COOH and PEG across the entire surface of a reconstructed nanodiamond, with atomic level resolution. This provides useful insights into how the structure of the host nanodiamond impacts the formation of COOH and PEG surface monolayers, and suggests suitable pre-treatments that increase coverage, homogeneity, and binding probabilities with respect to adventitious, non-functional adsortbates that impact performance.

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II:30 AM K1.02 Functionalized Nanodiamond for Water Disinfection Axel R. Arroyo1, Gerardo Morell1, Abelardo Colón2, Brad Weiner1 and Javier Avalos1; 1Chemistry, University of Puerto Rico Rio Piedras Campus, Toa Baja, Puerto Rico, United States; 2Physics, University of Puerto Rico Rio Piedras Campus, San Juan, Puerto Rico, United States; 3Environmental Sciences, University of Puerto Rico Rio Piedras San Juan, Puerto Rico, United States; 4Physics, University of Puerto Rico Bayamon Campus, Bayamón, Puerto Rico, United States.

Detonation nanodiamond or ultra-disperse diamond (UDD) can be used as an alternative and sustainable nontoxic new disinfection material for water treatment plants, due to its biocompatibility, inertness and antibacterial properties. In this research, we performed UDD surface modification to improve the UDD antibacterial properties against coliforms and fecal Escherichia Coli, by adding functional groups such as carboxylic acid (-COOH) and amines (-NH3), which will promote a better interaction between the material and the bacterial membrane, thereby enhancing the UDD efficiency as a water disinfection agent. UDD was successfully functionalized with -COOH and -NH3 groups by strong oxidation and amine addition. The samples were characterized with infrared spectroscopy (FTIR) to confirm the functional groups and X-ray diffraction (XRD). Bacterial characterization was done using Colisan MF method. The results indicate that the functionalized UDD has strong antibacterial properties, better than those of pristine UDD. The statistical analyses reveal that the carboxylated groups render the UDD more effective against coliforms in water than the aminated groups.

Field emitters with superior flat field electron emission (FEE) characteristics are employed as a cold cathode materials in flat panel displays and other electron emitting devices. Diamond possesses high FEE characteristics due to its negative electron affinity (NEA), which makes it a promising material for application as FEE emitters. But owing to the wide bandgap nature of diamond, the electrical conductivity in bulk diamond is low, which decreases its electron emission. Therefore, the material needs to be made conductive. Recently, the main focus in this respect has been directed towards the synthesis of ultrananocrystalline diamond (UNCD) films containing ultra-small diamond grains of 5–10 nm with smooth surface characteristics. Such films exhibit higher electrical conductivity and better FEE properties than any other known form of diamond films, which is believed to be due to the sp3-bonded carbon in the grain boundaries as acting as electron conduction channels [1]. Hence, direct detection of electron emission sites from diamond grains or grain boundaries on a microscopic scale is crucial to fully understand the underlying emission mechanisms and remaining related questions [2]. In this work, scanning tunneling microscopy (STM) is being utilized to investigate the local FEE behavior and surface electronic properties of diamond films [3]. It allows direct imaging of the emission, leading to understanding of the mechanism behind the enhanced conductivity and FEE properties for Au-ion implanted UNCD films. Such films, implanted with 1 × 1017 Au ions/cm2 possess a high electrical conductivity of ~ 5 kS/cm and a low turn-on field of 1.6 V/μm, yielding a high FEE current density of 5.4 mA/cm2 (@ 2.65 V/μm), and high lifetime stability of 1825 min. Straight imaging of conducting/non-conducting sites is mapped by STM. The local current-voltage measurements illustrate that grain boundaries are indeed the conducting/emitting sites. Further, this fact is supported by the high resolution current imaging tunneling spectroscopy. The formation of abundant conducting sp3 nanographic phases along the diamond grain boundaries, confirmed from transmission electron microscopic examinations, is believed to be the genuine factor that helps for the easy transport of electrons and hence enhances the conductivity/emission properties. The fabrication of these films with high conductivity and superior FEE properties is a direct and simple approach which opens up new prospects in flat panel displays and high brightness electron sources.K. J. Sankaran is a Postdoctoral Fellow of the Research Foundation-Flanders (FWO). References [1] O. Chubenko, et al., ACS Appl. Mater. Interfaces 9 (2017), 33229. [2] R.L. Harniman, et al., Carbon 94 (2015), 386. [3] K. Panda, et al., Carbon. 111 (2017), 8.

Diamond is a fascinating semiconductor with exceptional physical properties such as a wide band gap, a high breakdown electric field (10 MV/cm), an outstanding thermal conductivity (20 W/cmK) and high carrier mobilities. These exceptional properties, or more precisely, the combination of some of these properties makes diamond an ideal semiconductor for high power and/or high frequency electronics which should surpass other materials like silicon, silicon carbide or gallium nitride. Numerous diamond field effect transistors are under investigation:
H-terminated accumulation FET, O-terminated inversion channel FET, metal-semiconductor FET and junction FET.

In this work, we propose a new transistor concept in order to exploit the full potentialities of diamond material. First, a stable deep depletion regime will be demonstrated in metal oxide semiconductor capacitors using p-type oxygen-terminated (100) diamond as a semiconductor and Al2O3 deposited by atomic layer deposition at 380°C. Current voltage I(V) and capacitance voltage C(V) measurements were performed to evaluate the effectiveness of diamond semiconductor heterointerface. An effective modulation of the space charge region width is obtained by the gate bias, where the deep depletion regime is demonstrated for a positive gate bias. The deep depletion concept will be described and proposed for MOSFET devices. A proof of concept of deep depletion diamond MOSFETs will be presented. Finally, the recent improvements achieved at Institut Néel in terms of device performances will be discussed. References 1 T.T. Pham, N. Rouger, C. Masante, G. Chicot, F. Udrea, D. Eon, E. Gheeraert, and J. Pernot, Appl. Phys. Lett. 111, 173503 (2017). 2 T.T. Pham, A. Maréchal, P. Muret, D. Eon, E. Gheeraert, N. Rouger, and J. Pernot, J. Appl. Phys. 123, 161523 (2017). 3 T.T. Pham, J. Pernot, G. Perez, D. Eon, E. Gheeraert, and N. Rouger, IEEE Electron Device Lett. 38, 1571 (2017).

2:00 PM B1.02 Diamond RF Electronics Technology Development at the US Army Research Laboratory Pankaj B. Shah, James Weil, Mahesh R. Neupane, Kevin G. Crawford, A. G. Birdwell, Frank J. Crowne and Tony G. Ivanov; US Army Research Laboratory, Adelphi, Maryland, United States.

Due to the thermal limits of GaN and other prospective ultra-wide bandgap semiconductor materials, the US Army considers diamond, with its high thermal conductivity and large energy bandgap, as a potential next generation semiconductor electronic material. As a result, the Army Research Laboratory has an in-house program to develop Radio-frequency (RF) field-effect transistors (FETs) on hydrogen-terminated diamond surfaces. These devices are fabricated on single-crystal diamond substrates, and employ both atmospheric adsorbates and MoO3, as the transfer-doping electron acceptor layer leading to a free-hole current channel. Our presentation will discuss device fabrication together with the DC and RF characterization results for FETs fabricated with gate lengths ranging from 4μm to sub-100nm. Starting materials are plasma hydrogenated to achieve a negative electron affinity surface. Following this procedure, a standard four mask fabrication process is used with the last mask being utilized for electron-beam writing of the gate finger. These masks are 1) Ohmic contact / device isolation, 2) Ohmic contact anchor between oxide and hydrogenated regions, 3) source-drain separation / Schottky contact metal and 4) plating-up probe regions. Ohmic contacts adhesion to the hydrogenated surface is improved by deposited metal anchor layers that are held in place via the increased adherence to oxygen terminated diamond. Contact resistance, sheet resistance and mobility data are collected and correlated with device results. A highlight of the atmospheric transfer-doped RF FET performance comes from the devices fabricated at f = 100nm. These devices resulted in DC drain current densities I DS = 600 μA/mm, transconductance g m = 140 mS/mm, current gain cutoff frequency f T = 4GHz, and power gain cutoff frequency of f P = 44GHz. This demonstrated technology compares favorably with reported state-of-the-art results, in terms of DC and small signal performance. 1,2 Capacitance-voltage measured charge carrier concentration peaked at 1.3x1019 cm-3 for a 1μm gate length FET compared to 7.5x1019 cm-3 for a 2μm gate length FET. Sheet resistance below 5 kΩ/sq are typically seen for the hole conducting channel. To better understand device performance and improve chances for accurately predicting potential for transfer-doped diamond FET devices, we performed both drift-diffusion device and atomistic materials and electronic structure simulations. Drift-diffusion simulation of the FETs indicate that precise modeling of the acceptor states, including energy band offsets, correlates well with device performance. 3 Also, our modeling results indicate that dopants preserved under the gate lead to higher on-currents. An atomistic first principle simulation is used to identify stable diamond surface configurations with and without hydrogenation. Furthermore, using the identified stable configuration, the effect of hydrogen surface coverage on device parameters such as mobility, electron affinity and work-function were determined. Exploring the hydrogenation process by means of this atomistic model may assist experimental efforts focused on the preservation of the hydrogen termination layer, and hence to long-term robust device operation. 1 F. Maier, M. Riedel, B. Mantel, J. Ristein, and L. Ley, “Origin of Surface Conductivity in Diamond”, Phys. Rev. Lett., 85, 3472 (2000). 2 D. A. J. Moran, S. A. O. Russell, S. Shabbir, and A. Tallaire, “High Frequency Hydrogen-terminated Diamond Field Effect Transistor”, 12th IEEE International Conference on Nanotechnology, Birmingham, UK (2012). 3 H. Kawarada, H. Tsuboi, T. Naruo, T. Yamada, D. Xu, A. Daicho, T. Saito, and A. Hiraishi, “C-H Surface Diamond Field Effect Transistors for High Temperature (400°C) and High Voltage (500V) Operation”, Appl. Phys. Lett. 105, 013150 (2014). 4 P.B. Shah, J. Weil, A.G. Birdwell, and T. Ivanov, “Charge Trapping Analysis of High Speed Diamond FETs”, MRS Advances, DOI: 10.1557/adv.2017.141 (2017).

2:15 PM B1.03 Band Alignment of Al2O3/SO2/H-Diamond Heterointerfaces Using Synchrotron X-Ray Photoelectron Spectroscopy (XPS)/XANES Measurements Niloy C. Saha1, Kazutoshi Takahashi2, Masaki Imamura1 and Makoto Kasu3; 1 ‘Electrical and Electronic Engineering, Saga University, Saga, Japan; 2 Synchrotron Light Application Center, Saga University, Saga, Japan.

Diamond possesses the highest band-gap and high breakdown electric field among semiconductor materials. Therefore, diamond is preferred for high-power and high-temperature operations due to its excellent physical properties. We have developing diamond FET using NO2 hole doping. Thus, O2, NO2, SO2 and NO adsorption generate holes carriers. This mechanism was explained by the first principle calculation that the unoccupied orbitals of inorganic gas molecules attract the electron of H-diamond and induced holes on the surface, thus increasing the sheet concentration. 1 The Al2O3/NO2/H-diamond heterointerface was studied previously and found that type II band-alignment, where the valence band offset was 3.9 eV.2 Band offset of the Al2O3/H-diamond interface is influenced by the exposed NO2 gas molecules and a high band offsets were observed than those of H-diamond without any exposure. In this study, we determine energy band alignment using synchrotron X-ray photoelectron spectroscopy (XPS) and X-ray absorption near edge structure (XANES), and investigate the interface states of Al2O3/SO2/H-diamond heterointerface. We used 1-μm-thick (001) H-diamond homoepitaxial layer. H-diamond sample was exposed to the SO2 gas for 10 mins. Finally, a 4-mm-thick Al2O3 layer was deposited as oxide layer to fabricate the Al2O3/SO2/H-diamond structure. All the measurements were performed at Saga Synchrotron Light Source (SAGA-LS), while Al2O3 layer was thinning by Ne+ ion beam sputtering. The ratio of C 1s/ O 1s was used to determine the thickness of the Al2O3 layer. C 1s, Al 2p and Al 2p spectra were taken with the photon energy of 700 eV using XPS measurements. The respective peak of the measured spectrum was fitted by the least-square-fitting technique using a Shirley background and Voigt line shape. In this case, O 1s spectra were decomposed into two peaks and C 1s spectra were decomposed into 4 peaks. In addition, photoemission spectra were taken in the binding energy ranges from 155 to 180 eV in order to detect S 2p peak as the H-diamond was exposed to SO2. However, no peak of S 2p was found. The O 1s peak at higher binding energy and absence of S 2p at the interface indicate that SO2 gas molecules are decomposed and oxygen adsorbates chemically bonded to H-diamond surface. Measurement of X-ray absorption near edge structure (XANES) spectra at O K-edge and Al L-edge were performed to investigate interfacial states. Energy band alignment was determined from the energy positions of the core-level spectra of C 1s and Al 2p, and valence band maximum (VBM) value of the diamond and Al2O3 layer. VBM of Al2O3 layer was determined as 3.5 ± 0.1 eV. A type II band (staggered type) alignment is determined from measured values, where a valence band offset of 3.5 ± 0.1 eV and a conduction band offset of 2.3 ± 0.1 eV were found. The valence band offsets are lower than those of NO2-exposed diamond interface. However, a good agreement of accumulation hole carriers due to SO2 exposure is demonstrated from the band-offset of the Al2O3/SO2/H-diamond heterointerface. References 1 M. Kubovic and M. Kasu, Jpn. J. Appl. Phys. 49 (2010), 110208. 2 Y. Takagi, K. Shiraiishi, M. Kasu, and H. Sato, Surf. Sci. 609 (2013), 203. 3 K. Takahashi, M. Imamura, K. Hirama, and M. Kasu, Appl. Phys. Lett. 104 (2014), 072101.
2:30 PM B1.04
Hydrogen-Terminated Diamond Field-Effect Transistor with Double Dielectric Layers of HfSiO4/Al2O3. Yan-Feng Wang, Xiaohui Chang, Wei Wang, Dan Zhao, Jiu Fu, Zongchen Liu, Guoqing Shao, Zhangcheng Liu, Shuwei Fan, Renan Bu, Jingwen Zhang and Hongxing Wang; Xi’an Jiaotong University, Xi’an, China.

Diamond film collects all the outstanding properties of mechanics, electronics, heat, and optics etc. together making it have potential applications in the fields of wide range optical transparent window material, super-hard coating tools, especially, in the field of high power electron devices which can work with high frequency and in high temperature environment. Recently, researchers have extensively investigated hydrogen-terminated diamond (H-diamond) field effect transistors (FETs). H-diamond surface can form a p-type conduction channel with a sheet hole density and hole mobility of 10¹⁰ cm⁻² and 10⁻⁵ cm²V⁻¹s⁻¹ respectively. However, this conduction layer is thermally and chemically instable and vulnerable to the ambient environment such as oxidation of diamond surface or higher annealing even in vacuum. All these would cause the missing of p-type conduction layer and the degradation of FET performance. This problem could be solved by fabricating dielectric layers on diamond surface to maintain the p-type conduction channel, which also acts as a insulators. Various dielectric layers have been used such as SiO2, Al2O3, HfO2, Ta2O5 and ZrO2 on H-diamond surface. However, there are few reports on using dielectric of HfSiO3, which has excellent thermal stability, adequate band gaps from 15 to 25 depending on hafnium content. In this work, investigation of H-diamond FETs with ALD-Al2O3/ SD-HfSiO3 dielectric layers have been carried out. Firstly, gold electrodes were patterned on H-diamond by electron beam evaporation technique. Secondly, UV-ozone was used to insulate p-type conduction channels between source and drain electrodes. The length of channels were 20um. Then, 4nm ALD-Al2O3/ 30nm SD-HfSiO3 dielectric layers were fabricated on p-type conduction channels by ALD and SD technique. Finally, electrical properties of this diamond FETs were investigated. The detail will be presented in the conference. 1H. Kawarada, H. Tsuboi, T. Naruo, T. Xu, A. Daicho, T. Saito, and A. Hiraiwa, C-H surface diamond field effect transistors for high temperature and high voltage operation, Applied Physics Letters, 105 (2014) 013510. 2Akira Daicho, Tatsuya Saito, Shinichiro Kurihara, Atsushi Hiraiwa, and Hiroshi Kawarada, High-reliability passivation of hydrogen-terminated diamond surface by atomic layer deposition of Al2O3. J. Appl. Phys. 115 (2014) 223711.

3:00 PM BREAK

G1: Graphene and 2-D Materials I
Session Chair: Chia-Liang Cheng
Monday Afternoon, May 21, 2018
Room: Agassiz/Fremont

* Invited Paper

1:30 PM G1.01
Advances in Ultra-Low Energy Ion Implantation of Graphene and Other Low Dimensional Materials Hans Hofmann and Manuel Auge; Faculty of Physics, 2nd Institute of Physics, Göttingen, Germany.

Doping of 2D materials by ion implantation has unique requirements regarding ion energy, ion energy spread, ion beam optics, sample preparation and sample electrical conductivity. Efficient substitutional incorporation of low energy ions into the graphene lattice requires energies well below 50 eV. We use a low energy mass selected ion beam system with a UHV implantation chamber. A 30 keV mass selected ion beam is guided through differential pumping stages and homogenized using a beam sweep. The beam is then decelerated in a UHV-chamber down to energies of as low as 10 eV. With the help of focusing/defocusing lenses an area of several mm² up to about 2.5 cm² can be uniformly irradiated with these ultra-low-energy (ULE) ions with beam current up to several µA. Up to now ion sources are available as isotopically pure beams of B⁺, C⁺, F⁺, and P⁺, S⁺, Se⁺, W⁺ and Au⁺. Ion sources for elements like Al, Fe, As and rare earth elements are under development. The implanted areal concentration and elemental composition can be verified with in-situ Auger spectroscopy and more quantitative with Rutherford backscattering by implanting into amorphous carbon films as test samples. The detection limit is below 10¹⁰ ions/cm² for heavier elements. Implantation of agraphene on the ¹¹B(p,2α)α nuclear reaction with a detection limit of about 1x10¹⁰ B/cm². Challenges for ULE ion implantation such as non-flat substrates, charging of substrates, cleaning of surfaces and lateral controlled implantation will be briefly discussed. Examples for doping of monolayer graphene with ¹¹B⁺, ¹³C⁺ and P⁺ ions and doping of 2D MoS₂ with Se⁺ ions will be presented.

1:45 PM G1.02
DISCUSSION TIME

2:00 PM *G1.03
Unique Aspects of Charge Transfer in Graphene and Their Applications Mario Hofmann¹, Ya-Ping Hsieh² and Kevin Chang³; ¹Department of Physics, National Taiwan University, Taipei, Taiwan; ²Institute of Atomic and Molecular Sciences, Academia Sinica, Taipei, Taiwan; ³Department of Materials, National Cheng Kung University, Tainan, Taiwan.

Graphene has shown superior performance to bulk materials in many areas ranging from sensing to RF amplification. However, the two-dimensional nature of graphene is often neglected in approaches to employ it as a replacement for traditional engineering materials. We here report several unique aspects of carrier transport in graphene under extrinsic doping and the promising applications they enable. Since graphene’s carriers are confined to the surface, we observe that the morphology of dopants significantly affects carrier transport. Employing in-situ characterization
tools we identify distinct scattering mechanisms at low and high dopant coverage regimes. At low dopant coverage we observe a low charge transfer efficiency between dopant and graphene that is 5% of the values expected from energy considerations. This discrepancy originates from the limiting geometrical capacitance of small adsorbate clusters. An increase of the cluster size was found to increase the charge transfer efficiency to 70% and lower the sheet resistance to 1060 Ohm/sq at 97% transmittance which represents highest reported performance for doped single layer graphene and is on par with commercially available transparent conductors. Unfortunately, the achievable enhancement in performance upon increase of dopant coverage is limited by a competing effect of charge carrier scattering. We observe a capacitive coupling between doped and undoped regions of graphene that suppress ambipolar transport and result in a persistent p-type transfer characteristic. This effect is dominating the carrier scattering and can result in a six-fold decrease in mobility. When dopant clusters reach dimensions where they start merging, charge transport proceeds through percolation in the pristine graphene phase. This transition results in an increase in sheet resistance and a surprising behavior of the Hall effect that had been previously misinterpreted as change in doping type and mobility enhancement. The efficient charge transfer to graphene was demonstrated to enable several novel applications. Electrostatic control over graphene’s carrier concentration allowed change of the band alignment in graphene/insulator/semiconductor heterojunctions. Thus, vertical tunneling-injection light-emitting transistors (VtiLET) were produced where gating allows adjustment of the light emission process. This advance enabled arbitrary color light emission from one single emitter. Moreover, we show that the electrochemical properties of graphene are intimately linked to the position of its Fermi level. Thus, an electrochemical transistor was realized that permits the dynamic modification of the potential and reaction rate of an electrochemical reaction over a wide range.

2:30 PM G1.04

Newly Laser-Assisted Multilayer Graphene Patterning and Its Capabilities in Biosensors and Optoelectronics

Ievgenia Kovalska1, Pauline Lesongeur2, Petro Deminskyi2, Coskun Kocabas3 and Anna Baldycheva1; 1College of Engineering, Mathematics, and Physical Sciences, University of Exeter, Exeter, United Kingdom; 2Bilkent University, Ankara, Turkey; 3The University of Manchester, Manchester, United Kingdom.

An appropriate candidate in sensing systems (as an electrode) is graphene or other 2D materials. The large surface area and superior electrical conductivity of graphene make it an excellent ‘electron wire’ between the redox centers of an interested molecule and the electrode’s surface. Owing to the extraordinary electronic transport property and high electrocatalytic activity of graphene, the electrochemical reactions of analytes are greatly promoted on the graphene film, resulting in an enhanced voltammetric response. Graphene is now a more mature technology; it can be produced in a cost-effective way, in large scale and in a short time, it shows good biocompatibility, and the source material is abundant and inexpensive. Graphene is extremely stable to the environmental conditions and does not degrade with time, which makes it an ideal material for stable sensor performance. It also has a range of surface chemistry which can be used to modify the graphene surface and make it amenable to detecting different (bio)markers. Thus, graphene is a promising candidate for advanced electrode materials which has found its way into a wide variety of sensing schemes. Herein we report new laser-assisted patterning of graphene films which can selectively enhance certain sensory and (opto)electronic capabilities of graphene-based devices and can offer its progress of the next generation for energy storage, photonics, and bioelectronics. Basically, device’s advanced multifunctionality (sensitivity, selectivity, reactivity) is driven by exerting the periodicity and forming active centers on the surface of graphene electrodes. Therefore, we represent the new approach of multilayer graphene (MLG) patterning employing nonlinear laser lithography (NLL) which is contamination-free, rapid and low-cost pattern replication technique. Via patterning, we demonstrate tuning of chemical and electro-optical properties of MLG due to laser power adjustment (310 – 380 mW). We control the hydrophobic/hydrophilic properties which define multifunctionality of graphene-enabled devices due to the graphene surface (dis)organizing, and consequently, a formation of reactive oxygen-based functional groups. Distinct graphene structure alignment (which prevents defects appearance) assisting by strongest laser power (380 mW) contributes to patterned MLG electro-optical changes (sheet resistance decreasing and optical transmittance enhancement) as well. In conclusion, we discuss the great promise of fabricated devices with sensor, supercapacitor and battery designs by using as an electrically reconfigurable medium NLL-assisted graphene patterning. The patterned MLG-based sensor demonstrates high sensitivity to exalming molecules of humans that would be helpful for an early stage disease detection. The patterned MLG-based supercapacitor testing results reveal two times transmittance value rising (in comparison with MLG-based supercapacitor) caused by light interaction with patterned structures where its thickness is reduced. Meanwhile, the patterned MLG-based battery indicates long-life viability (500 charging/discharging cycles) with 0.01% capacity-loss per cycle. We anticipate a proposed NLL-assisted approach for MLG patterning demonstrates a new avenue to advance graphene for multifunctional device engineering particularly in energy storage, wearable electronics, and biosensors.

2:45 PM G1.05

Twisted Bilayer Graphene Based ECG Sensor

Angela Luis Matos1, Samuel Escobar Veras1, Ruth Adames Méndez1, Tej B. Limbu1, Frank Mendoza1, Brad Weiner2 and Gerardo Morell3; 1Physics, University of Puerto Rico Rio Piedras, San Juan, Puerto Rico, United States; 2Chemistry, University of Puerto Rico Rio Piedras, San Juan, Puerto Rico, United States; 3Interdisciplinary, University of Puerto Rico Rio Piedras, San Juan, Puerto Rico, United States.

Physiological recordings have been one of the most significant tools for today’s diagnosis technologies, allowing for non-invasive techniques that deliver useful insights in patient care. Electrocardiogram (ECG) recordings stand among the most important of the diagnosis tools, since according to the Department of Health statistics, for more than a decade heart related diseases have proven to be more lethal than cancer. Nonetheless, ECG recordings electrodes suffer from material degradation which results in high impedance values that limit the usability of the technique for an accurate diagnosis. In order to fix this problem new electrodes must be proposed with low impedance and high chemical stability, properties that graphene has been known for. Therefore, hereby we report results on the implementation of large area bilayer graphene as a long term low impedance electrode for ECG applications. The large area bilayer graphene has been synthesized using the hot filament chemical vapor deposition (HF-CVD) technique on copper substrates. The synthesized material was later transfer to a more suitable substrate for physiological recordings experiments. Raman spectroscopy, alongside sheet resistance measurements, ensures the high quality of our material, before and after the transfer process. Electrical measurements have been taken to determine the material impedance dependence on frequency, in the interface skin/gel/electrode. Results suggest that graphene offers a practical solution to extend the life cycle of an ECG electrode when interfacing with human skin. Thus, securing long term low impedance reliable recordings.

3:00 PM BREAK

C1: Diamond Photonics/Spintronics I

Session Chair: To Be Announced
Monday Afternoon, May 21, 2018
Room: Humphreys

* Invited Paper

3:30 PM C1.01

Fluorescence Enhancement of Nitrogen-Vacancy Centres in Diamond

Mauro Carmeli1, Philipp Reineck1, Desmond Lau1, Antony Orth1, Jan Jeske1, Marcus W. Doherty1, Takeshi Ohshima1, Andrew D. Green2 and Brant C. Gibson2,3; 1School of Science, RMIT University, Melbourne, Victoria, Australia; 2ARC Centre of Excellence for Nanoscale BioPhotonics, Melbourne, Victoria, Australia; 3Laser Physics Centre, Research School of Physics and Engineering, Australian National University, Canberra, Australian Capital Territory, Australia; 4National Institutes for Quantum and Radiological Science and Technology, Takasaki, Japan.

Bright fluorescence from nitrogen-vacancy (NV) centres in diamond is critical for many applications. The NV centre is a fluorescent defect in the...
Diamond lattice that has gathered interest in the science community in the last decades. Its applications range from optically detected sensing using ensembles of NV centres to nanometer scale fluorescent markers for fluorescence microscopy. The examples mentioned take advantage of the photostable, near-infrared emission from a large number of NV centres and the study of techniques to enhance their fluorescence is constantly needed. Our study, both experimental and theoretical, focuses on the effect of magnetic field on the fluorescence of the NV centre. Our results demonstrate a non-monotonic trend in the emission that shows an enhancement of the fluorescence at high magnetic field values. With the addition of a phenomenological model we further investigate the photo-physical behaviour of the NV centre and explore the implications in magnetic field-driven applications.

3:45 PM C1.02
Variation of Nitrogen Vacancy Center Concentrations in CVD Diamond Epitaxial Lateral Overgrown on Tungsten and HTHP Diamond Substrate Zongchen Liu, Jiao Fu, Zhaoheng Liu, Wen Cheng, Wei Wang, Shuwei Fan and Hongxing Wang; Institute of Wide Bandgap Semiconductors, Xi’an Jiaotong University, Xi’an, China.

The negatively charged nitrogen vacancy center (NV) in diamond is a promising light source for quantum applications, including quantum information processing and high sensitive detectors, such as magnetometer, thermometer and gyroscopes. The concentration of NV is one of the key factors that influences sensitivity of detector. For instance, the gyroscopes sensitivity can be greatly improved by increasing the NV concentration. Therefore, it is significant to find an approach to increase the NV center concentration in diamond. Here, CVD synthetic system is chosen to grow epitaxial lateral overgrowth (ELO) diamond layer on type Ib HTHP diamond substrate (no NV centres exist), whose surface is patterned by tungsten and, therefore, a higher NV center concentration around the tungsten metal even the HTHP substrate underneath the tungsten is gotten. Both higher NV and NV concentration are found in ELO diamond layer above the tungsten metal. We find that both NV and NV concentrations are increased above the tungsten, and the concentration of NV is much higher than that of NV barely exist beneath the tungsten. The higher NV center concentration is caused by the higher vacancy concentration, which could be increased by the existence of tungsten metal in CVD growth process. The details will be presented in the conference.

4:00 PM *C1.03
Engineering Coherent Defects in Diamond Nathalie de Leon; Electrical Engineering Coherent Defects in Diamond, *C1.03
4:30 PM C1.04
Engineering Spin Defects in <100> and <111> Oriented, Isotopically Controlled Diamond Layers
Christian Osterkamp, Priyadarsini Balasubramanian, Thomas Unden, Boris Naydenov and Fedor Jelezko; Institute for Quantum Optics and Center for Integrated Quantum Science and Technology, Ulm University, Ulm, Germany.

The negatively charged nitrogen-vacancy center (NV) in diamond is one of the most promising candidates for the realization of a quantum sensor. The fluorescence of a single NV can be detected and its electron spin can be polarized, read-out and manipulated at ambient conditions. The creation of NVs on demand is an important step towards quantum magnetic- and electric field sensors. We engineer 15NVs by delta doping during a plasma enhanced chemical vapor deposition (PECVD) process and we are able to produce an isotopically pure diamond environment by changing the ratio of 13C/12C atoms in the growth chamber. By polarizing the 13C spins in the vicinity of an NV center, a nano nuclear spin ensemble can be created, which is important for the further development of nuclear magnetic resonance spectroscopy. This effect can even be improved if the NV center is embedded in a 13C environment which is spin free, therefore preserves the coherence of the electron spin and increases the sensitivity.

A high nitrogen incorporation rate combined with the controllability of the NV axis alignment makes <111> oriented diamond an interesting material for the creation of ensembles. Shallow ensembles can be used for NV magnetometry and the detection of very small electric and magnetic fields. In our experiments we are able to show perfect NV alignment along the <111> axis with a NV concentration of 20 ppb. Our new modified vacuum system enables us to produce ultrapure diamond with the potential to control the NV creation in 13C enriched diamond layers for both orientations <100> and <111>. The study of nitrogen to NV conversion as well as the intrinsic nitrogen content of our isotopically controlled layers are further goals of our research. References

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4:00 PM K2.02
Nanodiamond–Gold Core Shell Nanoparticles for Bio-Imaging Applications
Yu-Chung Lin1,2, Elena Perevedentseva1,4, Zhe-Rui Lin1,5, Elena Perevedentseva1,4, Zhe-Rui Lin1,5, Christophe E. Nebel3, Giorgio Speranza4, Artashes Karmenyan1

It has been a new trend to develop multifunctional nanoparticle (NP) for bio-medical applications. The methods to integrate diverse functionalities are developed. One of the promising approaches is synthesis of hybrid NP with synergetic properties. This paper discusses multifunctional applications of core-shell nanodiamond-gold (ND@Au) nanoparticles and demonstrates number of imaging modalities using them. Development of the nanoparticles (NP) for bio and medical applications is in high degree motivated by perspectives of their multifunctional uses. Therefore, theranostic applications can include simultaneously such functionalities as drug delivery or other medical treatments with multimodal imaging, and are now widely developed on the base of nanoparticles of various properties. One of the approaches to obtain the NP with pre-established necessary properties is creation of hybrid structures for a combination of complementary facilities or obtaining synergistic properties. In the present work we consider diamond-based nanostructures formed by SiV-doped nanodiamond (ND) cores coated with a gold shell. This NP combines abilities and advantages of fluorescent ND and of the metal with plasmonic properties. The silicon impurities in a diamond lattice form Si-vacancies or SiV color centers. ND enriched with SiV is considered a promising NP for bio-imaging due to its intense and narrow fluorescence peak located in the near-infrared range, the most convenient for imaging of biological systems. The gold shell of NP provides additional opportunities for bio-imaging and treatment, in particular, on localized plasmon surface resonance (SPR) and thermal properties of gold. Additionally, both ND and Au nanostructures have been demonstrated as bio-compatible; their surface properties allow functionalization with different methods and different kinds of molecules thus they can be used in drug delivery studies and applications. In the present work we discuss multifunctional applications of ND@Au NP and demonstrate their applications for multimodal imaging, based on the optical properties both ND and gold, via mapping of distribution of spectral and fluorescence lifetime intensities. A number of imaging and sensing modalities for multifunctional ND@Au nanoparticles are demonstrated and add to more facilities for ND@Au bio applications. Particularly, ND@Au nanoparticles can be a convenient agent for applications like photothermal imaging and treatment and for studies involving photocoustic effect. Reference: [1] G. Bao, S. Mitragotri, S. Tong. Multifunctional Nanoparticles for Drug Delivery and Molecular Imaging. Annu. Rev. Biomed. Eng. 2013, 15, 253-282. [2] B. Shi, X. Du, J. Chen, L. Fu, M. Morsch, A. Lee, Y. Liu, N. Cole, R. Chung, Multifunctional Hybrid Nanoparticles for Traceable Drug Delivery and Intracellular Microenvironment-Controlled Multistage Drug-Release in Neurons, Small 13(20), 2017 [3] L. Minnati, C.L. Cheng, Y.C. Lin, J. Hees, G. Lewes-Malandrakis, C.E. Nebel, F. Benetti, C. Migliarei, G. Speranza, Synthesis of novel nanodiamond–gold core shell nanoparticles, Diamond & Related Materials 53 (2015) 23–28 [4] I. V. I. Vlasov, A. A. Shiryaev, T. Rendler, S. Steinert, S. Y. Lee, D. Antonov, M. Vörös, F. Jelezko, A. V. Fisenko, L. F. Semjonova, J. Biskupek, U. Kaiser, O. I. Lebedev, I. Sildos, P. R. Hemmer, V. I. Konov, A. Gali, J. Wrachtrup. Molecular-sized fluorescent nanodiamonds. Nature Nanotechnology 9, 54-58 (2014)
The optical and magnetic properties of the nitrogen-vacancy (NV) center make fluorescent nanodiamonds (FNDs) highly interesting for applications in biology. Due to their infinite photostability, they can be used as probes that can be tracked for extended durations. Another challenging application is the use of FNDs to extract magnetic information from the environment. In cell biology, magnetic noise originates from free radical molecules that play a key role in normal metabolism, age, and cell death.

Successful development of nanodiamond based magnetic sensing in biology would provide access to information on a time and length scale that is currently unavailable in the life sciences. The endeavor requires a multidisciplinary effort, ranging from physical characterization to biocompatibility studies and instrument development. To this aim, we have performed studies on the physical and chemical properties of nanodiamonds, as well as their interaction with various cell types. Single-center FNDs have been shown to possess angular geometries, which is expected to relate to their interaction with cell walls and intracellular pathways. While they show good biocompatibility with many model systems, such as macrophages, HeLa cells, and yeast cells, uptake efficiency among different cell types varies greatly. With respect to bacteria, nanodiamonds in high concentrations show a slight antibacterial effect, dependent on genus and strain, and their respective behavior in colloidal suspension. In accordance with experiments on smaller detonation nanodiamonds, the antibacterial effect of FNDs has been linked to their surface chemistry. The FNDs suitability as a biosensor in microbial research was assessed by evaluating bacterial viability and metabolism under varying levels of exposure to the particles. Furthermore, the clinically relevant biofilm mode of bacterial growth was considered. At the current level of investigation, interfacing or internalization of FNDs for magnetic sensing purposes show no significant adverse effects on the biological systems under study, providing a positive outlook on the development of new applications.

References

**4:45 PM K2.05**

**Purification and Characterization of Nanodiamond by Surface Enhanced Raman Scattering** by Yonhua Tzeng, Yen-Shiang Mao and YenChen Lin; Electrical Engineering, National Cheng Kung University, Tainan, Taiwan.

Surfaces of nanodiamond of 2-5 nm in sizes possess a wide variety of functional groups and non-diamond carbon phases. For many applications, it is desirable to begin further processing of nanodiamond from a purer and mostly sp3 bonded diamond phase. Therefore, removal of non sp3 bonded carbon phases and functional groups on surfaces of nanodiamond becomes necessary. In this work, nanodiamond is subjected to wet chemical etching, thermal treatment in hydrogen, and dry etching by hydrogen plasma. Raman scattering is a convenient means of characterizing diamond and nanocarbon phases. By the use of surface enhanced Raman scattering (SERS) substrates made of combined graphene and silver nanostructures which have been shown to exhibit Raman scattering signal enhancement factor as high as 10E14 times for R6G molecules, as received nanodiamond and purified nanodiamond are characterized to reveal the evolution of nanodiamond towards a purer diamond phase after nanodiamond surfaces are etched by selected wet chemical, thermal, and plasma etching. Effects of post-etching diamond CVD processes on the purified nanodiamond will also be discussed.

References
PS1: Poster Session I
Monday Afternoon, May 21, 2018
5:30 PM - 7:30 PM
Room: Doyle/Rees

* Invited Paper

PS1.01
Chemical and Structural Properties of RF \textsuperscript{(N)} Plasma Treated Diamond (100) Surfaces
Mohammed Attrash, Mohan Kumar Kuntumalla and Alon Hoffman; Schulich Faculty of Chemistry, Technion – Israel Institute of Technology, Haifa, Israel.

Diamond surface crystal structure quality and chemical composition play a vital role for many applications, such as activation and properties of NV centers emission in the near surface of diamond. Nitrogen terminated diamond (N-terminated diamond) can be fabricated by exposing diamond to N\textsubscript{2} radio frequency (RF) plasma. In this work, we investigate the interaction of \textsuperscript{N} RF plasma onto single crystal diamond (100). To minimize surface damage the plasma conditions were optimized such as flow rate, and grounded mesh electrode placed at the plasma source exit, to prevent interaction between ions and the diamond surface. Optical emission spectroscopy was used to characterize the species present in the plasma. Thermal stability and surface structure of N-terminated diamond were investigated in-situ by using x-ray photoelectron spectroscopy and low energy electron diffraction. HCN and \textsuperscript{N} desorption from N-terminated diamond was investigated by using temperature-programmed desorption (TPD). Optical emission spectroscopy showed that increasing flow rate can decrease the ratio of charged-to-neutral nitrogen particles. TPD spectra showed first order reaction, \textsuperscript{N} had two desorption peaks with maximum at 180°C and 610°C, while the CN spectra had desorption peak at 600°C.

PS1.02
Characterization of Single Crystal Diamond Grown on Different Off-Cut Angles from the (100) Crystallographic Plane
Ayan Bhattacharya\textsuperscript{1}, Ramon D. Diaz\textsuperscript{2}, Aaron Hardy\textsuperscript{1} and Timothy A. Grotjohn\textsuperscript{1,2}; \textsuperscript{1}Electrical and Computer Engineering, Michigan State University, East Lansing, Michigan, United States; \textsuperscript{2}Fraunhofer USA Center for Coatings and Diamond Technologies, East Lansing, Michigan, United States.

Single crystal diamond (SCD), that is grown by chemical vapor deposition (CVD) technique, is a material of great scientific and technological interest due to its exceptional mechanical, thermal, optical and electronic properties. However, applications of SCD for electronic devices ask for minimal nitrogen impurities to be present in the substrate, otherwise charge trapping, charge transport and electric field breakdown properties will be affected. This is one of the prime criteria for growth of SCD for high energy particle detector application\textsuperscript{1}. But such a growth process in a very low nitrogen environment comes with its cost, which can be undesirable surface morphologies and dislocation defects that reduce the quality of the grown layer and therefore making it less suitable for any detector and electronics applications. Also the growth rates become slow for SCD in low nitrogen impurity environment and adds to an additional challenge to grow thick layers (more than 100\textmu m). An alternative way is to grow diamond on a surface with an off-cut from the (100) crystallographic plane to reduce defects originating from the top surface\textsuperscript{2} during deposition. In this work, we have looked into growth strategies on 2.5\textdegree, 5\textdegree and 10\textdegree offcut substrates from the (100) crystal plane and along the [110] direction. Both bevel cut substrates and parallel plate substrates with offsets were used. All depositions were conducted in a 2.45 GHz a microwave plasma assisted CVD reactor\textsuperscript{3} using hydrogen and methane feedgas mixtures. Typical durations for depositions were 2.5, 12 and 24 hours. The end-product grown layer had thickness ranging from 30\textmu m to 250\textmu m. The major focus of these study was to examine the grown in terms of terrace and step formation and the spatial distribution of steps and terraces on the overall surface with respect to offset angle and growth duration. Any appearance of pyramidal features, the evolution of the top growth surface with time, and the growth rate variation versus the position of the top surface as the top surface evolves with time were studied in detail. We have also looked into grown layers with the offset being along [110] direction. The quality of the grown layers (in terms of nitrogen impurities) have also been studied by photoluminescence. An overall relationship between offset angle, step heights and terrace width, and impurity distribution will be presented. The authors would like to acknowledge the fund on NSF grant 1628958. 1) A. Bhattacharya, T. A. Grotjohn and A. Stolz, Degradation of single crystal diamond detectors in swift heavy ion beams, Diamond and Related Materials (2016) 70, 124-131. 2) O. Maeda, H. Miyatake, T. Teraji, T. Ito, Characterization of substrate off-angle effects for high-quality homoepitaxial CVD diamond films, Diamond and Related Materials (2008) 17, 435-439. 3) J. Lu, Y. Gu, T.A. Grotjohn, T. Schuelke, J. Asmussen, Experimentally defining the safe and efficient, high pressure microwave plasma assisted CVD operating regime for single crystal diamond synthesis. Diamond and Related Materials (2013) 37, 17-28.

PS1.03
Cubic Boron Nitride on Semiconducting Diamond and Its Application to Neutron Detection
Jesse Brown, Yu Yang, Joseph Shammas, Franz Koeck and Robert J. Nemani; Physics, Arizona State University, Tempe, Arizona, United States.

We have successfully deposited cubic boron nitride (c-BN) on nitrogen doped, polycrystalline diamond and boron doped, single crystal diamond, using plasma enhanced chemical vapor deposition (PECVD) employing fluorine chemistry. In situ X-ray photo spectroscopy (XPS) was utilized to characterize the sp\textsuperscript{3} bonding structure of c-BN. Cubic boron nitride is the zinc-blende analog to diamond, which is now being considered as an ideal material for radiation detection. TEM measurements demonstrate local epitaxy for c-BN on polycrystalline diamond. Boron containing materials are particularly relevant to detecting neutrons because of their large cross section to neutron capture and alpha particle emission. Moreover, diamond and c-BN have similar lattice constant and optical band gap which enables an integrated detector design. We present an approach to deposit c-BN on the p-type layer of a PIN diamond device in order to create a neutron detector. With the similar structural and outstanding thermal properties of c-BN and diamond, these devices can be used in a variety of applications, including high temperature environments.

PS1.04
Increasing the Area of Single Crystal Diamond Plates Grown by a Combination of Mosaic Technique and Lateral Growth
Ramon D. Diaz\textsuperscript{1}, Aaron Hardy\textsuperscript{2} and Timothy A. Grotjohn\textsuperscript{1,2}; \textsuperscript{1}Electrical and Computer Engineering, Michigan State University, East Lansing, Michigan, United States; \textsuperscript{2}Fraunhofer USA Center for Coatings and Diamond Technologies, East Lansing, Michigan, United States.

The electrical, mechanical, and thermal properties of diamond make it a promising material for new generation electronic devices. One of the challenges is the need for fabricating larger size Single Crystal Diamond (SCD) wafers with minimal defects. In this study, SCD plates were successfully grown based on the mosaic technique combined with conditions known for enhanced lateral growth. In earlier works\textsuperscript{1} the plates were tiled together using substrates created by a process consisting of ion implantation followed by growth and electrochemical separation. The approach in this work is different in that a starting substrate is cut in two, then each of the two pieces are grown larger laterally followed by a growth that stitches them back together with a larger area. A series of steps were taken to ensure good crystallographical orientation, starting with laser cutting the tiles from the same 3.5mmx3.5mmx1.4mm HPHT (High Pressure High Temperature) seed. The original area of the two substrates was increased by growing a layer of diamond via MPACVD (Microwave Plasma-Assisted Chemical Vapor Deposition) using a pocket configuration which favors lateral growth\textsuperscript{2}[3]. The grown tiles are polished and kept in aligned contact by their base with a polycrystalline diamond plate used as reference on the holder during growth. This step produced a continuous layer diamond across the two pieces. The grown together substrate was then re-polished and re-grown multiple times by MPACVD process until the contact (stitched region) interface disappeared, effectively merging the tiles back into a single crystal. Off-plane variations of the initial cut and their effect were explored. The defect densities from the top 500-600\textmu m grown layer from each step were analyzed by etch pit counting and birefringence measurements. This process shows the feasibility of combining known lateral growth techniques for expanding the area of 27

In this work we investigated some aspects of diamond growth from ammonia, methane and hydrogen precursors by hot filament CVD (HFCVD) method. The samples were deposited from different NH3, CH4 and H2 gas mixtures, pressures and different surface temperatures. The obtained polycrystalline diamond films were investigated using HRSEM, Raman and XPS spectroscopies. The structural evolution from ultra nano-crystalline diamond (UNCD) films to sub-microcrystalline structure was associated with increasing the ammonia concentration and substrate temperature. According to the SIMS measurements, it was found that nitrogen concentrations strongly depend on NH3/CH4 ratio and substrate temperature. The impact of total pressure and filament temperature during the diamond deposition on film morphology and composition is also discussed in this paper. We investigated the gas phase composition in-situ during the diamond deposition process by mass spectrometry. We examined the gas phase chemistry using deuterium gas (D2) and deuterated methane (CD3). Based on the obtained results the diamond growth mechanism from ammonia precursor in the HFCVD was proposed. It is suggested that by controlling the deposition parameters from NH3/CH4/H2 gas mixtures the diamond grain size and nitrogen concentration can be effectively tuned.

PS1.05
Relation of Activated Gas Phase Chemistry and Substrate Temperature on the Microstructural Properties of Diamond Films Deposited from CH4/NH3/H2 Gas Mixture Sergey Elinichev, Yulia Stotsky, Rozalia Akhvlediani and Alon Hoffman; Schulich Faculty of Chemistry, Technion-Israel Institute of Technology, Haifa, Israel.

In this work we investigated some aspects of diamond growth from ammonia, methane and hydrogen precursors by hot filament CVD (HFCVD) method. The samples were deposited from different NH3/CH4/H2 gas mixtures, pressures and different surface temperatures. The obtained polycrystalline diamond films were investigated using HRSEM, Raman and XPS spectroscopies. The structural evolution from ultra nano-crystalline diamond (UNCD) films to sub-microcrystalline structure was associated with increasing the ammonia concentration and substrate temperature. According to the SIMS measurements, it was found that nitrogen concentrations strongly depend on NH3/CH4 ratio and substrate temperature. The impact of total pressure and filament temperature during the diamond deposition on film morphology and composition is also discussed in this paper. We investigated the gas phase composition in-situ during the diamond deposition process by mass spectrometry. We examined the gas phase chemistry using deuterium gas (D2) and deuterated methane (CD3). Based on the obtained results the diamond growth mechanism from ammonia precursor in the HFCVD was proposed. It is suggested that by controlling the deposition parameters from NH3/CH4/H2 gas mixtures the diamond grain size and nitrogen concentration can be effectively tuned.

PS1.06
Improving the CVD Growth Duration and Quality of Thick Heavily Boron Doped Diamond Epitaxial Layers Aaron Hardy1, Robert B. Rechenberg1, Michael Becker2, Timothy A. Grotjohn1, 2 and Thomas Schuekier1, 2; 1Center for Coatings and Diamond Technologies, Fraunhofer USA, East Lansing, Michigan, United States; 2Electrical and Computer Engineering, Michigan State University, East Lansing, Michigan, United States.

As a material for high power electronic devices, single crystal diamond has the potential to outperform other materials in terms of power density and heat dissipation. In order for these devices to be realized, high quality, heavily boron doped epitaxial layers (p layers) must be synthesized faster and more reliably. This study presents working solutions to a number of problems commonly reported in the synthesis of p indicated diamond. A low substrate temperature results in reduced deposition rate, while a high substrate temperature may result in the formation of diamond films having nanometer sized grain structures. This study presents working solutions to a number of problems commonly reported in the synthesis of p diamond via hot-filament CVD including low growth rate, non-epitaxial crystallite formation, and premature reactor shutdown due to soot formation. In this study, a 2.45GHz tunable cavity type MPACVD reactor is used. Depositions are done on a thermally floating sample stage, because the higher power required to reach deposition temperature with an actively cooled sample stage results in unnecessary heating of the quartz dome. The high concentration of dopant gas (~2000ppm B/C) needed to get sufficient boron incorporation in the diamond (1010 – 1011 cm3) often causes unwanted soot formation around the plasma. Eventually this soot coats the quartz dome to the point that the plasma becomes unstable and the process must be terminated. Unnecessary heating of the system expedites this process. Therefore, in order to get long deposition times, it is best to use the minimum power required to operate the plasma such that the substrate reaches the process temperature. In order to achieve adequate plasma power density at relatively low forward power (1.3 – 1.5 kW), process power was increased from 240 to 300 Torr. Other techniques employed include the addition of CO2 to the process gasses in order to etch away crystallites which may pop off of the sample holder and land on the diamond during deposition [1]. Additionally, switching from (100) oriented substrates to those cut at an angle of 3° off-axis from the (100) plane in the [010] direction results in higher boron incorporation into the epitaxial layer, and smoother surface morphology after deposition. These key improvements result in higher conductivity p layers, and up to 400% increase in run time. Previously, unwanted shutdowns due to soot formation regularly occurred after less than 12 hours of deposition, and the p layers produced had room temperature resistivities between 1x104 and 9x102 Ωcm as measured by four-point probe. In comparison, the revised process has successfully been sustained for 47 hours, resulting in a 300 μm thick p layer with a room temperature resistivity of 2.2x102 Ωcm.


PS1.07
Morphological and Surface Properties of Diamond Thin Films Deposited at Low Substrate Temperatures Mohan Kumar Kuntumalla, Miriam Fischer, Rozalia Akhvlediani and Alon Hoffman; Schulich Faculty of Chemistry, Technion - Israel Institute of Technology, Haifa, Israel.

In this work, polycrystalline diamond thin films were deposited on Si (100) substrates by using CO2 (with and without) gas in the CH4/H2 gas mixture by hot-filament CVD in the 200 to 720 °C back substrate/surface temperature range by force-cooling. An exhaustive temperature calibration has been carried with outmost care to measure the films’ top-surface temperature during the diamond deposition. It was found that for silicon substrate (thickness 500 μm) the temperature difference (ΔT) between the back substrate and the top film surface was in the range 200 to 450 °C. Scanning electron microscopy was used to study the surface morphology of the grown films. Raman spectroscopy was used to determine the diamond and non-diamond phases whereas XPS and HREELS were utilized to investigate the diamond films’ surface. It was observed that the substrate top-surface temperature plays a crucial role on the diamond nucleation and growth process. A low substrate temperature results in formation of diamond films having nanometer sized granular features in comparison to the commonly anticipated columnar growth at higher temperatures. The growth-rate is largely reduced with temperature decrease due to low mobility of active species on the evolving surface. Our results are important for the quest to deposit diamond films at low substrate temperatures for electronic and other applications.

PS1.08
The Interface and Mechanical Properties of CVD Single-Crystal Diamond by Multilayer Epitaxial Growth Yun Zhao, Chengming Li, Kang An, Xiongbo Yan, Lifu Hei, Jinlong Liu, Liangxian Chen, Junjun Wei and Fanxiu Lu; Institute for Advanced Materials and Technology, University of Science and Technology Beijing, Beijing, China.

The single-crystal diamond homoepitaxial layers with multilayer are synthesized by changing nitrogen input on the substrate of high pressure high temperature (HPHT) Ib synthetic diamond substrate using microwave plasma chemical vapor deposition (MPCVD) method. The fluorescence and phosphorescence characteristics of the cross section of the CVD layers grown on the HPHT seed crystal were investigated by DiamondView™ instrument. The stress and impurity distribution at the interface were measured by Raman and infrared spectroscopy. The characteristics of internal and surface defects of the HPHT Ib seed crystals were observed by X-ray topography. The formation of dislocations at the interface and the inheritance of dislocations between the seed and the CVD layer are discussed. The dislocation density of the HPHT Ib seed and CVD homoepitaxial layers after each growth were gained by X-ray rocking curves measurement, and it is found that the dislocation density increases almost 4 times after double homoepitaxial growth. The hardness and fracture toughness of different CVD layers are measured by indentation test. The relationship between the change of dislocation density and the mechanical properties are investigated after multiple growth of single crystal diamond. The hardness and fracture toughness of multilayer growth layer are increase trend. It can be concluded that single crystal diamond with the multiple stratification characteristics will improve the wear resistance of single crystal diamond cutter.
Selective Growth of Phosphorous Doped Single Crystalline Diamond on (100) Oriented Diamond Substrates

Robert B. Rechenberg1, Michael Becker1, Aaron Hardy1, Matthias Muehle1, Stephen Zajac1, Timothy A. Grotjohn1 and Thomas Schuelke2, 1Center for Coatings and Diamond Technologies, Fraunhofer USA, East Lansing, Michigan, United States; 2Electrical and Computer Engineering, Michigan State University, East Lansing, Michigan, United States.

Diamond has unique properties which make it an excellent candidate for high frequency and high-power electronics. Its thermal conductivity, high breakdown voltage, and wide bandgap enable applications with higher power densities and greater efficiency. To enable those diamond properties for applications such as high power diodes, a high-quality diamond growth is needed and a fabrication process needs to be developed. One processing step that is desired for electronic device fabrication is a selective growth of n-type diamond on undoped or p-type doped diamond. Such n-type regions can serve as the n-type regions in pn and pi diodes and as heavily doped regions for contacts to n-type (100) surface diamond.

It is common to fabricate diamond electronic structures on the (100) surface. So far, the fabrication of n-type diamond with high doping concentrations on (100) surfaces has proven difficult due to several factors. Phosphorous for example has a higher incorporation efficiency into the (111) lattice orientation and can reach a doping level of 10^21 cm^-3 versus 10^19 cm^-3 for (100) [1]. Whereas boron doped diamond has been successfully grown with high doping concentrations of 10^20 cm^-3 on (100) substrates [2]. The very limited availability of (111) oriented diamond substrates and the more difficult processing does not make it a good candidate as a substrate. Thus, a process was developed to selectively grow highly phosphorous doped diamond on boron doped diamond using (100) oriented substrates. The selective doping process consist of starting with a boron doped or undoped diamond layer on a substrate. In order to achieve high phosphorous doping concentrations, a process was developed to etch either (111) or (110) facets into SCD. A thin layer of nickel was deposited and patterned using a lift-off process. Depending on the feature dimensions, patterning was either done using e-beam or conventional photolithography. Afterwards, the Ni coated substrate was heated to about 900ºC in a hydrogen atmosphere for 1-2 hours which then formed pyramid-like etching structures with open facets. Afterwards, phosphorous doped diamond was deposited and resulted in selective growth onto the (111) surfaces but not the (100) surfaces. To characterize the diode regions, contacts were deposited onto the boron and phosphorous doped diamond surfaces and the I-V curves were measured. The I-V curves show pn junction characteristics. References [1] Kato, H., Makino, T., Yamasaki, S., & Okushi, H. (2007). N-Type Diamond Growth By Phosphorus Doping on (001) -Oriented Surface. Journal of Physics D: Applied Physics [2] Demlow, S. N., Rechenberg, R., & Grotjohn, T. (2014). The effect of substrate temperature and growth rate on the doping efficiency of single crystal boron doped diamond. Diamond and Related Materials

XANES and EXAFS Study of P Doped Diamond

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Diamond film collects all the outstanding properties of mechanics, electronics, heat, and optics etc. together making it have potential applications in the fields of wide range optical transparent window materials, super-hard coating tolls, and electron devices. The microwave plasma chemical vapour deposition (MPCVD) method is one of the most promising techniques for producing single-crystal diamond. In order to obtain high quality diamond, oxygen is often added into MPCVD chamber, because oxygen can etch graphite on diamond surface during diamond growth. However, the rate of diamond growth with oxygen addition is lower than arc-jet methods, etc. In order to obtain high-rate diamond growth, nitrogen is often added into MPCVD chamber. However, this method can deteriorate the diamond quality because of the nitrogen doping. Therefore, in order to obtain diamond with high quality and high-rate, nitrogen and oxygen are alternately added into MPCVD chamber during diamond growth. In this work, investigation of nitrogen and oxygen alternate addition during diamond growth by MPCVD has been carried out. HPHT (001) Ib single crystal diamonds in dimension of 3×3×0.5 mm were used as substrates. The growth of diamond films was carried out in a conventional 5-kW, 2.54-GHz MPCVD system (AX-6500, Seki) using gas mixtures of hydrogen, methane, oxygen and nitrogen. The growth conditions were summarized in Table 1. The way of nitrogen and oxygen alternate addition was shown in figure 1.

References


Epitaxial Growth of Ir Film on MgO (001) Substrate at Low Temperature by Sputtering

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Ir film has been deposited epitaxially on various oxide
substrates. The previously reported epitaxial deposition of Ir film on MgO(001) substrate mainly uses magnetron sputtering or electron beam evaporation or pulsed laser deposition at high temperatures, usually greater than 650 °C. An extended structure zone diagram including energetic deposition proposed by André Anders proves the possibility of epitaxial metal thin films at lower temperatures. In this article, we describe a new deposition method that can be used to prepare a good epitaxial Ir film at a lower deposition temperature on MgO(001) substrate. Using a bias RF sputtering deposition method, a seed layer was first formed on a MgO (001) substrate material, and then an epitaxial metal Ir film was prepared using conventional sputtering deposition from room temperature to 600 °C. The Ir(001) preferred orientation was studied by XRD, the epitaxial orientation was confirmed by EBSD, the orientation of Ir is parallel to the substrate orientation, meets the relationship Ir(001)//MgO(001), and the surface morphology was studied by atomic force microscopy. The details will be presented on the conference.

PSI.13
Etching Rates of Nitrogen-Incorporated Ultrananocrystalline Diamond Thin Film in Hydrogen and Oxygen Plasmas Measured by an Interferometry Method
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There is a strong motivation to develop and understand novel materials with the potential to be utilized as photocathodes, as these could have desirable photoemission properties for research and industrial applications. Specific challenges are to achieve higher quantum efficiency, better reliability, ruggedness, rapid response time, and precise control over spectral response and spatial beam coherence [1]. Nitrogen-incorporated ultrananocrystalline diamond (N:UNCD) thin films (~200 nm in thickness) have potential to become a material of choice for photocathode applications [2]. N:UNCD is a highly engineered material that has high quantum efficiency (QE) [2], low surface roughness, and high electron conductivity through the bulk [3]. N:UNCD only have high QE when processed in hydrogen plasma. Hydrogen termination onsets negative electron affinity and reduces the work function of N:UNCD. The negative electron affinity remains stable even if N:UNCD is stored in air for a limited amount of time. Recently, we have experimentally established that N:UNCD films have non-monotonic reflectance/absorbance dependence on the wavelength due to interference. Because QE is proportional to optical absorption, there are potentially “blind spots” (i.e. high reflection optical bands) where the photocathode won’t operate. Therefore, thicknesses control becomes a key factor to optimize QE. Yet, another critical question emerges – how much thickness is removed when N:UNCD is processed in hydrogen to achieve for high QE? An analytical procedure was developed to calculate the thickness of films using interference patterns measure by UV-vis spectroscopy. The procedure was cross-validated by scanning electron microscopy. A sequence of etching experiments of N:UNCD samples were carried out in hydrogen plasma. By applying our procedure, an etching rate of 5.5 nm/hr was determined. It was shown that during time typically needed to process N:UNCD in hydrogen negligibly changes the thickness and therefore the optical response of N:UNCD films. As a next step, we have extended our procedure and determined etching rates for N:UNCD processed in an oxygen plasma. Essentially, same procedure can be further extended toward N:UNCD processing in many other technologically important plasmas, e.g. O2/ H and O2/Ar mixtures. The procedure will be described, and the results of hydrogen and oxygen etching rates will be presented at the conference. [1] D.H. Dowell et al., Nucl. Instr. Meth. Phys. Res. A 622, 685 (2010). [2] K.J. Pérez Quintero et al., Appl. Phys. Lett. 105, 123103 (2014). [3] S. Bhattacharyya et al., Appl. Phys. Lett. 79, 1441 (2001).

PSI.14
Ion-Induced Surface Pattern Formation on Diamond-Like Carbon Films
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Ion induced surface pattern formation is a well-studied subject since several decades. The major mechanisms leading to periodic surface nano-patterns were curvature dependent ion erosion (Bradley-Harper Theory) and curvature dependent mass redistribution (Carter-Vishnyakov effect). During the last years several novel mechanisms and theoretical models have been developed and proposed, including the role of surface impurities or surfactants, the role of ion implantation, phase separation, hydrodynamic models and the generation and relaxation of stress. For several reasons diamond-like amorphous carbon thin films appear as an ideal model case to investigate these recently proposed effects. The films are by definition amorphous, so that crystal structure effects are absent, and exhibit an almost atomically flat ultra-smooth surface. Depending on the DLC film preparation conditions, the initial existing compressive film stress can be tuned. Carbon ions are readily available as mass selected ions beams and allow the investigation of pattern formation due to implantation of self ions. Irradiation with e.g. B+, N+ or F+ ions allows the study of pattern formation for amorphous binary compounds. Moreover, there is a strong tendency of DLC to accommodate significant amounts of implanted noble gas ions in form of small bubbles exhibiting liquid noble gas density at extremely high pressure. Therefore, ion implantation of noble gas ions also appears as a significant contribution to the evolution of surface patterns. In this contribution, we present experiments on ion induced pattern formation on tetrahedral amorphous carbon films on Si substrates using ion irradiation of different ion species at energies ranging from few hundred eV up to several 10 keV. We compare our results with the predictions of different theoretical models using parameters determined from Monte Carlo simulations of ion solid interaction.

PSI.15
Synthesis of Hydrophobic Micro and Nanostuctures Based on Metal Oxides, Carbon Nanotubes and Polymer Wastes for the Separation of Oil-Water Mixtures
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Petroleum hydrocarbons are the most important and used energy resources in the world; however, they are the main environmental pollutants. One of the biggest petroleum pollution is caused by petroleum spills [1-2]. Spills occur mainly in the open sea due to accidents or improper practices during the exploration and extraction of the material, which affect the entire ecosystem when the event occurs [3]. For the remediation of the places where spills occur, various classic techniques are used, such as containment barriers, oil skimmers, chemical dispersants, controlled burning, manual cleaning, etc. [4] which serve to remove most of the oil spills and clean the contaminated place. However, novel alternatives to solve this problem are in progress due to the fast development of nanotechnology. The use of several oxides as adsorbent materials for hydrocarbons has certain advantages over conventional materials, such as, for example, larger surface area or greater adsorption capacity [5]. In addition, they can be modified chemically or physically to be oleophilic and hydrophobic, require less storage space and can be reusable. Materials on their basis can be used in the remediation of oil spills, wastewater treatment, separation of hydrocarbon mixtures and different types of oil in water [6]. In this work, the use of different composites based on metal oxides, mainly of iron and nickel, in combination with carbon nanotubes and silica nanoparticles, is proposed. For the oil adsorption, the composites were synthesized by solid-state reactions and self-combustion of precursors. We selected these materials, since they have been proved to be easy coupled in batch type reactors; also, due to their magnetic properties, some of these composites allow their easy removal from the water. The capacity of adsorption was determined for hematite composites / nickel oxide and magnemite / carbon nanotubes. Both systems were characterized by techniques such as SEM and XRD and adsorption tests, performed using crude oil. In addition, absorbent materials were prepared from polymer wastes (recycled polyethylene terephthalate, PET, from bottles) using salt templates and hydrophobilized using carbon nanotubes and silica nanoparticles. Their application for oil removal showed enhanced capacity, efficiency and reusability. References [1] Novaki, L.P.,

PSI.16
Needle-Like Structure of Ultrananocrystalline Diamond Films for UV Detector Applications Chi-Wen Liu1, Yin-Tung Albert Sun1 and Chii- Ruey Lin2; 1Graduate Institute of Manufacturing Technology, National Taipei University of Technology, Taiwan; 2Department of Mechanical Engineering and Institute of Precision Mechatronics Engineering, Hsinchu, Taiwan.

This research work focused on the fabrication of nitrogen-incorporated ultra-nanocrystalline diamond (N-UNCD) films and their characteristics including surface morphology, microstructure, electrical property and photocconductivity aiming at applications in UV detector detection. Needle-like N-UNCD were synthesized using a home-made microwave plasma jet chemical vapor deposition (MPJ-CVD) system with CH4/H2/Ar/N2 as gaseous precursors, and then Au interdigital electrodes were deposited onto the surface of the as-grown N-UNCD films by the sputtering technique. Annealing procedures were conducted at various temperatures to obtain Ohmic contact of N-UNCD/Au structure. It was found that the N-UNCD/Au structure annealed at 500 °C exhibited a good Ohmic contact characteristic and high photodetection efficiency as well as rapid response to UV irradiation in air ambient with the high photo-dark current ratio about 3.1 orders of magnitudes. The achievement of our current study indeed opens up a prospect of photodetector applications of needle-like N-UNCD films in the future.

PSI.17
Magnetic Properties of Thermal and Microwave-Plasma CVD Deposited Fe-Filled Carbon Nanotubes—Comparative Study for Magnetic Devices Sekhar C. Ray; Physics, University of South Africa, Johannesburg, South Africa.

Fe-filled Carbon nanotube (CNT) arrays are fabricated using thermal and microwave-plasma chemical vapour deposition (CVD) methods. SEM and TEM characterizations showed that the well-aligned CNTs were 80-500 μm in length, with outer (inner) diameter of 20-50 (10-20) nm. The CNTs grown by thermal CVD shows higher magnetization than those grown by microwave-plasma CVD, which may be ascribed to the formation of metal-oxides in the CNT structures. Out of all samples, thermal CVD grown Fe-filled CNTs showed maximum magnetic coercivity ≈ 732 Oe and this value is higher than that of bulk iron. X-ray diffraction and Raman spectroscopy results are correlated with magnetic behaviours. The high coercivity and the structure of single-domain Fe-nanoparticles isolated by antiferromagnetic CNTs make it a promising candidate for high-density magnetic recording media.1

PSI.18
Magnetic Properties of Metal-Free Nitrogen-Doped Graphene Quantum Dots Muhammad Shehzad Sultan1, Vladimir I. Makarov1, Frank Mendoza1, Wojciech M. Jadwisienczak, Danilo Barrionuevo2, Muhammad Sajjad3, Brad Weiner4 and Gerardo Morell5; 1Physics, University of Puerto Rico, San Juan, Puerto Rico, United States; 2School of Electrical Engineering and Computer Science, Ohio University, Athens, Ohio, United States; 3Chemistry, University of Puerto Rico, San Juan, Puerto Rico, United States; 4Physics and Astronomy, Western Kentucky University, Bowling Green, Kentucky, United States.

Metal-free nitrogen doped graphene quantum dots (N-GQD) were synthesized and, for the first time to our knowledge, their magnetic properties were investigated. The results indicate that N-GQDs exhibit superparamagnetic behavior. The specific size, shape and zigzag edge structure of N-GQDs were taken into account to explain the origin of the observed magnetism. The magnetization dependence led to estimating the N-GQD material magnetic permeability for different ambient temperatures. From the zero-field-cooled (ZFC) and field-cooled (FC) magnetization measurements, carried out at 50 Oe magnetic field strength, we estimated the blocking temperature $T_B$ to be around 300 K. On the basis of the experimental data analysis, the magnetic permeability, number of correlated spins per single N-GQD, and number density of superparamagnetic N-GQD per gram of material were estimated. The excellent magnetic properties together with optical properties manifested by N-GQDs have the potential to lead to high performance biomedical and data recording devices.

PSI.19
(Late News) The Effects of Gamma Radiation on Carbon Nanotube Structure and Field Emission Performance Tasso von Windheim; Electrical and Computer Engineering, Duke University, Durham, North Carolina, United States.

Solid-state technology dominates the consumer electronics market because of the low cost associated with large-scale integration. However, there are numerous applications in which solid-state devices are unreliable or do not provide adequate performance, particularly applications with military systems operating in high radiation environments. In these applications, vacuum microelectronic devices present an attractive alternative. Despite the performance advantages, the use of vacuum electronics has been limited because there is no versatile and reliable microscale platform that enables integration of large numbers of vacuum circuit elements on a single substrate. To address this need, RTI International in collaboration with Duke University has been developing a Microelectromechanical systems (MEMS) platform with integrated carbon nanotube (CNT) field emitters that enables integration of high-performance microelectronic vacuum components into functional circuits on a single silicon substrate. In this study, we investigate the effects of radiation on the field emission properties of CNTs. CNTs were deposited on silicon substrates using microwave plasma enhanced chemical vapor deposition. The samples were exposed to gamma radiation doses of 0.5 Mrad(Si), 1 Mrad(Si), and 3 Mrad(Si). Typical lifetime exposure level for a spacecraft is 0.3-0.5 Mrad(Si). Scanning electron microscopy revealed no changes in the film morphology and no damage was visible on the surfaces of the AMW-CNTs. Raman spectroscopy was used to investigate the change in defect density caused by irradiation, and revealed that gamma irradiation at all dose levels caused a reduction in defect density as indicated by a reduced ratio of the D to G peak height observed in the Raman spectra. The decrease in D/G ratio for the 0.5 Mrad(Si), 1 Mrad(Si), and 3 Mrad(Si) was 7%, 11%, and 2% respectively.

Due to relationship between defect density and field emission, the field emission performance was affected by radiation. Turn-on field ($E_{on}$) increased by 1 V/micron for the sample exposed to 1 Mrad(Si) gamma radiation and increased by 5 V/micron for the sample exposed to 3 Mrad(Si) gamma radiation. There was no observed change in $E_{on}$ for the sample exposed to 0.5 Mrad(Si) gamma radiation. So while defect density was affected at all radiation dose levels, significant changes in field emission performance was only observed for samples dosed at 1 Mrad(Si) and 3 Mrad(Si), which are much greater than the expected lifetime exposure levels for a typical spacecraft. In addition, analysis of the field emission performance using the Fowler-Nordheim model indicates that the decrease in defect density reduces self-heating. This is further evidence that CNTs are indeed a potential candidate for use in vacuum microelectronics in high-radiation environments such as outer space.

PSI.20
A Betavoltaic Microcell Based on Semiconducting Single-Walled Carbon Nanotube Arrays/Si Heterojunctions Jinwen Zhang; Institute of Microelectronics, Peking University, Beijing, China.

This paper reports a novel betavoltaic (BV) microcell based on semiconducting single-walled carbon nanotube (s-SWCNT) arrays/Si heterojunctions. There are three new features. Firstly, the new BV microcell is constructed by the aligned arrays of p-type s-SWCNTs onto n-type silicon forming p-n heterojunctions as energy conversion, rather
than Schottky junctions such as SWCNTs thin film/Si [1] and Au/s-SWCNT-Ti [2] in our previous works. Secondly, the s-SWCNT arrays/Si p-n heterojunctions display better rectification characteristics than the foregoing two Schottky junctions with a leakage current (I_L) as low as 1.5pA and an ideality factor (n) of 1.83. Thirdly, the new BV microcell reveals higher performance than our previous ones. Under 7.8mCi/cm² 63Ni irradiation, \( I_{c}=62nA, I_{v}=3.8μA/cm² \), fill factor (FF) of 33.4% and energy conversion efficiency (η) of 9.8% were achieved. BV microcells are attractive candidates for micro-power sources owing to their high energy density, long lifetime and durability in extreme environments. Several semiconducting materials have been studied such as GaN and GaAs [3, 4]. However, most microcells are limited to the low current density and energy conversion efficiency. Our group first proposed and demonstrated that SWCNTs could be considered as a perfect material for BV microcells. Given that the p–n junction exhibits better rectification property than Schottky junction [5], we present the design, fabrication and performance of a novel BV microcell based on s-SWCNT arrays/Si p-n heterojunctions in this paper. In conversion part, the aligned arrays of p-type s-SWCNTs contact with the n-type silicon substrate (2-4Ωcm) to form p-n heterojunctions. The front and back electrodes of Au forming ohmic contact with s-SWCNTs and Si respectively are employed to transport carriers to external circuit. In source part, 63Ni thin film on a nickel foil continuously emits β particles for energy supply. Under radiation, electron-hole pairs (EHPs) excited and generated in the depletion region can be separated and swept by the built-in electric field into external circuit to produce electrical current. Cr/Au and Ti were sputtered and patterned on silicon substrate with 300nm thick silicon dioxide (SiO₂) layer in sequence. Cr/Au was sputtered on the back side of silicon substrate and sintered at 320°C. Whole water was diced to 6980μm×6980μm dies as samples. The semiconducting-enriched (99%) SWCNT solution of NanoIntegris was diluted with deionized water down to 0.1μg/ml. After switching on the AC voltage source (Vpp=5V and f=5MHz), a drop of the suspension was dripped onto a sample and blown off after 60s. Then a staircase-increased negative drain bias from 0V to -20V was applied to selectively burn off metal-SWCNTs with 15V on the back gate. Next, the Ti and uncovered SiO₂ layer were etched by BHF so that the parallel and aligned s-SWCNTs adhered tightly to Si substrate by capillary force (Fig. 4). 7.8mCi/cm² 63Ni film was electroplated on a nickel foil. In our testing system, the conversion part was aligned to the source part face to face with 1mm gap. I-V curve in dark of the device proves good rectifying characteristics. By fitting it with the ideal diode equation \( I=I_0[exp(qV/nkT)-1] \), the leakage current was deduced to 1.5pA with n=1.83, indicating that s-SWCNT arrays/Si p-n heterojunction has better characteristics than SWCNTs based Schottky junctions. Under radiation, the I-V curve moves downwards revealing \( V_{c}=62mV \) and \( I_{c}=3.8μA/cm² \) and the P-V curve shows FF of 33.4% and η of 9.8%. It proves that s-SWCNT arrays/Si p-n heterojunctions have huge potential for application in betavoltaic microcells. References [1] Anonymous Reference No. 1. [2] Anonymous Reference No. 2. [3] M. Lu, et al., Energy Conversion and Management, vol. 52, pp. 1955-1958, 2011. [4] C. W. Liang, et al., Nano Lett., vol. 8, pp. 1809-1812, 2008. [5] Y. B. Liu, et al., vol. 70, Appl. Radiat. Isotopes, pp. 438-441, 2012.

**PSI.21**

**Synthesis and Extensive Characterization of Mesoporous Graphene-Based Nanomaterials to Establish Structure-Activity Relationship**

Sanju Gupta, Brendan Evans and Romney Meek; Western Kentucky University, Bowling Green, Kentucky, United States.

Graphene-based nanomaterials including few-layer graphene oxide, reduced graphene oxide, three-dimensional scaffolds of graphene and graphene-carbon nanotube aerogels and their nitrogenated counterparts are synthetically and environmentally friendly. These graphene-family nanomaterials are extensively characterized in terms of surface morphology and structure using electron microscopy, optical and vibrational techniques which provided microscopic structure and unprecedented physical properties useful for electrochemical energy storage and water desalination. Raman spectroscopy (RS) provided lattice dynamical structural characterization at nanoscale revealing collective atomic/molecular motions and localized vibrations. We analyzed Raman spectra in terms of prominent band position and intensity ratio that help to quantify microscopic stress/strain, structural disorder, number defect density, respectively. Photoluminescence excitation (room temperature luminescence with varying excitation wavelength) spectra revealed the electronic band structure such that distinct localized pi electrons were found in-between the band gap for the functionalized graphene. In addition, we have used advanced electrochemical microscopy technique to investigate dynamic physicochemical processes occurring at the surface of these exotic graphene-family nanomaterials and at the solid/liquid (electrode/electrolyte) interface. We discuss our experimental findings in terms of the multiple roles of oxygen and nitrogen functional groups and establish (micro)structure-property-activity relationship, relevant for alternative energy, catalysis, sensing and water treatment, to name a few.

**PSI.22**

**Graphene/TiO₂ Composites for Infrared Radiation Shielding**

Artur Malolepszy, Marta Mazurkiewicz-Pawlicka and Leszek Stołbński; Faculty of Chemical and Process Engineering, Warsaw University of Technology, Warsaw, Poland.

Inorganic nanocrystals attract great interest due to their unique physical properties and immense potential for applications. In particular, nanocrystals offer exciting opportunities for technologies on the interfaces between chemistry, physics, biology, and medicine. The aim of our research was investigation of the influence of titanium dioxide / graphene composites on the infrared radiation shielding. Depending on the content of TiO₂, the composites exhibit different IR shielding efficiency. Graphene oxide (GO) were prepared via modified Hummer’s method. Titanium dioxide nanoparticles were deposited on the surface of graphene flakes by the hydrothermal method. Isopropanol alcohol solution of Titanium(IV) isopropoxide precursor was initially mixed with water and then heated in the microwave pressure Teflon reactor at the temperature around 220 °C and under the pressure of 55 bars for 30 min. The obtained composites were characterized by: i) X-ray diffraction (XRD) – to determine the average size of crystallites and the phase composition, ii) electron microscopy (SEM/STEM) – for imaging the metal oxide distribution on the surface of graphene flakes, iii) thermo-gravimetric analysis (TGA) – for determining the thermal stability and percentage content of graphene and metal oxides. Absorption of IR radiation were measured using FT-IR spectrometer in the range of 400 – 7000 cm⁻¹.

**PSI.23**

**Nonacrystalline Graphene Film Growth on Non-Metallic Substrates by Hot Filament Chemical Vapor Deposition**

Sandrin M. Rodriguez¹, Alvaro Instan¹, Frank Mendoza¹, Ram Katiyar¹, Brad Wiener² and Gerardo Morell¹; ¹Physics, University of Puerto Rico at Rio Piedras, San Juan, Puerto Rico, United States; ²Chemistry, University of Puerto Rico at Rio Piedras, San Juan, Puerto Rico, United States.

Direct synthesis of nanocrystalline graphene by hot filament CVD on non-metallic materials is reported. Samples were deposited in a low pressure atmosphere of methane with an average substrate temperature of 904°C followed by convection cooling to room temperature. The structural properties of the carbon films were analysed using Raman Spectroscopy and Atomic Force Microscopy (AFM). Raman mapping showed that the ratio of the D/G peaks intensity is in the range of 0.41 to 0.68 over 90% of the scanned surface area of 150 × 100 μm². The average value of the 2D peak FWHM was 60cm⁻¹ and the average ratio of D/G peak intensity was 1.3, indicating that the carbon films are composed of nanometer-scale crystallites. AFM in tapping mode was used to estimate the number of layers of the grown graphene films. The potential applications in electrical devices to measure biological responses are also discussed.

**PSI.24**

**Synthesis and Characterization of Various Graphene Foams**

Leszek Stołbński, Artur Malolepszy, Marta Mazurkiewicz-Pawlicka, Tomasz Kotkowski, Robert Cherbanski and Eugeniusz Molga; Faculty of Chemical and Process Engineering, Warsaw University of Technology, Warsaw, Poland.

Graphene foams (GF) exhibit a high sorption capacity due to their high porosity and very low density, generally less than 0.01 g/cm³. Due to their diverse chemical nature, they may exhibit specific sorption activity against various gases. These properties can be used in the process of selective removal of individual gases from their mixtures. Graphene foams, due to their high sorption capacity, can be applied as storage tanks for various gases. In future GF can be widely used in the removal of various types of gaseous and liquid pollutants. Due to their high electrical conductivity GF
can be also used as an excellent carrier for electrocatalysts in various types of fuel cells as well as an excellent carrier for various types of metal and metal oxide nanoparticles used in catalytic chemical processes. GF due to its high porosity is also an excellent heat insulator resistant to high temperatures and an aggressive chemical environment. The authors of this presentation will present the synthesis process of various types of pure and doped graphene foams and characterize their physicochemical properties. The starting material for these synthesis is graphene oxide and reduced graphene oxide.

**PS1.25**

**Surface Enhanced Raman Scattering Based Molecular Sensors Enabled by Graphene Quantum Dots Templated Growth of Silver Nanoparticle Arrays**

Yonhwa Tzeng, JiuNchi Lai and YingRen Chen; Electrical Engineering, National Cheng Kung University, Tainan, Taiwan.

Plasmonic coupling induced enhancement in Raman scattering signal strength from laser illuminated molecules has been proven to be an effective means of detecting, indentifying, and quantify essential molecules for biomedical, environmental, and industrial applications. The enhancement factor of the stronger Raman scattering signal strength emitted from the same amount of molecules is achieved by local strong electric field at so-called hot-spots induced by plasmonic charge separation of closely spaced neighboring metal nanoparticles such as gold, silver, and copper. The key issues for excellent SERS sensors are the creation of high-density hot spots, the higher electric fields at hot spots, the placement of molecules at hot spots, the suppression of fluorescence background signal, and the collection of Raman scattering signal with a high signal to noise ratio. In this paper, novel SERS molecular sensors with Raman enhancement factors on the order of 10E14 for R6G and 10E9 for Adenine will be presented and discussed. The excellent performance of SERS molecular sensors has been made possible by the combination of fluorescence quenching by graphene and preferred closely spaced and irregular shaped silver nanoparticles grown between graphene nanoislands/ quantum dots. Practical applications of such high performance molecular sensors will be discussed.

**PS1.26**

**Tribological Properties on Carbon Nanotubes Containing Copper-Diamond Composite Films Deposited by Cold Spray Technique**

Nobuhisa Ata1, Nana Okimura1, Ryota Ohtani2, Hiroshi Uetsuka2, Naoto Ohtake1 and Hiroki Akasaka1; 1Mechanical Engineering, Tokyo Institute of Technology, Tokyo, Japan; 2Asahi Diamond Industrial Co., Ltd, Chiba, Japan.

The metal-based diamond composites have been used as whetstones because the diamond has the high hardness. On these metal-diamond whetstones, there are problems that high processing torque and worn out quickly when they process the hard metals are required. Thus, adding lubricant into metal-diamond composite can reduce energy consumption due to lower processing torque and increasing their tool life due to lower amount of wear. Carbon nanotube (CNT) have not only solid lubrication property but also high thermal conductivity. Whetstones are heated for high temperature by frictional heat during the grinding hard materials. Since, lubricants are also required high thermal conductivity to exhaust heat, CNTs are suitable as lubricants.

Cold spray (CS) is one of the process to prepare “mm” thick coatings from plastic material particles, directly. In addition, metal based composite films with high hardness materials can be obtained by a simple process using a mixture of plastic metal and high hardness particles. Thus, CS is able to fabricate metal-diamond composites without dies required conventional methods such as metallurgical processes, etc. In this study, CNTs containing copper-diamond composite films deposited by CS technique from mixture of copper, diamond particles and CNTs, and investigated the effect of CNT addition on tribological properties for the reduction of energy consumptions at materials processing. Copper particles with a mean diameter of 20 mm (HWQ 20: Fukuda Metal Foil & Powder Co., Ltd) were used as the matrix of the film. Diamond particles (IRM5, Tomei Diamond Co. Ltd.) with a mean diameter of 4-8 mm were used. Vapor grown carbon nanofiber (VGNF: Showa Denko Co., Ltd.) which mean diameter is 80 mm and \( f_{N} / f_{C} \) is 20 was used as CNT. Cu, diamond particles and CNTs were mixed by a coffee mill for 10 s. The concentration of the diamond particles and CNTs mixture was fixed at 2.4 and 0.5 wt.%. A1050 aluminum plates were used as substrates. The surface of the aluminum plate was processed by a sand blaster with white alumina particles (\#46, Fuji Manufacturing Co., Ltd.) to increase the surface area for improving the deposition efficiency. An advanced cold gas system (Medicoat Co., Ltd.) based on a DIMET 412-K cold spray system (TEIN TC Co., Ltd.) was used as the CS system. Acceleration gas was air with 0.64 MPa in pressure 723 K in temperature. The particle feed rate was maintained at 10 g/min. The distance between the end of the nozzle and the substrate surface was maintained at 12 mm. The scan speed and number of scan were 50 mm/s and 20, respectively. The copper-diamond film was also fabricated same conditions as the composites films for comparison. The friction coefficient of the samples were measured by Ball on Disc (BoD) test. The fabricated composite films surfaces were processed by milling machine and obtained flat space for the BoD test. SUJ2 ball with 6 mm diameter was conducted to BoD test. The load and the speed of rotation were maintained at 1 N, and 400 rpm. The maximum number of the rotations was 50000. The CNTs contained copper-diamond composite film with 500 mm in thickness was fabricated by the CS technique. As the results of BoD test, the mean friction coefficient of the CNT contained copper-diamond composite film was 0.56 and that of the copper-diamond composite film without CNT was 0.88. Thus, CNTs addition into the copper-diamond composite film can reduce the friction coefficient by approximately 36 %. Sliding marks on the SUJ2 ball was observed by laser microscopy to estimate the wear rates. Specific wear rates for the CNTs containing film and the non CNTs containing film were 3.3×10^-3 and 3.7×10^-4 mm^3/N m, respectively. There were no significant reduction in grinding efficiency by the CNTs addition into the copper-diamond composite films. These results suggested that adding CNTs into the copper-diamond composite film can reduce the processing torque without reduction of grinding ability.

**PS1.27**

**Graphene Synthesis Using Passivation of Porous Silicon by Carbon Atoms**

Kurbangali Tshastrybayev1, Aradik Aimabayev2, Oleg Kononenko3, Zamart Ramazanova2, Ramiz Zulkharnay2 and Zinetula Z. Insepov1,2,3; 1Nuclear Engineering, Purdue University, West Lafayette, Indiana, United States; 2Nazarbayev University, Astana, Kazakhstan; 3Condensed Matter Physics, National Research Nuclear University, Moscow, Russian Federation; 4IPTM, Moscow, Russian Federation.

Experimental data on the synthesis of graphene (Gr) and graphene oxide (GO) by acetylene passivation of porous silicon (PS) using a CVD method are presented. Various regimes of low-temperature synthesis of carbon nanocomposites Gr and GO on a PS surface are shown. By selecting a carbonization mode of the PS surface, it was possible to form spatially-oriented graphene and graphene-like structures in the temperature range of \( T = 350 - 500 \) °C. Various carbon nanocomposites on the surface of PS were obtained using the Raman and IR spectroscopy the formation, at three synthesis temperatures of 1050, 500, and 350 °C. Passivation of PS by carbon atoms open the way for fabrication of spatially oriented graphene with an architecture that repeats the PS topology. The proposed method allows synthesis of a large area Gr sheets with an extremely high surface area, which will significantly widen the scope of its application. Additionally, possibility of passivation of a PS surface, which has a high chemical resistance due to the presence of graphene layers, is discussed.

**PS1.28**

**The Properties and Potential Applications of High Color Carbon Black**

Sooyoul Park; Green Chemistry Process Research Division, Korea Research Institute of Chemical Technology, Yusung, Korea (the Republic of).

This is a function of the manufacturing process and the heat history of a carbon black and generally refers to the oxygen-containing groups present on a carbon black’s surface. For specialty carbon blacks, oxidized surfaces improve pigment wetting, dispersion, rheology, and overall performance in selected systems. In other cases, oxidation increases electrical resistivity and makes carbon blacks more hydrophilic. The extent of surface oxidation is measured by determining the quantity of the “volatile” component on the carbon black. High volatile levels are associated with low pH. In our works, carbon black was surface-modified to introduce hydroxyl groups or carboxyl groups such as organic acids (nitric acid, sulfonic acid) on the surface. The surface-modification of carbon black was confirmed by FE-SEM and FTIR. Also, color properties of carbon black are measured using colorimeters and have values of \( L, a^*, b^* \). The “Lab” value can be correlated to the ratio of particle size to surface area and is a useful tool for comparing competitive grades of carbon black.
P-type surface conductivity of diamond can be readily achieved by surface transfer doping. It provides an alternative strategy to enable high power and high frequency diamond FET operation. Recent studies have reported surface transfer doping on diamond using various high work function activation compounds, such as MoO$_3$, V$_2$O$_5$, Al$_2$O$_3$, etc. For materials with high electron affinity (Ea>4.3 eV), their lowest unoccupied molecular orbitals are below the valence band maximum of H-terminated diamond, such that electron transfer from the diamond to the oxides is energetically favorable. While a higher work function of the oxide leads to a higher sheet hole concentration at the diamond surface, the hole mobility is found to decrease which limits high frequency operation. It is thought that the charge transfer negative ions distributed inhomogenously near the interface give rise to Coulomb scattering in the hole accumulation layer. The lack of controllability of the induced hole concentration and the reduced mobility limits the application of surface transfer doping in diamond electronic devices. In this work, the hole concentration and mobility is modulated by affecting the distance between the hole accumulation layer in diamond and the negative ions in the oxide layers.

The surface conductive diamond was achieved with MoO$_3$ as an acceptor layer and Al$_2$O$_3$ as an interfacial layer. The Al$_2$O$_3$ layers were deposited by plasma enhanced atomic layer deposition (PEALD) on hydrogen-terminated, undoped diamond (100) surfaces, immediately followed by a remote hydrogen plasma treatment. A molybdenum layer was deposited using electron beam deposition (MBD), and the MoO$_3$ oxidation state was achieved with an oxygen plasma treatment. Using Hall measurements, the diamond sheet resistance, hole concentration and mobility were characterized with Al$_2$O$_3$ interfacial layers of different thickness. The changes of the band bending and the hole accumulation layer were monitored using in situ X-ray photoelectron spectroscopy (XPS) where the binding energy of the diamond C 1s core level was correlated with electrical measurements. The valence band offsets are found to be 2.7±0.2 and 3.1±0.2 eV for Al$_2$O$_3$/H-terminated diamond and MoO$_3$/diamond, respectively. With MoO$_3$ deposited on Al$_2$O$_3$, the Al 2p core level shifted to lower binding energies, indicating that the original negative charges close to diamond surface transfer into the MoO$_3$ layer. The increase of Al$_2$O$_3$ interfacial layer thickness adds to the distance between the hole accumulation layer and the negative ions, and apparently reduces the ionic scattering leading to an increase of hole mobility. Conversely, the hole concentration decreases which may be ascribed to a lower efficiency of surface transfer doping. By combining two oxides (Al$_2$O$_3$ and MoO$_3$ in this case), the hole mobility and concentration were modulated by altering the thickness of the interfacial layer. This work provides a strategy to achieve a surface conductive diamond surface with optimized hole concentration and mobility. This research is supported by a grant from MIT-Lincoln Laboratories and National Science Foundation (DMR – 1710551).
The H-terminated surface of diamond when activated with NO₂ forms a highly conductive surface layer. This activated surface was used to make field effect transistors (FETs) with drain currents > 1 A/cm². However, the conductance of NO₂-activation diamond decreases over time. Previous reports have suggested that during NO₂ exposure (NO₂-activation), NO₂ forms on the diamond surface and generates positive carriers (holes) in the diamond, making the diamond surface conductive. Evaporation of NO₂ from the diamond is reported to be responsible for the loss of conductance. We report here on x-ray-photoelectron-spectroscopy (XPS) surface characterization of single crystal diamonds and on infrared absorption of diamond powder. After activation, XPS showed the presence of N atoms on the diamond surface, but infrared absorption found no evidence of the nitrite ion (NO₂⁻), but instead the nitrate ion (NO₃⁻). Two wet chemistry techniques determined the concentration of NO₂⁻ per milligram of diamond powder. With the powder’s surface area measured by the BET technique, the surface NO₂⁻ concentration was measured to be between 6.2x10¹⁹ and 8.2x10¹⁹ cm⁻². This is in the same range as the carrier densities, 3x10¹⁹ to 9x10¹⁹ cm⁻², determined by Hall mobility and surface conductivity measurements of single crystal diamonds. Using similar techniques, the concentration NO₂⁻ was determined to be below the detection limit, < 10¹⁷ cm⁻². NO₂ activation was observed to decrease the surface concentration of H, presumably by reacting with NO₂. This affects the surface conductance is unknown. Other oxidizing chemistries (O₂, WO₃, and V₂O₅), also chemically react with the H-terminated diamond surface with comparable effect. Contrary to an evaporation theory, both the surface conductance and the surface H atoms are stable (+/- 10% over a week) when stored in dry nitrogen, with or without NO₂-activation. However, surface conductance and the concentrations of NO₂⁻ and H decrease when exposed to laboratory air over a period of hours to days. Infrared absorption measurements showed the reduction of surface NO₂⁻ and H atoms during laboratory air exposure, but gave no indication of what reactions are responsible for their loss in laboratory air. Stabilizing diamond’s NO₂⁻-activated conductance will not be obtained by reducing the evaporation of NO₂, but by protecting the diamond surface from atmospheric contaminants. This presentation will discuss surface activation as well as possible encapsulation techniques. This material is based upon work supported by the Assistant Secretary of Defense for Research and Engineering under Air Force Contract No. FA8721-05-C-0002 and/or FA8702-15-D-0001. Any opinions, findings, conclusions or recommendations expressed in this material are those of the author(s) and do not necessarily reflect the views of the Assistant Secretary of Defense for Research and Engineering.

9:00 AM A1.02

Increasing the diameter and crystallinity of the diamond substrate is important for research and development activities of diamond semiconductors. Heteroepitaxial diamond growth method has a high potential to obtain a large-size diamond substrate compared to other growth methods of that. Due to the difference of the thermal expansion co-efficient between diamond and basal (such as MgO) substrate material, crack generation and random delamination are generated in the diamond film during the cooling process from the diamond growth temperature to RT. Therefore, it is very difficult to enlarge the diameter of the substrate. We have reported growth method in detail, where fabrication of the freestanding heteroepitaxial diamond substrate via microneedles prevent the crack generation and the delamination. Microneedles play a role as the buffer or shock absorption, and a large-size diamond substrate of 10mm ×10mm was achieved. Production of large-size diamond crystals is challenging because of two reasons: (1) the diameter of the commercially available MgO substrate is limited up to 1-inch. (2) its cost increases exponentially increases with the diameter of the MgO substrate. Although the hexagonal crystal structure of sapphire is different from a cubic structure of diamond and iridium, the sapphire substrate is another candidate because of its chemical stability, size, and cost-effectiveness. Therefore, heteroepitaxial diamond growth on the sapphire substrate instead of MgO substrate was demonstrated. The conventional process for heteroepitaxial diamond growth on the MgO substrate was applied to the A-plane sapphire substrate size of with 10mm × 10mm. The grown crystal was grown without any cracks and breakage. The thickness of the diamond crystal was 800µm. The as-grown diamond crystal was characterized by X-ray diffraction (XRD) and Raman spectroscopy. The diamond [111] X-ray pole figure shows four fold symmetry with four sharp peaks at w≈ 55°, indicating that the freestanding diamond has a single-crystal structure without polycrystalline inclusions or misoriented blocks. Furthermore, as a result of X-Ray Rocking Curve measurements, the crystallinity was improved for both (400) and (311) compared to the case that of the MgO substrate. Heteroepitaxial diamond growth on the 1-inch A-plane sapphire substrate was successfully demonstrated in the same manner. A comprehensive comparison between the diamond growth methods on MgO substrate and on the sapphire substrate will be discussed.

9:15 AM A1.03
Room-Temperature Direct Bonding of Diamond to Aluminum Jianbo Liang¹, Shoji Yamajo¹, Martin Kuball1 and Naoteru Shigekawa1; 1Osaka City University, Osaka, Japan; 2University of Bristol, Bristol, United Kingdom.

Power electronics semiconductor devices such as metal oxide semiconductor field effect transistor (MOSFET), bipolar junction transistor (BJT), insulated gate bipolar transistor (IGBT), high electron mobility transistor (HEMT) etc. are extensively used in home electronics, telecommunications, transport, electric grid and numerous other applications. The high operating power density in such devices commonly produces an increase in temperature near the active region, which would degrade device performance and reliability. Therefore, the suppression of the temperature rise is particularly important to increases the operational power density. Diamond has the highest thermal conductivity among materials and is an ideal materials to suppress the rise in the device temperature. The application of diamond substrate to the fabrication of the devices is attracting much attention due to its superior heat transfer property, compared to that of Si, sapphire or SiC substrates. The integration of GaN-based devices and diamond by direct growth and wafer bonding has recently been demonstrated, resulting in improved thermal management and three-fold increase in areal power density. For any device, an effective thermal boundary resistance exists between the device and the heat sink, which is a significant thermal barrier for heat transfer from the devices to the heat sink. The device was directly mounted onto the heat sink by solder bonding. However, the thermal conductivity of the solder materials such as AgSn and AuSn are very low in comparison with that of diamond. In this work, we bonded polycrystalline diamond substrates to aluminum at room temperature by surface activated bonding (SAB) and investigated the structural properties and the bonded strenght of the interfaces. A straight line can be clearly observed at the center of STEM images of the diamond/Al bonded interfaces, which corresponds to the bonded interface. No structural deficits or hollow spaces as cracks were observed at the interface. The obtained results indicate that SAB method is applicable for bonding diamond with dissimilar materials at room temperature. Reference 1. L.S. Pan and D. R. Kania, Diamond: Electronic Properties and Applications (Springer, London, 1995). 2. H. Sun, R. B. Simon, J. W. Pomery, D. Francis, F. Faili, D. J. Twitchen, and M. Kuball, Appl. phys. Lett. 106, 111906 (2015). 3. D. Francis, F. Faili, D. Babic, F. Ejeckam, A. Nurmkikko, and H. Maris, Diamond Relat. Mater. 19(2), 1525-1532 (2012). 4. M. Kuznetsov, F. Hakimi, R. Sprague, and A. Mooradian, IEEE Photonics Technol. Lett. 9, 1063 (1997). 5. J. Liang, S. Masuya, M. Kasu, and N. Shigekawa, App. Phys. Lett. 110, 111603 (2017).
9:30 AM A1.04

Due to excellent mechanical, chemical and biological stability and the widest potential window among natural materials, diamond is an ideal material choice in the applications of sensors, supercapacitors, catalysts, or solar energy conversion etc. Large surface area of a diamond electrode could significantly elevate the device’s performances such as high sensitivity in a sensor, high power density in a supercapacitor, high efficiency on a catalyst interface, or higher conversion rate in a solar cell. However, realizing a large surface area of diamond is more challenging than fabricating a large surface area of any other carbon allotrope such as activated carbon or graphene. Herein we report a special diamond structure, so-called diamond nanofeather which is highly porous with large surface area. The nanostructure is realized by removing the relatively more instable sp³ carbon content from the grain boundaries of doped NCD (nanocrystalline diamond) or UNCD (ultrananocrystalline diamond) via a optimized electrochemical etching process and by leaving the pure sp² carbon structure. Since NCD and UNCD have very high density of the grain boundary compared to other polycrystalline diamonds, after the sp³ carbon is removed from the grain boundaries, a large number of nano-vacancies and hence large surface area is generated. Further chemical or other oxidation of sp³ through these vacancies can adjust the size of the nano pores to meet an optimized diamond-pore ratio to meet surface area requirement for specific applications. The nanofeather structure also helps us revisit the mechanism of NCD and UNCD deposition from a new perspective.

9:45 AM A1.05
DISCUSSION TIME

10:00 AM BREAK

10:30 AM *A1.06
Thick Homoeptaxial Layer Growth—A New Approach to Obtain Desired Substrates Tokutoki Teraji; National Institute for Materials Science, Tsukuba, Japan.

Selection of suitable diamond substrates is important for fabricating high-performance devices. However, single crystal substrates being suitable for each device is sometimes difficult to obtain. Alternative way to prepare these substrates is to grow thick diamond layer with desired function on the generally-used substrates. The thicker the homoeptaxial layer is, the smaller an effect of original substrate becomes [1]. Then, the growth technique of functionalized (super high purity, isotopically-enriched, and so on) diamond layer becomes considerably important. We recently found the growth conditions being optimized for long-duration homoeptaxial diamond growth; formation of non-epitaxial crystallites is effectively suppressed by adding oxygen in the source gas [2]. This growth condition is suitable to accomplish the purpose mentioned above. In this talk, some examples that indicate advantage of the thick layer deposition will be presented. References T. Teraji, T. Yamamoto, K. Watanabe, Y. Koide, I. Isoya, S. Onoda, T. Ohshima, L.J. Rogers, F. Jelezko, P. Neumann, J. Wrachtrup, S. Koizumi, Homoeptaxial diamond film growth: high purity, High crystalline quality, isotopic enrichment, and single color center formation, Phys. Stat. Sol. (a) 212, 2365 (2015). T. Teraji, High-quality and high-purity homoeptaxial diamond (100) film growth under high oxygen concentration condition, J. Appl. Phys. 118, 115304 (2015).

11:00 AM A1.07
Improvement of CVD Diamond on Chemical Mechanical Polished Diamond Substrate Dukui Fujii¹, Satoshi Masuya¹, Koki Oyama¹, Hitotose Takeda¹, Yutaka Kimura¹, Seongwoo Kim¹ and Makoto Kasu²; ¹Adamant Namiki Precision Jewel Co., Ltd., Adachi-ku, Japan; ²Department of Electrical and Electronic Engineering, Saga University, Saga City, Japan.

Diamond can be used for wide range of applications, not only for jewelry. Diamond has a lot of attentions to be an ultimate semiconductor material because of its physical properties like as the wide band gap and high carrier mobility. The ultimate semiconductor devices, such as high frequency device and high-power transistor, are also expected application by these physical properties [3]. In semiconductor device fabrications, damage- and roughness-free substrate surface is essential. For this purpose, in conventional semiconductors, chemical mechanical polishing (CMP) is widely used. However, in diamond there are very few reports of CMP. In this work, we perform CMP on single-crystal diamond substrates and investigate its effect on the surface properties. The samples were HPHT single crystal diamond (001) (~4 x 4 x 0.5 mm³). First, all the surfaces were mechanically polished (MP) to adjust the thickness, the off angle, the roughness. Next, CMP was performed on the diamonds with different processing time: 0 h (MP only), 5 h, 50 h, and 100 h. The surface roughness before DC plasma CVD growth was less than 0.2 nm. Finally, the diamond films were homoepitaxially grown on the MP and CMP-treated diamond substrates for 10 hours by DC-plasma CVD method. In synchrotron radiation X-ray section topography observation, we have found different contrast between the substrate subsurface with and without CMP. Further, we confirmed pits on the CVD diamond surface grown on the substrate without CPM. However, as the CMP process time increased, the pit density decreased. Eventually, on the surface for 100 h CMP, no pits were observed. From these results, we concluded that the subsurface damage leads to pit formation in homoepitaxial growth, and CMP on the substrate is effective to prevent pit formation in CVD diamond growth. 1) H. Aida et al., Appl. Phys. Express 9, (2016) 035504. 2) M. Kasu et al., Appl. Phys. Express 5, (2012) 025701.

11:15 AM A1.08
Homoeptaxial Growth of High Quality Single Crystal Diamond by Introducing a Buffer Layer Guoqing Shao, Renan Bu, Zangcheng Liu, Wei Wang and Hongxing Wang; Xi’an Jiaotong University, Xi’an, China.

Due to its excellent properties such as wide band-gap, high carrier mobility, low dielectric constant, high radiation hardness and high thermal conductivity, diamond is considered as a feasible candidate for next generation semiconductor material. The high quality thick diamond substrate has relied on synthesis under the high pressure high temperature (HPHT) and microwave plasma chemical vapor deposition (MPCVD) techniques. These diamond growth methods were mostly driven by highly promising application in high-power, high-frequency electronic device, quantum technologies, optical windows, jewellery and mechanical tools. The effects of growth temperature, gas composition, substrate holder and pressure are very important in the growth of diamond morphology, quality and specific electronic properties. However the presence of extended defects and mismatch strain are still a major issue in diamond growth. The buffer layer was introduced during the deposition to improve the quality of epitaxial film by releasing the mismatch stress and preventing threading dislocations extends to the epitaxial layer. In this work, the introduction of preferred orientation polycrystalline diamond (POPCD) buffer layer were grown on HPHT (100) single-crystal diamond (SCD) substrate, and then the SCD layer were grown on POPCD buffer layer by the choice of suitable growth parameters in MPCVD reactor. The structure and morphology of POPCD buffer layer and SCD epitaxial layer were revealed using scanning electron microscopy (SEM) and high resolution transmission electron microscopy (HRTEM). The quality and residual stress of diamond was investigated by X-ray diffraction and Raman spectroscopy. To measure the dislocation densities of HPHT substrate and epitaxial diamond layer, the etch pits were formed by H/O plasma in MPCVD reactor. We have also revealed the growth scheme of diamond to illustrate how continues diamond films were grown on POPCD buffer layer. Our reports provide a novel strong feasibility for applying this concept in heteroepitaxial growth of diamond. The details will be presented at the conference.

11:30 AM A1.09
Bulk Crystal Growth for Realization of Inch-Size Single-Crystal Diamond Wafers Hideaki Yamada, Akiyoshi Chayahara, Shinya Ohmagari, Yuki Asahara and Yoshiaki Mokuno; ADPARC, AIST, Osaka, Japan.

For realization of several future applications of diamond, it is indispensable to establish technique to fabricate inch-size wafers. In addition to growth and processing techniques for such a large size wafers, preparation of the seed wafers with the same size is perquisite condition. Recently, inch size bulk crystals were achieved by using the HPHT method [1]. In the case of microwave plasma (MWP) CVD, deposition area could be 2inch diameter for frequency 2.45GHz, and 4-inch size could be grown by up-scaling the conventional apparatus with lower
frequency. One may be able to obtain several inch size wafers in principle. We reported a 2inch size mosaic diamond wafer by using MWPVD [2], but the size of the constituent mono-crystal diamond plates is still limited to half inch [3]. We studies techniques to prepare bulk crystal by using MWPVD and obtained several millimeter size bulk crystal. Observation of the cross section of several millimeters thick crystal shows that quality saturate into a certain level for a certain thickness by introducing Oxygen into the source gas mixture and adopting pulse mode discharge. We have achieved to continue the growth for several hundred hours, and to reduce interfaces among the growths, from which defects are generated. [1] A. Katrusha, ICDCM 2017. [2] H. Yamada, et al., Appl. Phys. Lett. 104 (2014) 102110. [3] Y. Mokuno, et al., Diamond and Related Materials 18 (2009) 1258.

11:45 AM A1.10 High Pressure Synthesis of Boron Nitride Crystals and Impurity Controls for Their Functionalizations Takashi Taniguchi; High Pressure Group, National Institute for Materials Science, Tsukuba, Japan.

Hexagonal boron nitride (hBN) is chemically and thermally stable, and has been widely used as an electrical insulator and heat-resistant materials. Cubic BN (cBN), which is a high-density phase, is an ultra-hard material second only to diamond. The color of the cBN crystals were always amber or brownish so far which is attributed by carbon and oxygen impurity. After some struggles for high pressure and high temperature (HPHT) solution growth, we could find suitable solvent of Ba-BN system which gave us almost colorless cBN with band-edge nature[1]. At the same time, high purity hBN crystals were recovered in the same HPHT capsule and their attractive potential as a wide-band gap material was realized. It is emphasized that hBN crystals exhibits superior properties as ultra violet light emitter[2] as well as a substrate of graphene devices[3]. On the other hand, cubic boron nitride and diamond heterojunction crystals can be obtained under HPHT and their interface structure was realized[4].While the current subject is to realize how the major impurities such as carbon and oxygen affect the properties of hBN and cBN, some progresses for the realization for the application of 2D substrates and photonic materials have been achieved. Also, controlling of boron and nitrogen isotope ratio (10B,11B and 15N) in hBN and cBN crystals can be now carried out by methathesis reaction under HPHT.In this paper, our recent studies on hBN and cBN single crystals growth under HP with respect to impurity / isotope controles and their functionalizations will be reported. [1] T.Taniguchi, K.Watanabe, J.Cryst.Growth , 303,525 (2007). [2] K.Watanabe,T.Taniguchi,A.Niyama,K.Kiya, M.Taniguchi, Nature Photonics 3, 591(2009). [3] C.R. Dean, A.F. Young, I. Meric, C. Lee, W. Lei, S. Sorgenfrei, K Watanabe, T. Taniguchi, P. Kim, K.L.Shepard, J. Hone, Nature Nanotechnology, 5,722 (2010). [4] C.L. Chen, Z.C.Wang, T. Kato, N.Shibata, T.Taniguchi, Y.Ikuhara, Nature Commun. 6, 6327 (2015).

G2: Graphene and 2-D Materials II Session Chair: Jimmy Davidson Tuesday Morning, May 22, 2018 Room: Agassiz/Fremont

8:30 AM G2.01 Novel Approach to Synthesize High Quantum Yield Nitrogen-Doped Graphene Quantum Dots Muhammad Shehzad Sultan1, Vladimir I. Makarov2, Frank Mendoza3, Wojciech M. Jadowszczak4, Muhammad Sajjad5, Brad Weiner6 and Gerardo Morell7; 1Physics and Astronomy, Western Kentucky University, Bowling Green, Kentucky, United States; 2Nazarbayev University, Astana, Kazakhstan; 3Condensed Matter Physics, National Research Nuclear University, Moscow, Russian Federation; 4Condensed Matter Physics, National Research Nuclear University, Moscow, Russian Federation; 5Condensed Matter Physics, National Research Nuclear University, Moscow, Russian Federation; 6Nazarbayev University, Astana, Kazakhstan; 7Condensed Matter Physics, National Research Nuclear University, Moscow, Russian Federation.

The graphene quantum dots (GQDs), a zero-dimensional graphene quantum structure, have triggered an intense research worldwide. GQDs possess unique optical, chemical and physical properties as compared to conventional quantum dots (QDs), such as low toxicity, biocompatibility, optical stability, chemical inertness, high photo-stability and good water-solubility and therefore hold great application potential in biomedical, optoelectronics and energy storage devices. The doping of GQDs with heteroatoms is one of the most effective ways to tune their photoluminescence emission and to increase quantum yield. In this study, we developed a novel approach to synthesize high-quality Nitrogen-doped graphene quantum dots (N-GQDs) with high quantum yield, via irradiation of s-triazene in a solution with benzene by using pulsed laser. The TEM, HRTEM, XPS, Energy Dispersive Spectroscopy (EDS), Raman spectroscopy, FTIR, XRD were carried out to observe the morphology, size distribution, crystalline structure and to prove successful doping of GQDs with nitrogen atoms. To observe optical properties of as synthesized N-GQDs, the UV-vis and Photoluminescence measurements were carried out. The as-synthesized N-GQDs exhibit high quality crystalline structure of graphene with an average size of about 3.7 nm. A high quantum yield was exhibited by the obtained N-GQDs as compare to the pristine GQDs. The obtained N-GQDs with oxygen-rich functional groups exhibit a strong emission at 456 nm. These outcomes result in an ample opportunity for the biomedical and optoelectronic applications.

8:45 AM G2.02 Large-Area Membranes and Mesoporous Capacitive Deionization Electrodes from Graphene—A Breakthrough in Water Desalination Sanju Gupta; Western Kentucky University, Bowling Green, Kentucky, United States.

The development of scalable cost-effective robust and resistant to biofouling membranes would have a profound and direct impact on current commercial and emerging markets for water detoxification. In this work, we developed large-area nanofiltration membranes using (1) sheet aligned discotic nematic phase of graphene oxide and (2) holey graphene with narrow hole size distribution via controlled metal catalytic oxidation. We also prepared interconnected network of mesoporous graphene-based ‘hybrid’ electrodes with carbon nanotubes to achieve optimal desalination during capacitive deionization (CDI) of brackish water, attributed to higher specific surface area, electrical conductivity, good wettability of water, environmentally safe, efficient pathways for ion and electron transportation, as potential successor of current filtration membranes. The pressure driven transport data on highly ordered (nanoslit and nanopore), continuous, thin films of multi-layered graphene oxide and holey graphene is expected to demonstrate faster transport of ions for salt water, higher retention for charged and uncharged organic probe molecules with hydrated radii above 5Å as well as modest retention of mono- and di-valent ionic species in salts for ~150 nm thick membranes. The highly ordered graphene nanosheets and hierarchical porous (mesoscale and nanoscale) graphene in the plane of the membrane make organized, molecule-hugging cylindrical and spherical channels, respectively, thus enhance the permeability and hydrodynamic conductivity. The results illustrate that both the meso and nanoscale pores are favorable for enhancing CDI performance by buffering ions to reduce the diffusion distance from external electrolyte to the interior surfaces and enlarging surface area. The findings demonstrated the feasibility of the graphene-based membranes and electrodes compared to currently existing conventional polymeric and ceramic-based technology. Supported by KY NSF EPSCoR Grant.

9:00 AM G2.03 Nanoporous Graphene Film Fabrication with Cluster Ion Beams Zinetula Z. Insepetsov1,2,3, Ardak Ainabayev4, Aidyn Shaikhov5, Abat Zhuldassov6, Zamart Ramazanova7, Sean Kirkpatrick8 and Michael Walsh9; 1Nuclear Engineering, Purdue University, West Lafayette, Indiana, United States; 2Nazarbayev University, Astana, Kazakhstan; 3Condensed Matter Physics, National Research Nuclear University, Moscow, Russian Federation; 4Exogenesis Corporation, Billerica, Massachusetts, United States.

Density-functional theory (DFT) was used for studying the number of layers of a several layer graphene (SLG). Large-scale parallel molecular dynamics (MD) simulations (Lammps) were employed for studying interactions of accelerated cluster ions with ultrathin films, such as graphene, MoS2, HOPG, and BN. Graphene was grown by CVD on a Ni (111) surface from acetylene and transferred to a Si surface. Graphene oxide was synthesized using a Hummers’ method. Argon gas cluster ions were produced by nAccel accelerator, with total energy of E = 30 KeV, average cluster ion sizes between 1×103 and 1×104 cm. (Exogenesis Corp, MA USA). The Raman spectroscopy (Horiba) study of the irradiated samples was...
conducted by a 632 nm laser wavelengths and 100x objective with a laser spot size of ~1 μm, 2 mW power and atomic force microscopy (AIST NT) measurements were carried out in a tapping mode by SUPERSHARP SILICON™ AFM probes for high resolution. Our DFT simulation results were validated with the Raman spectra of several layers of graphene (SLG). The MD simulations showed formation of nanometer-sized holes in the 2D films irradiated with Ar, with acceleration energies of E = 1 - 50 eV/atom. The MD results showed formation of uniform holes, with the diameters of 10-20 nm, on the ultrathin films, and were used for optimization of the experimental fabrication of holes in 2D-films. The computer simulation results were confirmed with irradiation experiments, where Ar gas cluster ions were used to bombard graphene, graphene oxide, HOPG, MoS2 and BN 2D-films, with total cluster ion energy of 30 KeV. Uniformly distributed holes, several nanometers in diameters, were experimentally observed by atomic force microscopy (AFM) for the first time. Raman spectra were experimentally observed on the irradiated vs non-irradiated samples and calculated using a density-functional theory (DFT) method.

9:15 AM G2.04
(Late News) Defect Mediated Transport in the Reverse I-V Characteristics of Diamond-Based PIN Diodes Mehdi Saremi1, Raghuraj Hathwar1, Maitreyi Dutta2, Franz A. Koeck3, Robert J. Nemanich1, Srebrani Chowdhury1 and Stephen M. Goodnick1; 1Department of Electrical Engineering, Arizona State University, Tempe, Arizona, United States; 2Department of Electrical Engineering, University of California, Davis, Davis, California, United States; 3Department of Physics, Arizona State University, Tempe, Arizona, United States.

Diamond is one of the most promising candidates for high power and high temperature applications, due to its large bandgap and high thermal conductivity. In particular, the large bandgap of diamond compared to other materials such as GaN and SiC, should result in commensurately higher breakdown voltages when the limiting current mechanism is band to band impact ionization, with breakdown fields expected on the order of 10 MV/cm. However, as a result of the growth and fabrication process of diamond-based devices in this emerging technology, structural defects such as threading dislocations (TDs) may degrade the electrical properties of such devices, by providing a leakage path for current leading to unwanted excess current. Understanding and control of such defects are important for improving device technology particularly the reverse breakdown characteristics. Here, we have analyzed the voltage and temperature dependent behavior of the reverse bias current-voltage characteristics in diamond PIN diodes, grown by microwave plasma enhanced chemical vapor deposition (MPCVD) on high pressure high temperature (HPHT) single crystal diamond substrates. Over a range of temperatures from 323 K to 423 K, the reverse current can be described by combination of hopping conduction at low bias and Poole-Frenkel emission (PFE) at higher bias, which is hypothesized to occur through TDs assuming typical values of the TD density found in epitaxial grown material.

9:30 AM G2.05
(Late News) Single Crystal Diamond Deposition by Toroidal Plasma CVD Amanda Charris, William Holber, Robert Basnett, Andrew Basnett, Doug Hansel and Adam Brown; Plasmability, LLC, Austin, Texas, United States.

As an alternative to microwave plasma reactors typically used for chemical vapor deposition (CVD) of diamond material, we have been investigating for several years the use of a toroidal plasma reactor. The toroidal reactor operates with a 400 kHz power source operating at up to 11 kW of coupled power. The plasma shape is a line source, so that it is ideal for growth of single crystal diamond on multiple seeds places along the line of plasma. Samples can be retracted during the growth process, so that the growing surface can be kept at all times at an optimum distance relative to the plasma core. A wide range of process parameters have been investigated, with the aim of optimizing growth rate, growth quality and chamber cleanliness. Work will be described that improves the quality of the bulk diamond material by eliminating growth defects and minimizing polycrystalline material at the edges. Single crystal diamonds are grown on 5 mm x 5 mm and 7 mm x 7 mm CVD (100)-oriented diamond seeds. The growth rate for high quality single crystal diamond was in the range of 30 mm/hr to 70 mm/hr. The local growth environment at the seed is controlled by adjusting (1) chamber configuration and (2) gas flow injection. This work is carried out in part under support from Army Research Laboratory SBR Contract W911QX-16-P-0222.

10:00 AM BREAK

E2: Characterization II
Session Chair: Yasuo Koide
Tuesday May 22, 2018
Room: Agassiz/Fremont

10:30 AM E2.01
New Insights into Identification of Carbon (C 1s) Peak in X-Ray Photoelectron Spectroscopy Analysis of Crystalline and Polycrystalline Diamond and Associated Effects from Argon Atoms Insertion in the Lattice Jean-Francois Veyan1, Elda de Obaldia2, Jesus J. Alcantar-Peñas3, Jorge Montes-Gutierrez4, Maria A. Arellano-Jimenez5, Zaibing Guo6, Husam N. Alshareef7, Miguel J. Yacaman8 and Orlando Asuello9; 1Materials Science and Engineering and Bioengineering, The University of Texas at Dallas, Richardson, Texas, United States; 2Department of Physics and Astronomy, University of Texas at San Antonio, San Antonio, Texas, United States; 3Materials Science and Engineering, Florida Atlantic University, Thuwal, Saudi Arabia; 4Materials Science and Engineering, King Abdullah University of Science and Technology, Thuwal, Saudi Arabia.

The C 1s peak’s electron binding energy in X-ray photoelectron spectroscopy (XPS) analysis of crystalline diamond and diamond films has been extensively investigated. The splitting of the C 1s peak is usually reported as the combination of C 1s/sp2 and C 1s/sp3 bonding in the sample. In this work, we present a systematic study of polycrystalline diamond films and single crystal diamond (SCD) via XPS analysis, with special focus on clarifying critical analysis issues related to the identification of the C 1s/sp2 and C 1s/sp3 positions in the XPS electron binding energy coordinate, which appear confusing from prior work in the literature, potentially due to problems related to sample charging. The systematic XPS analysis of polycrystalline diamond films and SCD described here, demonstrated that the charging of the insulating diamond surface, resulting from X-ray induced electron emission, introduce substantial uncertainty to unmistakably identify the position of the C 1s peaks related to the sp2 and sp3 C atoms bonding of diamond and graphite, respectively. In addition, the work reported here demonstrated that the use of Ar+ ion bombardment,
generally done to clean the samples surface, introduces another uncertainty in the identification of C 1s XPS peak in the low binding energy position, as the sp2 C atoms bonding of graphite, as generally reported in the literature in relation to XPS analysis of diamond surfaces cleaned by Ar+ ion bombardment. The detailed XPS analysis of Ar+ ion bombarded diamond samples shows that the C 1s is identified as correlated with the sp2 C atoms bonding of graphite, is, in reality, the result of Ar atom incorporation in the diamond lattice formed by sp2 C atoms bonding. In fact, the low energy C 1s peak identified in this paper as Csp2 peak, corresponds to C atoms associated to the Ar atoms inserted in the diamond lattice during Ar+ ion bombardment surface cleaning. The correlation of the Csp2 peak and the Ar+ beam energy as well as the concentration of Ar atoms inserted in the diamond lattice is discussed. The incorporation of Ar atoms in the diamond samples have been confirmed via complementary high resolution transmission electron microscopy (HRTEM) and nanoscale resolution Rutherford backscattering (RBS) analysis, the latter showing that the Ar atoms are inserted through a 2 nm layer depth from the surface.

10:45 AM E2.02 Spectroscopic Characterisation of Single Point Defects in Single-Crystal Boron Doped CVD Diamond Phil L. Digele1,2, Ben L. Green2, Matthew L. Markham1, Daniel J. Twitchen3 and Mark E. Newton4,5; 1University of Warwick, Coventry, United Kingdom; 2Diamond Science and Technology Centre for Doctoral Training, Coventry, United Kingdom; 3Element Six (UK) Ltd., Didcot, United Kingdom.


11:00 AM E2.03 Superconductivity in Thin- and Micro-Structured Boron-Doped Diamond Taisuke Kageura1, Masakuni Hideko1, Itako Tsuyuzaki1, Shota Amano1, Yoshihiko Takano2, Minoru Tachiki3, Syuichi Ooi3 and Hiroshi Kawarada1, Waseda University, Tokyo, Japan; 2NIMS, Tsukuba, Japan; 3Kwansei Gakuin University, Sanda, Japan.

Superconducting electronics is expected to be applied to quantum computing, high sensitive magnetic field sensing and microwave filter, searching for superconducting materials suitable for application is an urgent research topic. A low temperature superconductor made of a non-oxide material is desirable for a high-performance, complexed and integrated superconducting devices. Superconducting boron-doped diamond is excellent materials for these superconducting devices because it is mechanically, thermally and electrochemically stable, does not deteriorate over time in performance, and the superconducting temperature (Tc) can be controlled by doping concentration[1]. However, there are few reports for evaluating the superconducting properties from the viewpoint of manufacturing a superconducting devices. So in this study, we report the superconducting properties of thin and micro-structured boron-doped diamond with Tc=10K. First we investigated the doped layer thickness dependence of Tc. The superconducting boron-doped layer were synthesized by custom-built wave-guide type MPCVD system. In this study, two types of gas introduction method at the start of synthesis were examined. The first method (conventional method) is to simultaneously supply methane and tri-methyl-boron (TMB) gas at the start of synthesis. The second method (new method) is to decompose TMB by plasma in advance and supply methane thereafter. The latter intends to improve boron incorporation efficiency in the early stage of synthesis. The sample synthesized by conventional method shows that Tc(offset) is 10K above 500nm, but it decreases as the doped layer becomes thinner below 500nm region. On the other hand, the sample synthesized by new method shows that Tc(offset) is 10K even if the thickness become 100nm, and the sample with 42nm thickness has Tc(offset)=7.8K. The obtained results are compared with the theoretical equation about thickness dependence of Tc generally applied to superconducting materials such as Nb [2]. The experimental value coincided with the theoretical equation up to about 100 nm, however the experimental value tended to be lower than the theoretical formula as the film thickness became thinner. This is in good agreement with the film thickness which the boron concentration saturates (conventional: ~200 nm, new: 100 nm). So it is said that the new method is effective for improving boron incorporation efficiency in the early stage of growth. And this results also demonstrated that Tc = 10 K can be obtained up to a thickness of 100 nm or more even if the growth thickness is below critical film thickness (about 200-300 nm) at which crystal defects are introduced due to lattice mismatch between the substrate and the doped layer. Then we evaluated the line width dependence of Tc using thin (160nm) film. Superconducting diamond line (-100μm) were formed by oxygen plasma selective etching of the superconducting diamond film with Tc(onset) and Tc(offset)=9.5K, 9K. Here, Tc (onset) / Tc (offset) are defined as the temperature which the normalized resistivity R (T) / R (300 K) reaches 90%/ 10%, respectively. Experimental results revealed that both Tc (onset) and Tc (offset) did not decrease even if the line width was 1 μm. This means that diamond has high workability in fabricating a fine superconducting device. One interesting point is that 1 μm sample shows strange two-step transition, the first transition occurred at 9.5K and the R (T) / R (300 K) becomes below 1%, then second transition occurred at 7.5K and the resistivity becomes zero. The origin of this two-step transition were under investigation, we estimated that a part where the superconductivity locally weakened like Josephson junction was formed due to the influence of microfabrication. [1] Kawano, A. Kawarada, H, et al. Physical Review B 82, 085318 (2010). [2] Wolf, S. A., et al. Journal of Vacuum Science and Technology 13, 145-147 (1976).

11:15 AM E2.04 Dislocation Analysis of HPHT Seed Diamond by X-Ray Topography Shinichi Shikata, Eiichi Kamei and Naoya Akashi; School of Science and Technology, Kwansei Gakuin University, Sanda, Japan.

For high voltage and high current applications of diamond, the vertical structure device is inevitable and a substrate with low positive and low dislocation density is required. Therefore, the dislocation analysis of the substrate is very important; especially for the selection of seed crystal [1]. Especially, the X-ray topography (XRT) is very attractive non-destructive method to investigate the dislocations by the direct high resolution imaging. However, due to the high symmetry of diamond crystal, the diffraction vectors that can be used for the XRT imaging is limited. For instance, [220] vectors for the transmission image and [202], [404], [113] and [133] vectors for the reflection images can be used for (001) oriented substrate. The depth difference between these vectors might be the drawback for the determination of Burgers vector and dislocation vectors. In this paper, the dislocation analysis is carried out by varying the incident beam energies and angles to realize different depth images to understand the depth information of dislocations. The insulating and p type HPHT grown diamond substrates are studied by X-ray topography using SR light source of Kyushu SR Research center (BL09) [2]. The reflectance images are taken using g vectors <202>, <113> and <404>. The monochromatized SR X-ray was used with the energy from 6.7 to 11.7keV. For <404>, several images are taken by varying the energies and angles. Dislocation analysis by g vector (Diffraction vector) and b vector (Burgers vector) are carried out for the reflectance images. Four [404] XRT images are taken by varying the energies from 12 to 13.54keV associated with incident
angles from 10.56 to 2.0 degree. The calculated depths of the X-ray were 247µm, 348µm, 416µm and complete substrate. The images were compared with the measurements taken by <202> and <113> diffraction vectors. Almost no changes are found in all four images for 50 dislocations; indicating possible dislocation vectors of [110], [100] and [210]. 3 dislocations are defined as c-axis oriented threading dislocations. The images of 57 dislocations are changed by depth, and the dislocation vectors are assumed to be [111], [101] and [211]. As a conclusion, the depth analysis by varying the energies and angles of incident X-ray beam might be a powerful method to understand the dislocations of substrate and epitaxial film, eventually the mechanism of dislocation formation during the growth. Ref [1] S.Shikata, E.Kamei, K.Yamaguchi, Y.Tsuchida and H.Takahashi, Material Science Forum, (2018) accepted for publication Jan.9 2018 [2]. K. Ishiji, S. Kawado and Y. Hirai, Phys. Stat. Solidi, A 208 (2011) pp.2516-2521 Acknowledgement Authors wish to thank Dr.Ishiji of Kyusyu SR center for helping us the XRT measurement.

11:30 AM E2.05
Conductive-Probe AFM Characterization of Atomically Well-Defined Diamond (111) Surfaces
Norio Tokuda, Ryo Yoshida, Masatsugu Nagai, Taira Tabakoya, Tsubasa Matsumoto and Takao Inokuma; Kanazawa University, Kanazawa, Japan.

Recently, we realized inversion channel diamond MOSFETs with normally-off operation using ALD-Al2O3 films as the gate oxide, which were deposited on OH-terminated diamond (111) surfaces [1]. However, the field-effect mobility was much lower than an ideal one because of interface states in the oxide/diamond interface. The origin of the interface states is not yet well understood. An atomic force microscopy (AFM) with the field-effect mobility was much lower than an ideal one because of fin and hole accumulation by metal-oxide-semiconductor (MOS). The conventional hydrogen-terminated channel will be discussed. Leveraging Diamond fin field-effect transistor (diamond FinFET) without a LLC, Malibu, California, United States.

Huang, Xiwei Bai, Stephen Lam and Kenneth Tsang; HRL Laboratories Biqin


B2: Diamond Electronics II
Session Chair: James Butler
Tuesday Afternoon, May 22, 2018
Room: Humphreys

* Invited Paper

1:30 PM B2.01
Diamond FinFET Technology for Future Power/RF Electronics
Bsein Huang, Xiwei Bai, Stephen Lam and Kenneth Tsang; HRL Laboratories LLC, Malibu, California, United States.

Diamond fin field-effect transistor (diamond FinFET) without a conventional hydrogend-terminated channel will be discussed. Leveraging metal-oxide-semiconductor (MOS) structures, we are able to effectively control the channel conduction. Enhancement mode devices with 100-nm—wide fins were designed and fabricated to ensure that the channel pinched off at zero gate bias. Device characteristics at various temperatures will be discussed. With improved ohmic contact, larger than 300nA/mm current density were measured at 150°C, orders of magnitude more than current density at room temperature. The potential application of diamond FinFET technology in future power/RF electronics will be discussed.

1:45 PM B2.02
Breakdown Mechanism of C-H Diamond MOSFETs Compared with Other Wide Bandgap Materials
Hiroshi Kawarada; Waseda University, Tokyo, Japan.

Breakdown voltage \( V_b \) is now more than 2000 V [1] in hydrogen terminated (C-H) diamond MOSFETs with 2 dimensional hole gas (2DHG) and channel as drain and channel layer. In general, the maximum breakdown voltage relates with gate-drain distance \( L_{gd} \), i.e. drain layer length in lateral FETs. At present, \( V_b/L_{gd} \) (a criteria for evaluating high voltage FET) is ~ 1 MV/cm in the C-H diamond FET [2] and is almost equivalent to those of SiC and AlGaN/GaN lateral FETs (0.8-1.2 MV/cm) and is higher than that of the oxygen-terminated (C-O) diamond MESFET [3] using lightly boron doped layer (~ 0.5 MV/cm). How \( V_b \) is defined in the C-H diamond MOSFET and other wide bandgap FETs is an important issue, because the \( V_b/L_{gd} \) around 1 MV/cm is far less than critical breakdown fields (\( E_b \)) of SiC (>3.0 MV/cm), GaN (>3.0MV/cm), and diamond (>5.0 MV/cm). Even in the large grain poly crystalline diamond, the \( V_b/L_{gd} \) in the MOSFET with \( V_g \sim 1800\text{V} \) [4] shows ~1 MV/cm. The grain boundaries or defects are not a substantial reason for breakdown in these cases. We have recently found that breakdown frequently occurs at the drain side of drift layer, not its gate side. This phenomenon is very similar to those observed in AlGaN/GaN lateral FETs [5]. In our study, the electric field distribution has been estimated by a device simulation based on the negative charge sheet at Al2O3/C-H diamond interface [2], which reproduces experimental I-V characteristics of 2DHG FET very well [2]. Only by the negative charge sheet, however, the electric field is located near the gate side of drift layer. Adding positively charged layer under the undoped homo-epitaxial layer (channel and drift layer), we could reproduce a highly localized electric field peak which exceeds 5.0 MV/cm near the drain side (the opposite side) of drift layer. The electric field peak explains breakdown phenomenon quite well. The positive charged layer might originate from the ionization of nitrogen donor of type Ib substrate (nitrogen density >1017 cm–3) under the undoped homo-epitaxial layer (500 nm in thickness) through hole injection and recombination. The positively charged layer is useful for charge compensation to realize the homogeneous electric field (super junction) for ideal power device if the positive charged layer exactly neutralizes the negative charge sheet at the interface. Well controlled nitrogen doped layer is quite necessarily to design high power diamond devices. [1] Y. Kitabayashi, H. Kawarada et al., IEEE Electron Device Lett., 38, 3, 363 - 366 (2017). [2] H. Kawarada et al., Scientific Reports, 7, 42688/1-8, (2017). [3] H. Umezawa, T. Matsumoto and S. Shikata; IEEE Electron Device Lett. 35, 1112 (2014). [4] M. Syamsul, H. Kawarada et al., Applied Physics Letters, 109, 203504/1-4 (2016). [5] M. Kuzuhana, IEEE Trans. Electron Devices, 62, 405 (2015).

2:00 PM *B2.03
Complex Charge Transfer in Chameleon Diamonds: A Model of the Color Change Process
James E. Butler1, Keal Byrne1, Wuyi Wang2 and Jeffrey E. Post*
1Department of Mineral Sciences, Smithsonian Institution, Washington, DC, United States; 2Gemological Institute of America, Carlsbad, California, United States.

A group of natural diamonds change their color tint from green to yellow based on their exposure to light and heat. These diamonds also emit long live phosphorescence after uv excitation. We have observed optical response of these diamonds to optical and thermal excitation and developed a model to explain the observed phenomena. A principle element of the model is the proposal of an acceptor state which should be observable in the near IR. Subsequently, we have observed the near IR absorption to this acceptor state supporting our model of charge transfer processes in these diamonds.
Diamond is a candidate material for next-generation power electronic devices and integrated circuit (IC) which operate under extreme environment. In order to use an advantage of high-density hole channel of hydrogenated diamond (H-diamond) surface, we have developed the high-k stack gate dielectrics for H-diamond MOSFETs, such as HfO2/HfO2, LaAlO3/Al2O3, TaOx/Al2O3, and ZrOx/Al2O3, TiOx/Al2O3, and AlIN/Al2O3, prepared by a combination of sputter-deposition (SD) and atomic layer deposition (ALD) techniques [1-5] and Y2O3 [6] prepared by e-beam deposition. In addition, we have developed both of normally-on and off modes MOSFETs, which usually named by D and E modes, respectively, by using the stack gate structure and controlling the threshold voltage ($V_{th}$) [7]. The D/E-modes control provided demonstration of the inverter circuit [8]. After improving the electrical properties of H-diamond MOSFETs and fabricating D/E-modes H-diamond MOSFETs controllably, next challenge is to combine these devices to be logic circuits. In this paper, the H-diamond NOT and NOR logic circuits composed of D-mode ALD-Al2O3/H-diamond and E-mode SD-LaAlO3/Al2O3/H-diamond MOSFETs were fabricated. Electrical properties of the MOSFETs and logic circuits were characterized. By controlling $V_{th}$ value from the FET fabrication process, the H-diamond NOT and NOR logic circuits composed of D- and E-modes MOSFETs were fabricated. The Al2O3/H-diamond and LaAlO3/Al2O3/H-diamond MOSFETs operated with D- and E-mode characteristics, respectively. Distinct inversion characteristics were observed for the H-diamond MOSFET NOT logic circuits. The gain maximum increased from 1.2 to 26.1 with input voltages of $V_{dd}$ changing from −5.0 to −25.0 V. The H-diamond NOR logic circuit showed the clear NOR gate characteristics. 

magnetic field sensor and for magnetic imaging. Although there is a large variety of commercial diamond nanoparticles available, the demanding applications require the use of high quality diamond nanoparticles. Most of the commercial particles contain non-negotiable amounts of metals, which is detrimental for magnetic-related applications. Besides, non-diamond carbon is also present in commercial diamond nanoparticles, leading to unwanted particles aggregation. For all the reasons above, it is highly important to be able to customize the diamond nanoparticles, and produce them according to their ultimate application. The most versatile method for diamond nanoparticles production, is the use of milling techniques to crush bulk diamond. High quality diamond nanoparticles can be obtained crushing high quality commercial bulk samples, such as electronic grade single crystal diamond, or crushing CVD grown diamond films. For instance, diamond nanoparticles with SiV colour centres (with silicon incorporated either from a solid source or from a gas phase) can be created milling down diamond films grown onto passive substrates. Nevertheless, the particles need to be subjected to deep cleaning methods and centrifugation processes to remove the contaminants produced during the milling and to obtain the desired nanoparticles size distribution. The choice of the appropriate milling material is also critically determined by the acceptable contaminants in the ultimate application. Nanoparticles obtained with both tempered steel and silicon nitride materials have been extensively studied by XPS measurements, Raman and TEM measurements. Diamond nanoparticles’ production (including diamond nanoparticles with SIV centres) and different characterization methods will be discussed. 


2:00 PM K3.02

To answer this question, a technique that is capable of detecting not only the pre-edge features that are associated with the presence of point defects. Using a combination of theoretical EELS spectra calculations, we were able to quantify the amount of point defects in the sample. While this is very useful, the life-time broadening in the core-loss spectra means that different types of N-V center may not be directly differentiated. Here we demonstrate that we can now directly measure the signals arising from the N-V centers in individual nanoparticles. The measurement is based on high-energy resolution EELS in a scanning transmission electron microscope (STEM). Using the low-loss region of EELS, we can measure the electronic transitions within the nanodiamond bandgap to detect N-V centers. We used a STEM operated at low voltages (40-60 kV) with both high spatial (~0.1 nm) and high-energy (16 meV) resolutions. Such capability allows us to observe the inter-band transition at high spatial resolution without damaging the structures of particles. Our initial results were demonstrated on ~70 nm nanodiamond particles synthesized by the HPHT methods. We found that a small fraction of particles within the sample show transitions corresponding to the presence of N-V centers. Interestingly, a relatively large fraction of particles do not exhibit these transition states. The reason, we then confirmed is due to the lack of nitrogen in the particle. These observations highlight the importance of dopant control for nanodiamond particles.

2:15 PM K3.03
Aspects of Particulate Nanodiamond as Applied to Host Systems for Enhancement of Their Properties

Particulate nanodiamond, aka detonation nanodiamond, has been explored for its utility as an additive to liquid and solid systems to enhance properties of said systems, such as improved thermal conductivity. Our work has shown that to achieve these improvements it is essential that the nanodiamond from its as-received condition must be cleaned, totally de-aggregated, then functionalized for the appropriate host material if the benefits of particulate nanodiamond in a host system are to be realized. It is insufficient to simply break up, mill or otherwise mechanically treat the nanodiamond and then add it to the system; this does not achieve the dispersed, de-aggregated truly segregate nominal ~ 5 nanometer particle size and distribution that is essential to keep the FND permanently dispersed and enhance the host properties at small concentrations. We have prepared different functionalized nanodiamond, FND, samples, where the functional group is specifically intended to have its terminal chemical bonding couple with the host matrix such that the desired improvement in the host bulk, such as thermal conductivity or strength will be achieved. Because the effective diameter of molecular influence in the host matrix can be much greater than the 5 nanometers of the “core” nanodiamond, concentrations of FND in the range of ppm can result in double digit improvements of, for example, thermal conductivity or flexural strength. Examples of these FND applications will be presented. Furthermore, it is imperative that the nanodiamond particles’ surface be chemically processed such that they are functionalized, that is the appropriate chemical (functional) groups are attached to the diamond nanoparticles which are compatible with and appropriately interact at the molecular level with the host system such as water, oils or polymers and related types of matrices. In this paper we will present examples of how appropriately functionalized nanodiamond combined with practical, in-use bulk materials, at proportions well below 1% of the host can significantly enhance the thermal and strength properties of liquid and solids (polymer) host systems and present and discuss the advantages derived from such treatments. For example, many cooling loop systems, be they for electronics or engines, are water based. We have examined an FND formulation and evaluated it in a precisely controlled and monitored water cooling loop which allows the direct determination of the heat transfer coefficient, a more practical parameter than thermal conductivity, and an improvement as to what's was observed at FND concentration of 500ppm. An appropriate FND formulation to enhance the polymers used in composites was applied and improvement in the flexural strength was observed. These evaluations and others, along with a detailed discussion of how FND can achieve these striking effects at very low additive concentrations, will be presented.
Acid-base titration method has been applied to detonation nanodiamond (DND) powder to determine active site functional groups attached on DND surfaces for de-aggregation of DND powders using different functionalization techniques. The UV/Ozone treated DND containing carboxylic group on its surface, tri-ethylenetetra-amine (TETA) having ammine functionality, and ball milling treatment using ammonium bicarbonate as de-agglomerating and functionalizing media for ammine group attachment, are the functionalization techniques applied to DND powder. Functionalization and morphology of DND samples were characterized by XRD, SEM, RBS, ERDA and FTIR, while for measuring de-agglomeration and particle size distribution we performed dispersion tests and DLS of DND in three different solvent media. During investigation, the amount of carboxylic acid in the UV/Ozone functionalized DND sample has been observed to be 0.3 and 0.25 mM (milli moles) on the surface of DND powder with mole percentage of 1.28 and 2.86% in the forward and backward titrations respectively. Similarly, the amount of ammine group (NH2) in TETA and ball-milling treatment has been observed to be 4 and 5 mM with mole percentages of 0.35 and 0.49% respectively. Results showed that ball-milling treatment provides superior results and de-aggregation of DND powders.

2:45 PM  C2.05
Top-Down Route to NV Fluorescent Nanodiamonds Using Detonation
Vadym N. Mochalin1, Ibrahim Abdullahi1, Martin Langenderfer1, Nicholas Nunn2, Marco Torrielli3, Catherine Johnson3, William Fahrenholtz2 and Olga Shenderova3; 1Chemistry, Missouri University of Science and Technology, Rolla, Missouri, United States; 2Materials Science and Engineering, Missouri University of Science and Technology, Rolla, Missouri, United States; 3Adamas Nanotechnologies, Raleigh, North Carolina, United States; 4Chemistry, Missouri University of Science and Technology, Rolla, Missouri, United States; 5Mining and Explosives Engineering, Missouri University of Science and Technology, Rolla, Missouri, United States.

Detonation is a technique for manufacturing 5 nm diameter nanodiamonds, which are known as detonation nanodiamonds. Although these nanodiamonds are believed to have numerous NV centers, only a small fraction of them are optically active. As a result, the vast majority of detonation nanodiamond particles remain non-fluorescent for reasons that are not completely clear. On the other hand, bright and stable optically active NV fluorescent centers can be produced by irradiating microcrystalline diamonds that are synthesized by high pressure, high temperature (HPHT) processes. Reduction of size of these microcrystalline diamonds by milling yields brightly fluorescent NV nanodiamonds with the sizes down to 10 nm. However, milling of microcrystalline diamonds is a long and expensive process. Here, we investigate the possibility of producing smaller NV fluorescent nanodiamonds by mixing commercially available NV microdiamonds with explosives and detonating the mixture in the conditions typical for detonation nanodiamond synthesis. In our experiments fractions of microdiamonds with average sizes 150nm, 40nm and 15nm had been used. After purification of the detonation product from metal impurities and non-diamond carbon, we observed significant fragmentation of the starting micron-sized particles including fractions of particles below 1 micron. The behavior of NV fluorescent HPHT diamonds in detonation environments depending on their initial size and the potential to use detonation as a cheaper and faster way to reduce the size of NV fluorescent HPHT diamonds below 100 nm will be discussed.

3:00 PM  C2.02
Hybrid Photovoltaics—Covalent Functionalization of Boron-Doped Diamond via Sonogashira Cross-Coupling
Jorne Raymakers1, 2, Hana Krysova1, Anna Artemenko1, Shannon S. Nieley1, 3, Jan Cermák1, Pieter Verstappen1, Daria Miliarieva2, Sam Gielen3, Alexander Kromka1, Ladislav Kavan1, Bohuslav Rezek1, 2, Wouter Maes1, 2 and Ken Haenen1, 2; 1Institute for Materials Research (IMO), Hasselt University, Diepenbeek, Belgium; 2IMOMEC, IMEC vzw, Diepenbeek, Belgium; 3J. Heyrovsky Institute of Physical Chemistry, CAS, Prague, Czechia; 4Faculty of Electrical Engineering, Czech Technical University in Prague, Prague, Czechia.

As recently shown, boron-doped nanocrystalline diamond electrodes are promising alternative photocathode materials for p-type dye-sensitized solar cells (DSSCs) [1]. Their excellent stability, good transparency in the visible and near-infrared region and high hole mobility gives them a clear advantage over the currently employed NiO electrodes. Additionally, the possibility to covalently functionalize diamond surfaces can provide a more stable interface between the electrode and the light-absorbing material, resulting in a more robust device [2]. Unfortunately, the generated currents for p-type diamond based DSSCs are still several orders of magnitude lower as compared to state-of-the-art NiO photocathodes. These low currents can mainly be ascribed to a poor surface coverage, which is partly related to the relative chemical inertness of the diamond surface. Recently, we have expanded the scope of diamond surface chemistry via careful investigation of the Sonogashira cross-coupling, with special emphasis on both the surface coverage and possible remaining contamination [3]. Here, we present a two-step functionalization approach, consisting of the diazonium grafting and subsequent Sonogashira cross-coupling, employed to attach a novel functionalization approach, consisting of the diazonium grafting and subsequent Sonogashira cross-coupling, employed to attach a novel...
alkyne functionalized dithienopyrrole-benzothiadiazole light-harvesting small molecule to heavily B-doped nanocrystalline diamond films. 150 nm thick films were grown on Si p-type conductive substrates by microwave plasma enhanced CVD, while similar films were grown on a Au mirror on Corning Eagle glass allowing subsequent FTIR analysis. The chemical reaction conditions were optimized to maximize the surface coverage, as it was observed from X-ray photoelectron spectroscopy and photoelectrochemical measurements that this is directly related to the generated currents. Additionally, the Sonogashira reaction was compared with functionalization of azidophenyl terminated diamond films via the well-known Cu(I) catalyzed azide-alkyne cycloaddition (CuAAC) to determine the influence of the linker on charge separation and thus the photocurrent generation. References [1] H. Krysova, L. Kavan, Z. Vlekova Zivcová, W.S. Yeap, P. Verstappen, W. Maes, K. Haenen, F. Gao, C.E. Nebel, RSC Advances 5 (2015), 81069-81077. [2] W.S. Yeap, X. Liu, D. Bevk, A. Pasquarelli, L. Lutsen, M. Fahlman, W. Maes, K. Haenen, ACS Applied Materials & Interfaces 6/13 (2014), 10322-10329. [3] J. Raymakers, A. Artenenko, S.S. Nicley, P. Stenclova, A. Kromka, K. Haenen, W. Maes, B. Rezek, Journal of Physical Chemistry 121 (2017), 23446-23454

4:00 PM C2.03
Responsibility Improvement of Diamond UV Photodetector with Novel Device Design ZhanCheng Liu1, Dan Zhao1, Jin-Ping Ao2, Xiaohui Chang1, Yan-Feng Wang1, Jiao Fu1, Minghui Zhang1 and Hongxing Wang1; 1Xi’an Jiaotong University, Xi’an, China; 2Tokushima University, Tokushima, Japan.

Deep ultraviolet (DUV) photo detection is becoming increasingly important for its variable applications such as flame detection, engine monitoring, chemical sensing, and intersatellite communications. Among many wide bandgap semiconductor materials used to fabricate DUV photodetectors, diamond is a promising candidate owning to its high carrier mobility, high thermal conductivity (22 W/cm), low dielectric constant (~5.7) and high radiation hardness. The researches of diamond DUV photodetector are mainly focused on film quality and device design. For device design, there exists a trend to fabricate three dimensional structure to optimize the electric field distribution in the bulk. J. Forneris et al and Kang Liu et al applied groove-shaped electrode structure with a much easier process, in which quasi one dimensional carrier transport might be realized. A thin layer of diamond epitaxial layer was firstly grown on the high-pressure high-temperature single crystal diamond substrate. Then, ICP etching method was used to fabricate diamond strips on the surface. Sequentially, a second thinner diamond film was grown on the processed sample. Before and after the second growth step, photodetectors were fabricated on the sample with interdigitated electrodes vertical to the diamond strips. Compared with the planar structure detectors, the novel detectors own higher responsibility. The details will be presented at the conference.

4:15 PM C2.04
High-Temperature Solar Cells Based on Black Diamond Technology Daniele M. Trucchi1, Alessandro Bellucci1, Marco Girolami1, Matteo Mastellone1, Stefano Orlando1, Andrea Orsini1, Riccardo Polini1, Stefano Salvatori1 and Veronica Valentin1; 1 Institute for Structure of Matter, National Research Council of Italy, Monterotondo (RM), Italy; 2 Department of Chemical Sciences and Technologies, Univ di Roma Tor Vergata, Roma, Italy; 3 Faculty of Engineering, Università degli Studi Niccolò Cusano, Rome, Italy.

High-temperature solar cells are possible by exploiting the Photon-enhanced Thermionic Emission (PETE) concept, which represents a novel and very attractive mechanism for the exploitation of solar radiation, especially if concentrated, and characterized by promisingly high conversion efficiency (>50%). PETE converters rely on the concept that engineered semiconductor photocathodes can provide a very efficient electron emission, induced by hot-electrons produced by photons with sufficient energy, combined to a thermionic emission, sustained by the high temperatures induced by every other thermalization process. Surface nano-texturing combined to surface-hydrogenation, aimed at achieving negative electron affinity conditions and a work function as low as 1.7 eV with a nitrogen-doping of the emitting-layer, are here proposed as a radically new and potential effective PETE cathode completely based on chemical-vapour-deposited (CVD) diamond, able to operate up to temperatures of 800 °C. CVD diamond is transparent to solar radiation due to its wide bandgap, consequently black diamond technology was developed for drastically increasing its absorption coefficient and photogeneration capability under sunlight irradiation. The final p/i/n structure merges the technologies of surface texturing by fs-laser1, boron implantation for formation of buried p-type layer2, and laser-induced graphitic microchannels3, to form an innovative defect-engineered black diamond cathode for the conversion of concentrated solar radiation operating at high temperature. Results under high-flux solar simulator will be reported and discussed by demonstrating for the first time the PETE effect at temperatures from 350 to 550 °C. References 1. P. Calvani, A. Bellucci, M. Girolami, S. Orlando, V. Valentin, R. Polini, and D. M. Trucchi, “Black Diamond for Solar Energy Conversion”, Carbon 105 (2016) 401-407. 2. A. Bellucci, P. Calvani, M. Girolami, S. Orlando, R. Polini, and D. M. Trucchi, “Optimization of Black Diamond Films for Solar Energy Conversion”, Applied Surface Science 330 (2016) 8-11. 3. A. Bellucci, P. Calvani, M. Girolami, V. Carocci, S. Michaelson, A. Hoffman, and D. M. Trucchi, “Buried Boron-Doped Layer for CVD Diamond Photo-Thermionic Cathodes”, IEEE Transactions on Nanotechnology 15 (2016) 862-866. 4. M. Girolami, L. Cristante, F. Di Fonzo, S. Lo Turco, A. Mezzetti, A. Notargiacomo, M. Pea, A. Bellucci, P. Calvani, V. Valentin, and D. M. Trucchi, “Graphite distributed electrodes for diamond-based photon-enhanced thermionic emission solar cells”, Carbon 111 (2017) 48-53.

4:30 PM C2.05
Layer Structure and Characterization of a Diamond Based Thermionic Electron Emitter Sergey Elfimchev, Yulia Stotsky, Rozalia Akvledianidi and Alon Hoffman; Schulich Faculty of Chemistry, Technion-Israel Institute of Technology, Haifa, Israel.

The purpose of this work is the construction of a diamond based electrode for thermionic electron emission (TEE). Nitrogen-doped polycrystalline diamond films were deposited on molybdenum substrates by a hot filament CVD (HFCVD) method. We investigated diamond films with different morphology and nitrogen content produced by variation of the NH/CH4/H2 gas mixture ratio, substrate temperature and gas pressure. It was found that deposition conditions have a strong effect on the effective electrode work function and TEE yields. To improve the electrical contact and the electron transport between molybdenum substrates and nitrogen-doped diamond films we used ultra-nanocrystalline diamond (UNCD) interlayer. The optimal deposition conditions for UNCD interlayer were studied in this work. In addition, we examined different molybdenum surface pretreatments to improve TEE yields. The produced diamond electrodes were investigated by HRSEM, Raman, XPS, UPS spectroscopies and 4PP measurements. The TEE curves were measured at ultra-high vacuum conditions in the 300-600°C temperature as a function voltage.

4:45 PM C2.06
Fabrication of Compact Microlens Arrays Tian-Fei Zhu, Jiao Fu, Zongchen Liu, Zhangcheng Liu, Yan-Feng Wang, Guoqing Shao, Dan Zhao, Xiaohui Chang, Shaoeng Zhang, Yan Liang, Juan Wang and Hongxing Wang; Xi’an Jiaotong University, Xi’an, China.

Fabrication of microlens arrays with high fill factor in chemical vapor deposited single crystal diamond is described. An optimized photore sist reflow and inductively coupled plasma etching processes are used to realize compact diamond microlens arrays. First, photore sist pillars developed by photolithography are reflowed on hotplate. The effects of reflow temperature, time and photore sist thickness on occupancy ratio of photore sist spherical segments are investigated. Second, via dry etching, compact diamond microlens arrays are fabricated by transferring the spherical segment pattern into substrate. Eventually, the compact diamond microlens arrays demonstrate uniform arrangement and good optical performance with projection experiment.
3:30 PM F1.01
Covalent Bond Formation Between Collapsed Carbon Nanotubes Using ReaxFF Molecular Dynamics Simulations
Benjamin Jensen1, Jae-Woo Kim2, Godfrey Sauti3, Kristopher Wise4, Emilie Siochi5, Liang Dong6 and Haydn Wadley7; 1NASA Langley Research Center, Hampton, Virginia, United States; 2National Institute of Aerospace, Hampton, Virginia, United States; 3University of Virginia, Charlottesville, Virginia, United States.

Despite the well-known high mechanical properties of individual carbon nanotubes (CNTs), bulk CNT formats have much lower properties because the weak van der Waals interactions between tubes permit nanotube sliding under load. Covalent bonds are more robust linkages enabling more effective load transfer across the tubes. To maximize the mechanical properties, these inter-CNT bonds must be distributed throughout the material at a density sufficient to prevent tube sliding and telescoping, while minimizing disruption of the CNT structure. This work used molecular dynamics simulations on simplified CNT structures to identify conditions that promote formation of covalent bonds, and to analyze the structures that result from the bond formation process. Reactive molecular dynamics simulations using the ReaxFF(3,20) parameter set were used to model atomic interactions and bond formation between 8 nm diameter double-walled CNTs with collapsed ‘dog bone’ cross sections. For each system, the pressure was increased along isotherms ranging from 1000 to 3500 deg C. Snapshots of the system were quenched to room temperature and zero pressure to permit analysis of equilibrium structural features. The results indicate that high temperature and pressure can induce direct covalent bonding between adjacent CNTs and that the high curvature regions of the collapsed tubes react at lower pressures than planar regions.

3:45 PM F1.02
High Strength Macroscale Carbon Nanotube Structures by Covalent Bond Formation
Jae-Woo Kim1, Godfrey Sauti2, Benjamin Jensen3, Kristopher Wise2, Emilie Siochi2, Liang Dong2 and Haydn Wadley3; 1NASA LaRC/NIA, Hampton, Virginia, United States; 2NASA LaRC, Hampton, Virginia, United States; 3University of Virginia, Charlottesville, Virginia, United States.

Carbon nanotubes (CNTs) have been shown to possess excellent mechanical properties at the nanoscale level. However, after scale-up to formats such as CNT sheets and yarns, the mechanical properties are significantly lower due to poor load transfer within tubes (wall to wall), between tubes in bundles, and between bundles of tubes. Based on guidance from computational modeling, research was conducted to create covalent bonds between CNTs in an effort to enhance load transfer in CNT based structural materials. In this study, spark plasma sintering (SPS) was used to obtain pressure and temperature conditions likely to produce tube-to-tube bonding in macroscale CNT sheets. Various temperatures (1000 ~ 1500 °C) and processing pressures (0 ~ 60 MPa) were applied to CNT sheets under pulsed dc electric current, where the sheets were compressed between two graphite dies in an argon atmosphere. Raman spectroscopy, x-ray diffraction, and microscopic data revealed the formation of cubic diamond and nano-diamond domains, depending on the conditions applied in the SPS experiments. These results indicate that local conditions at the CNT/CNT junctions are capable of inducing covalent bond formation. Mechanical testing of SPS-processed CNT sheets suggests that these bonds contribute to enhanced mechanical properties, especially in densely packed and highly aligned CNT sheets.
enable the commercial development of high-power diamond diodes. These and future diamond-based electronic components can enable the more efficient operation of motors, power grids, electric vehicles, charging stations, geothermal/oil and gas drilling, power processing units for space applications and radiation detectors. Because of its wide bandgap, high breakdown field and high mobility, diamond electronics can handle high power, and are robust to both high temperatures and the high radiation environment encountered in space, making them ideal for applications in harsh environments or where cooling would be impractical. Advant is the recipient of an NSF Small Business Innovation and Research grant for the development of freewheeling diodes.

PS2: Poster Session II
Tuesday, May 22, 2018
5:30 PM - 7:30 PM
Room: Doyle/Rees

PS2.01
Nitrogen and Hydrogen Distribution in Delta-Doped Diamond Films
Mohammed Attrash, Mohan Kumar Kuntumalla and Alon Hoffman;
Schulich Faculty of Chemistry, Technion – Israel Institute of Technology, Haifa, Israel.

Nitrogen delta-doped diamond layers can be fabricated by exposing diamond substrate to N₂ radio frequency (RF) plasma, followed by growing a diamond capping layer. Recently it was found that on preferential retention of hydrogen is occurs within the volume where the nitrogen atoms are localized. Here we investigate the hydrogen and nitrogen distribution and bonding in nitrogen delta-doped diamond layers produced by thin method. The influence of grain boundaries on nitrogen distribution in polycrystalline diamond films was studied. Delta layers were fabricated on single crystal (100) diamond substrate (i.e., no grain boundaries) and polycrystalline diamond thin films with different grain-boundary densities onto the front and back surfaces of the films. X-ray photoelectron spectroscopy (XPS) was used to study the nitrogen chemical states present on the N₂ RF plasma treated diamond surface in-situ. To measure the nitrogen concentration and hydrogen TOF-SIMS was used. The concentration of nitrogen is of order of 10¹⁹ cm⁻³ in nitrogen delta-doped layers. The depth profile (FWHM) of nitrogen distribution in diamond films of front surface (Rrms=6.9) and back surface (Rrms=34.6 nm) are 32.3 nm and 24.6 nm respectively. From our study it is concluded that the source of hydrogen is from the capping layer deposition process.

PS2.02
Grain-Orientation Dependence of Anodic Corrosion Effects in Boron-Doped Diamond
Francesca Celine I. Catalan¹, Norihiko Hayazawa¹, Yasuyuki Yokota¹, Raymond A. Wong¹, Takeshi Watanabe², Yasuaki Einaga³ and Yusouo Kim³; ¹Surface and Interface Science Laboratory, RIKEN, Wako, Japan; ²Department of Electrical Engineering and Electronics, Aoyama Gakuin University, Sagamihara, Japan; ³Department of Chemistry, Keio University, Hiyoshi, Japan; ⁴ACCEL, Japan Science and Technology Agency, Tokyo, Japan.

Recently, boron-doped diamond (BDD) has been extensively studied for its exceptional properties as an efficient electronics. Previous reports, however, have shown that significant degradation in surface morphology¹, and electrochemical performance and stability² can occur in BDD films especially in high current density anodic treatments. Here, we describe the chronological progression of corrosive degradation in highly-doped polycrystalline BDD film electrodes under high current density anodic conditions. The morphological and chemical properties of BDD were systematically analyzed as the electrolysis time is increased up to 12 hours. High-resolution, grain-dependent anodic corrosion was observed for the first time in polycrystalline BDD using Raman spectroscopy and Raman spectral imaging. As confirmed by X-ray Photoelectron Spectroscopy (XPS), high-resolution Raman analysis suggests that degradation starts via the graphitization of sp² carbon on the BDD surface by methyl radicals (CH₃). Further reactions with hydroxyl (OH) creates carbonyl groups specifically on (100)-grain facets and (111)-grain edges. Raman spectral imaging showed that as the sp² carbon atoms are etched from the surface, sub-surface boron dopants are exposed and subsequently detached from the lattice as the BDD undergoes longer anodic treatment. The observed grain-orientation dependence of the corrosion process in BDD offers new and important insights into the chemical interactions occurring on the BDD surface during electrochemical treatments, allowing for future works to be geared towards minimizing degradation without sacrificing BDD electrode efficiency. [1] Kashiwada, T., et al, ACS Appl. Mater. Interfaces 8 (2016), 28299-28305. [2] Chaplin, B., et al, Electrochim. Acta 89 (2013), 122-131. [3] Catalan, FCI, et al, J. Phys. Chem. C 121 (2017), 26742-26750.

PS2.03
Decoration of Growth Sector Boundaries with Single Nitrogen Vacancy Centres in As-Grown Single Crystal HPHT Synthetic Diamond
Phil L. Diggle¹, ², ³, Ulrika F. D’Haenens-Johansson², Ben L. Green¹, ², ³, Chris M. Welbourn¹, Wuyi Wang¹, Andrey Katriusha and Mark E. Newton¹, ², ³, ¹University of Warwick, Coventry, United Kingdom; ²Gemological Institute of America, New York City, New York, United States; ³Diamond Science and Technology, Coventry, United Kingdom; ⁴New Diamond Technology, St. Petersburg, Russian Federation.

It is well known that the morphology of diamonds produced by high pressure high temperature (HPHT) synthesis in a metal solvent is in a large part determined by the relative development of the {100} and {111} faces, however relatively large {113}, {110}, and {115} growth sectors can be found in material grown with nitrogen “getters” in order to produce relatively pure diamond. It is also understood that the morphology of synthetic diamond crystals grown from metal–carbon systems changes from cube to octahedron with increasing temperature and that the orientation of the seed initiation surface can also significantly affect the morphology. Furthermore, the major impurities, nitrogen and boron, are heterogeneously incorporated in the different growth sectors. New Diamond Technology (NDT) have demonstrated that large (lateral dimension > 10 mm), relatively pure (nitrogen and boron impurities less than 0.1 ppm in some growth sectors), low birefringence HPHT diamonds can be routinely produced. We report on confocal photoluminescence microscopy studies of plates cut from HPHT diamonds grown by NDT. We show that the growth sector boundaries between {001} and either {113} or {111} sectors are decorated with negatively charged, nitrogen vacancy (NV⁻) defects. Furthermore we observe a dependence on the distribution based on the type of interface, such that single NVs can be seen at the {001}/[111] interface and ensembles only at the [001]/[113] interface. The bulk {001} growth sector contains essentially no NV defects and there is no decoration involved for an interface involving the {011} growth sector. The optical and spin properties of these NV⁻ defects have been studied by optically detected magnetic resonance (ODMR) spectroscopy, and these data will be reported. ODMR studies reveal that there is no preferential orientation of the incorporated NV⁻ defects. The production and distribution of NV⁻ defects at growth sector boundaries will be discussed. Furthermore, we identify that negatively charged silicon vacancy (SV⁻) and the 1.4 eV nickel centres are present in both {111} and {113} growth sectors in agreement with previously presented results¹. The presence and distribution of these defects will be discussed. References 1. W. Wang, U. F. S. D’Haenens-Johansson, L. Loudin, and P. Johnson, ‘Distributions of the [Si- V⁻] Defect in Diamonds’, SBDD XXI Hasselt (2016).

PS2.04
Phosphorus-Doped Diamond Films by Red Phosphorus Evaporation
Sergey Efimchev¹, Anatoly Bekkerman¹, Yulia Stotsky¹, Tatiana Kravchuk¹ and Alon Hoffman¹; ¹Schulich Faculty of Chemistry, Technion-Israel Institute of Technology, Haifa, Israel; ²Solid State Institute, Technion-Israel Institute of Technology, Haifa, Israel.

A novel simple method for phosphorus-doped diamond films deposition by hot filament CVD (HFCDV) method is presented in this work. Red phosphorus was thermally evaporated and transferred inside the HFCVD chamber by hydrogen flow. The amount of phosphorus was controlled by the source temperature and additional pre-heating of gas mixture. The creation of phosphine gas was detected by mass spectrometry measurements. High concentrations of phosphorus incorporated into polycrystalline and single crystal diamonds was detected by SIMS measurements. The deposited samples were also investigated by high resolution SEM, Raman and photoluminescence spectroscopies. The
method described in this work for phosphorus-doped diamond deposition is controllable, safe and cheap.

PS2.05

Application of a Boron Doped Diamond Electrode Stack for Remediation of Single and Mixed Perfluoroalkyl Compounds in Water

Mary Ensch1, 2, Cory Rusinek1, Michael Becker1 and Thomas Schuelke1, 3

1Chemical Engineering and Materials Science, Michigan State University, Haslett, Michigan, United States; 2Fraunhofer USA Center for Coatings and Diamond Technologies, East Lansing, Michigan, United States; 3Electrical and Computer Engineering, Michigan State University, East Lansing, Michigan, United States.

Perfluoroalkyl compounds (PFAS) are persistent in the environment and are toxic to humans, making them a priority in wastewater treatment. Two of the main compounds detected around the world are the two eight carbon chain compounds, perfluorooctanoic acid (PFOA) and perfluorooctane sulfonate (PFOS) [1,2]. These compounds are man-made and were manufactured in various consumer and industrial products allowing for their release in the air, water, and soil throughout the early 1950s. The EPA has set since a drinking water advisory level of 70 parts per trillion (ppt) for PFOA and PFOS, both individually and combined [3]. Replacements for these compounds have been shorter chain PFAS such as the four carbon chain compounds, perfluorobutanolic acid (PFBA) and perfluorobutane sulfonate (PFBS). However, these shorter chain compounds are still non-biodegradable and are accumulating in the environment. Some of the most recent reports even have reported PFBA and PFBS at higher levels then PFOA and PFOS at this time. Boron doped diamond (BDD) has proven to be an excellent electrode material in early investigations of pollution remediation. BDD has a high over potential for oxygen generation which allows for the creation of hydroxyl radicals and has shown the ability to degrade some of the PFAS compounds in the research literature [1,2]. To better understand the process requirements to degrade these compounds, more studies need to be done with varying current densities and different mixtures of initial components. In doing so, a better understanding of required current densities will be obtained and the knowledge of if the current needs to be increased significantly for shorter chain compounds. Insight into the required current densities for various compounds will lead to the ability to optimize a process based on the initial concentrations of the components in a given water sample. This study aims to investigate the effects of current density on the degradation of individual compounds and mixtures using a BDD electrode stack comprised of two double side coated anodes and three double sided cathodes. The working electrode surface area is roughly 110 cm². In such, five current densities, 5-70 mA/cm², were evaluated for PFOA, PFOS, PFBS, PFBA individually and for varying mixtures of the four. Studies were analyzed with a fluoride ion selective electrode (ISE) to find optimized process parameters. The ISE works by measuring a membrane potential for a specific analyte, such as F⁻, and provides a logarithmic relationship between the measured potential and the concentration of the ion in solution. This allows for the determination of the amount of free F⁻ ions as the degradation of the PFAS proceeds. From these studies, reaction order and each compound’s reaction rate, at each current density, was determined. pH and temperature changes throughout each run were also monitored. Throughout the 8-hour degradation process, the pH for each solution has been between 5-11 and increased as time progressed. The temperature in the lowest current density study increased to an average of 30 °C whereas the highest current density study reached final temperatures of up to 70 °C. Early results indicate that higher current densities have a significant advantage in the early stages of the degradation process, providing over a 50% increase in the F⁻ concentration obtained in the first hour when comparing the lowest and highest current densities for PFOA. Higher current also showed a benefit when degrading PFOS in the first hour, although PFOS has shown to be more difficult to degrade than PFOA. [1] Schaefer, C. E., et al. Chemical Engineering Journal 317 (2017) 424–432 [2] Qiongfang, Z., et al. Electrochimica Acta 77 (2012) 17-22 [3] Environmental Protection Agency. Web. Basic Information About Per- and Polyfluoroalkyl Substances (PFAS) (2018)

PS2.06

A Theoretical Study of Negative Electron Affinity from Aluminium on the Diamond Surface

Michael James1, 2, Paul W. May1 and Neil Allan1

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The ability to form a negative electron affinity (NEA) surface on diamond is of interest for electron emission applications. These surfaces form when atoms electropositive relative to carbon terminate the surface. Simple H-termination gives NEA but hydrogen desorption occurs at elevated temperatures (>700 °C). This makes H-terminated diamond unsuitable for high-temperature applications. Previous work has studied NEA surfaces generated by termination from group I, II and transition metals (TMs). Larger group I metals do not have thermal stability but smaller group I and II metals, such as Li and Mg, show promise. Computational work on various first-row TMs including Cu, Ni, Ti, and Zn, suggest carbide-forming TMs give larger NEA and experimental work has shown ~10 Å thin films of various TMs can give NEA. Density functional theory calculations were performed to simulate the addition of up to 1 ML of aluminium on the diamond surface. Aluminium is a carbide-forming metal that bonds sufficiently well to be used for Ohmic and Schottky contacts, and here we show it is of interest for NEA applications as well. For all metals on diamond, different bonding sites can affect electron affinity (EA), sometimes showing positive EA. Here we show sites can be differentiated by ionic or covalent behaviour. For certain Al coverages, for example 0.25 ML coverage on the (100) O-terminated surface, we find adsorption energies were observed to be larger than for H-termination whilst maintaining a NEA. References 1. W. F. Paxton, M. Howell, W. P. Kang and J. L. Davidson, J. Vac. Sci. Technol. B, Nanotechnol. Microelectron. Mater. Process. Meas. Phenom. 30, (2012), 21202. 2. K. M. O’Donnell, T. L. Martin, N. A. Fox and D. Cherns, Phys. Rev. B 82, (2010), 115303. 3. K. M. O’Donnell, T. L. Martin and N. L. Allan, Chem. Mater. 27, (2015), 1306–1315. 4. A. K. Tiwari, J. P. Goss, P. R. Bridden, A. B. Horvath, N. G. Wright, R. Jones and M. J. Rayson, EPL Europhysics Lett. 108, (2014), 46005. 5. D. A. Evans, O. R. Roberts, A. R. Vearey-Roberts, D. P. Langstaff, D. J. Twitchen and M. Schwitter, Appl. Phys. Lett. 91, (2007), 132114.

PS2.07

Electron Spectroscopy Investigation of Nitride Parylene-crystalline Diamond Surfaces by RF (N2) Plasma

Mohan Kumar Kuttanmanna, Mohammed Attrash, Fengnan Li and Alon Hoffman; Schulich Faculty of Chemistry, Technion - Israel Institute of Technology, Haifa, Israel.

In this work, we demonstrate a simple technique to induce adsorption of nitrogen onto diamond surfaces with low levels of damage. This was achieved by exposing the surfaces to N2 RF plasma. Nitridation process has been carried out for different N2 plasma exposure time (10, 20 and 30 minutes) and pressure (3x10⁻³ and 7x10⁻³ torr) at plasma power of 36 W. A neutralizer was placed at the exit of the plasma source to decrease the density of the high energetic nitrogen species in the plasma arriving at the surface. The structural, chemical and electronic properties of nitried (as-processed, annealed and hydrogenated) diamond surfaces were evaluated by using HREELXS, XPS and UPS, respectively. It is observed that the structural quality of diamond surfaces can be optimized by using a neutralizer during the nitridation process. XPS and HREELXS measurements confirmed the nitrogen incorporation into the diamond surfaces. The HREELXS analysis of nitried diamond surfaces suggest that the plasma processing pressure and the exposure time play a crucial role in controlling surface structural quality. The presence of the optical phonon (300 meV), which is a signature feature of well-defined and defects-free diamond surface; confirm the structural quality of nitried surfaces. Hydrogenation of annealed surfaces revealed that the surface structural recovery is possible with low level of structural damage.

PS2.08

Evaluation of Highly Doped HPHT Diamond Crystallinity by Electron Backscatter Diffraction

Akio Matsushita, Koji Ashida, Daichi Dojima, Kazunori Koide, Yuki Tsuchida, Tadaaki Kanejo and Shinichi Shikata; Physics, Kwansei Gakuin University, Sanda, Japan.

Low resistivity p+ substrate is essential to realize high power diamond device for energy saving power electronics. Highly B doped p+ high pressure and high temperature (HPHT) substrate is receiving much
attention as a seed crystal for low resistivity p+ substrate growth, because of the small difference of lattice mismatch and doping concentration, compared with an insulating HPHT seed. However, due to small quantities in the current market, the commercially available p+ HPHT substrate is still under the development associated with B incorporation during HPHT growth. According to the recent reports [1, 2], four [111] growth sectors can be clearly seen in the p+ substrate by Raman mapping and X-ray topography measurements, with the large variations of crystalline quality and B incorporation [3]. In this paper, we focus on the crystallinity of the growth sectors and report on the evaluation of crystal orientation by electron backscatter diffraction (EBSD) method. Three commercially available B doped p+ HPHT (001) single crystal substrates (3.0mm×3.0mm) having a doping concentration from 5 to 9 × 10^18 cm^-3 were used. High performance EBSD system (Zeiss MERLIN™) is used to perform quantitative crystallographic analysis to investigate growth sector boundaries. The incident electron beam of 20 keV was introduced into the specimen tilted 70 degree from horizontal axis. In this configuration, the maximum penetration depth of electron is about 900nm, however, the electrons scattered from the diamond layer down to 70nm below the surface are estimated to contribute to Kikuchi pattern information. By the EBSD method, the lattice distortion can be captured by analyzing the pattern change as tensor of normal, shearing strain and lattice rotation. Four boundaries regions of four growth sectors for p+ HPHT substrate were measured and observed following imperfect crystallographic disorders. First, 40 μm^2 area across the boundary between the [-111] and [1-11] growth sector was measured. It was found that the [001] axis of [111] growth sector was rotated from [001] to [-1-10] direction compared to [1-11] growth sector for 0.02 degree. The same measurements were carried out along the sector boundary, and similar phenomena were found in several more places. No tendency of rotation was observed along the boundary, and the highest rotation angle of 0.05 degree was measured. These rotations of the crystal axis were observed for all four sector boundaries. For other boundary, the [001] axis of [-111] growth sector was rotated from [001] to [-1-10] compared to [-111] sector, the [001] axis of [111] growth sector was rotated from [001] to [-110] compared to [111] sector, and the [001] axis of [-111] growth sector was rotated from [001] to [-1-10] compared to [111] sector. This fact shows “grain boundaries” are formed for p+ HPHT substrate. The measurements were carried out for another two substrates, and the similar phenomena were found for the second substrate. Third substrate was found to be perfect single crystal without any grain boundaries. In our previous study, the SBDs fabricated on boundaries have relatively lower reverse-bias voltages compared to devices fabricated on no dislocation regions, seemingly have poor crystal qualities.[4] These phenomena presumably due to “the grain boundaries” observed by EBSD in this paper. Since the p+ crystal growth by HPHT method, the crystallinity might be affected by fluctuations of temperature and pressure, associated with the presence of B, the optimization of growth conditions presumed to be difficult compared to the conventional insulating substrate. The improvement of p+ crystal growth technology is highly desired to advance toward the seed crystal of p+ substrates for power device applications. References [1] S. Shimakita, Diam. Relat. Mat., 65(2016)168 [2] K. Srimongkon, et al., ibid, 63(2016)21 [3] S. Shimakita, et al., Diam. Relat. Mat., 73(2017)241 [4] N. Akashi, et al., Mat.Sci.For, (2018) accepted for publication Dec. 9, 2017

PS2.09 Diamond High-Power Switching Transistor—Design, Device Structure Analysis and Demonstration Matthias Muehle1, Timothy A. Grotjohn1, 2; Tom Zimmermann2, 1, Yuelin Wu2, Michael Becker2 and Thomas Schuek1, 2; 1Fraunhofer USA, East Lansing, Michigan, United States; 2Electrical and Computer Engineering, Michigan State University, East Lansing, Michigan, United States. Single crystalline diamond (SCD) based electronics has the potential to significantly impact and change the state of the art technology for high-power electronics. In recent years, significant development has made in the fabrication of diamond electronic devices, which are capable of operating in high-power regimes. These include the demonstration of high voltage Schotky diodes with breakdown voltages exceeding 1.7 kV with high current densities [1], as well as the demonstration of various field effect transistor design concepts for high breakdown voltage [2]. The next step in technology development is the implementation of design ideas for the realization of a high-power switching transistors that have both high forward current and high reverse bias breakdown voltages. As realization of such a high-power switching transistor we propose a mixed vertical-lateral transistor structure. A combination of vertical and lateral features allows the design of a transistor which is capable of withstanding high voltages while also being able to conduct high currents. The high current is achieved by a lateral current path with the current controlled by a gate structure, and the high voltage region being a larger area p- vertical region. The vertical component contributes the capability of high current conduction with only little losses (minimized Rn) in the way of operating a vertical voltage through this region [3]. First, we report on the controlled growth and material properties of the individual layers (p+, p and n). Temperature-dependent (room temperature up to 400°C) Hall effect measurements, I-V and C-V characteristics are used to determine mobility, majority carrier concentration and lifetime, and compensation concentration. Various Ohmic and Schottky contact metal configurations are evaluated. It is demonstrated that annealed Ti/Pt/Au Ohmic contacts result in the lowest contact resistance while providing good adhesion. It is shown that the formation of good Schottky contacts is the most critical and problematic to achieve. It is demonstrated that Mo/Au Schottky contacts provide good compromise of adhesion and electric performance. We present the proposed semiconductor processing steps for the realization of the vertical-lateral high-power transistor based on the individual films and contacts studied. We will also present different design variations of doping concentration and sizes to achieve various currents and breakdown voltages. The target breakdown voltages are in the range of 1-2 kV. Finally, preliminary data of transistors fabricated will be reported.


PS2.10 Diamond Brewster Windows for Microwave Transmission Theo A. Scherer, Gaetano Aiello and Dirk Strauss; IAM-AWP, Karlsruhe Institute of Technology KIT, Eggenstein-Leopoldshafen, Germany. The diamond Brewster window consists of a diamond disk brazed to two copper waveguides at the Brewster angle of 67.2°. Being 140 mm the maximum available diameter in the market for a CVD diamond disk, the aperture of the waveguide has an upper limit of 50 mm. Because of the high heat loads occurring in gyrotrons that operate in the MW power range, a greater aperture of the waveguide is required, and this leads to the use of very large diameter disks. The current target is an aperture of 63.5 mm, leading to the need of a 180 mm minimum diameter for the diamond disk in the Brewster configuration. State of the art microwave plasma reactors are not capable of growing diamond disks of such size. In collaboration with the industrial partner Diamond Materials GmbH (Freiburg, Germany), experiments with unconventional method were thus first carried out in a small scale: to join diamond fragments by overgrowing the joint gap with diamond to obtain large diamond disks. The hot filament method was used and a dedicated reactor was designed, assembled and tested. The hot tungsten filament was placed right in the center of the joint gap having the shape of a V-groove. In this work, the results of such experiments shall be reported and discussed. In addition, the results of the very first attempts of growing directly large area diamond disks with a diameter of 180 mm in a microwave plasma reactor shall be presented. A first setup of reflectometry and polarization diagnostics for future high power multi-frequency transmission windows with low reflection coefficient will be discussed.

PS2.11 Fabrication of Diamond Composites with Rare Earth Fluoride Nanoparticles for X-Ray Scintillators Vyacheslav S. Sedov1, Sergey Kuznetsov2, Maria mayakova1, Andrew A. Khomich2, Victor Ratchenko1 and Pavel Fedorov1; 1General Physics Institute of Russian Academy of Sciences (GPI RAS), Moscow, Russian Federation; 2Harbin Institute of Technology, Harbin, China. Diamond nanoparticles is an area of modern materials science of an increasing interest. Extensive efforts in this field are focused at the impurity-related color centers in diamond (e.g., nitrogen-vacancy (NV), silicon-vacancy (SIV), germanium-vacancy (GeV), chromium- or nickel-related defects, etc.), that typically show narrow (a few nanometers at room temperature) zero-phonon lines (ZPL) in photoluminescence (PL) spectra and short PL decay times on the order of nanoseconds. These color
centers can be easily produced by ion implantation in diamond or by chemical vapor deposition (CVD) with in-situ doping. The known PL properties of the impurity-vacancy centers are quite suitable for engineering single photon emitters, the search for new and better PL sources in a diamond matrix, which could extend their spectral range and increase their decay time and efficiency, is still an ongoing activity. The goal of such studies is to extend the capabilities of diamond-based PL materials. More specifically, RE in form of nanoparticles (or atoms) with bright X-ray fluorescence can complement X-ray-transparent and small X-ray matrices to fabricate scintillators with tunable high-performance and relatively low absorption of the incident X-ray beam. Recently, Magyar et al. [1] reported the first such attempt to introduce RE atoms into a diamond lattice by doping diamond single crystals with Eu(III) tri-(2,6-pyridine dicarboxylic acid) complex. In our first studies [2], we used europium fluoride (EuF₃) nanoparticles to fabricate “Diamond-EuF₃” composite films. Chemical vapor deposition (CVD) technique was used for the synthesis of diamond to grow the composite material, which showed bright PL at 612 nm. In this work, our method was applied for the preparation of the multilayered composites with different RE fluorides (Eu, Ce, Er, Dy, Ho etc.) in our search to find the best combination of materials for X-ray scintillation applications. Both PL and X-ray fluorescence performance of best “Diamond-RE” composites will be reported. The study was funded by a grant from the RFBR #14-28-11784.1.


PS2.12 Influence of the Surface Oxidation to the Spin Coherence of Properties of Single NV Centers in Nano-Diamonds Ryuta Tsukahara¹, Masazumi Fujivara¹, Yoshihiko Sera¹, Hideki Hashimoto³ and Shinichi Shikata¹; ¹Physics, Kwansei Gakuin University, Sanda-shi, Japan; ³Chemistry, Kwansei Gakuin University, Sanda-shi, Japan; ²Osaka City University, Sumiyoshi-ku, Japan.

The NV center in diamond is a point defect showing excellent stable emission, that allows optical readout and manipulation of the spin states, and entanglement between photons and the spin qubits. [1,2] Thus, the NV center can be easily produced by ion implantation in diamond or by chemical oxidation at 90°C for 6 hours. Spin coherence time (T₂) was measured for NV center using spin echo method for the four treatments were a) ~1.8µs, b) ~1.4µs, c) ~2.5µs and d) ~2.6µs. This fact showed that the spin coherence time was extended by annealing the nano-diamonds in air at 550°C. The longest T₂ was 6.1 µs for the sample which was annealed in air at 550°C for 2 hours. This is about 1.3 times higher than that of un-treated sample. Unfortunately, the positive effect for longer lifetime was not observed for the chemical oxidation. In summary, we have conducted the statistical evaluation of the spin coherence time of single NV centers in 25 nm-sized nano-diamond in relation to the surface condition. The longer spin coherence time of the NV center in the nano-diamond was obtained by the annealing in air at 550°C for 2 hours. The longest spin coherence time of 6.1 µs was obtained; however, further improvement is required for the biotechnology application.


PS2.13 Thermionic Emission Studies of Diamond Gary Wang¹, Alex Croot¹, Mattia Cattelani¹ and Neil Fox¹, ²; ¹Physics, University of Bristol, Bristol, United Kingdom; ²Chemistry, University of Bristol, Bristol, United Kingdom.

Thermionic emission offers a potential way for direct conversion of thermal to electric energy in a thermionic converter, where thermally excited electrons from a cathode are emitted and passed through a vacuum gap to a colder anode. According to the Richardson-Dushman equation, the main barrier for high emission current is the material work function. With suitable doping and termination, diamond is known to exhibit a low work function. Various studies on thermionic emission of diamond have been done before, but typically only the current density's temperature dependence is recorded. This is in part due to the instability of the diamond surface at high temperatures. Energy-filtered electron emission microscopy and electron spectroscopy techniques available in the Bristol NanoESCA facility were used to study diamond samples with various dopants. Samples were kept at elevated temperatures for thermionic emission, while different light sources were used for photoemission. Work function was determined for the diamond with and without a hydrogen termination at various temperatures by observing the electron emission distribution in the low energy region. X-ray photoemission spectra of the C1s peak was used to monitor charging and band bending of the sample.


To investigate the doping effect of silicon of the corrosion resistance of diamond-like carbon films, the silicon doped films etched by nitric acid were evaluated using a surface plasmon resonance (SPR) device with a multilayer structure consisting of an DLC layer on metal. Si doped DLC films with different concentration was deposited by pulsed plasma chemical vapor deposition method. A flow cell for the introduction of nitric acid solution was placed on the DLC layer of the multilayer structure. A nitric acid solution was used in the etching tests. The Kretschmann configuration was used for SPR measurement, and the SPR angle was determined as the angle with minimum reflectivity. The SPR angle decreased with increasing concentration of nitric acid injection into the flow cell, indicating that the film was corroded by the nitric acid. The thickness of the films was calculated from the SPR angle. The rates of decrease in the thickness were decreased with Si concentration increasing. Although the Si doping is good effect for nitric acid solution, the corrosion rates against sodium hydroxide were increased with increasing of Si doping concentration. These results indicate that the Si doping is good for the chemical resistance to nitric acid solution, not good for sodium hydroxide.
PS2.15  
**New Approaches for the Fabrication of Free Standing TiO2 NWs/CNTs and SiNWs/CNTs Anodes, Appropriate for High Performance Lithium-Ion Batteries**  
Juan C. Arango1, Francisco Márquez1, Carmen Morent2, Abnle Machin3 and Sergio Pinilla1; 1The School of Natural Sciences and Technology, Universidad del Turabo, Caguas, Puerto Rico; 2Applied Physics, Autonomous University of Madrid, Madrid, Spain; 3School of Professional Studies, Ana G. Méndez University System, Orlando, Florida, United States.

Titanium dioxide nanowires (TiO2NWs), are considered as one of the most promising candidates to be used as anode material for lithium-ion batteries (LIBs). TiO2 is abundant, has low work potential, its synthesis process has a high yield, and is a non-toxic and non-corrosive solid. Due to these characteristics, this material is positioned as a promising environmentally friendly material towards the future of clean energy storage and transportation, through batteries. However, bare TiO2NWs does not possess high capacity (ca.330mAhg-1), which restricts the good characteristics of this material when compared with the batteries currently manufactured with graphite anodes (ca.372mAhg-1). Silicon, with a specific capacity of ≈4200mAhg-1, is considered as the most promising candidate to be used as anode material for lithium-ion batteries (LIBs).

Among its good features, silicon is abundant, has low work potential, and has a high theoretical specific capacity, which is more than ten times higher than that of graphite (commercial anode). However, silicon undergoes an enormous change in volume (ca.275%) during the lithiation/de-lithiation processes, resulting in a disintegration of the material, and subsequent electrical disconnection. To mitigate these common issues within each described material, the use of single walled Carbon nanotubes (CNTs) rises as a possible solution among the scientific community; CNTs are outstanding nanostructures, widely studied for their potential use in LIBs anodes, due to their conductive, resistance and mechanical properties. In this research, TiO2NWs were synthetized through a hydrothermal approach. Likewise, Silicon nanowires (SiNWs) were synthetized through a Metal Assisted Chemical Etching (MACE) approach. Reaching high crystallinity and purity nanostructures suitable for LIBs. After that, commercial CNTs (RhenofitCNT-4) were added in various percentages to obtain mixtures of TiO2NWs/CNTs and SiNWs/CNTs. These mixtures were carried using mixtures of different solvents, preventing the formation of clusters throughout the electrode surface. Finally, each mixture was left to dry overnight, to reach a homogenous deposition of the mixtures over the intended current collector (Cu film). The resulting electrodes show high flexibility and resistance due to the CNTs presence, reaching membrane-like structures usable as free-standing anodes suitable for LIBs. In addition, the physical framework formed by the CNTs around the TiO2NWs or SiNWs will help accommodate the mechanical strain caused during the lithiation/delithiation process in LIBs, while improving the life lasting of the materials, increasing the capacity of mechanical strain caused during the lithiation-delithiation process in LIBs, and the shape of the particles varies from sphere, polyhedron to hollow polyhedron with the temperature. The current study is designed to characterize frictional properties of carbon onions with different particular shape.Carbon onions are prepared by annealing of nanodiamond at 2000, 2400 and 2800 degree C. The morphology of carbon onions is observed by transmission electron microscopy and are confirmed as the spherical, polyhedron and hollow polyhedron nanoparticles. Raman spectroscopy and dynamic light scattering (DLS) are also employed to analyse the chemical microstructures and cohesive property, respectively. Friction measurement is carried out using a ball-on-disc friction tester to examine how the difference of morphology affects the tribological properties of carbon onions. Balls of high carbon chromium bearing steel (SUJ-2) and silicon wafer are used for sliding materials. For illuminating the frictional properties of the carbon onions, the minimum coefficients of friction and the lubrication lives that are sliding distances when friction coefficients increase and then reach 0.1 are measured in vacuum. Raman spectroscopy and DLC reveal that the crystallinity and dispersion of polyhedral carbon onion produced at 2400 degree C are the highest among the carbon onions. The results of friction measurement show that the minimum coefficients of friction for the carbon onions produced at 2000 and 2800 degree C are lower than that of the carbon onion at 2400 degree C, and the lubrication lives of the carbon onions at 2000 and 2800 degree are longer.

PS2.16  
**Sonication Enhanced ODMR Response of NV Colour Centre Nanodiamond Powders**  
Mateusz Fliciek1, Maciej Glowacki1, Krystian Sycz2, Mariusz Mrózek2, Adam Wojciechowski3, Wojciech Gwilk4 and Robert Bogdanowicz2; 1Gdansk University of Technology, Gdansk, Poland; 2Institute of Physics, Jagiellonian University, Krakow, Poland.

The color center may couple an electron to become negatively charged (NV- or NV-) with spin S=1. The nonzero spin is responsible for paramagnetic properties of the center. The vacancies may be created in diamond powders or in a bulk CVD or HTHP diamond. Due to photoconversion between the charged and neutral forms of the center and its light-power dependence, the NV centers are very attractive for applications in various quantum devices. Nitrogen-vacancy (NV) centers are the most widely studied crystallographic defect in the diamond lattice since their presence causes strong and stable fluorescence. The negative charge state of the defect (NV-) is especially desired because of its potential for quantum information processing. In this study, fluorescent suspensions of diamond particles have been produced by microbeadassisted ultrasonic disintegration of commercially obtained diamond powder containing NV color centers. The sample characterization was based on optical (absorption, emission, Raman) and microwave spectroscopy with high spatial (confocal, ~μm3) and spectral (sub-Hz) resolution. The measurements were performed using a technique of optical detection of magnetic resonance (ODMR) improved by development of the microwave hole burning technique. Moreover, thin layer of the diamond particles has been deposited on a silicon substrate and examined using scanning electron microscopy (SEM). The development and applications of quantum technologies and nonlinear spectroscopy for studies of color centers in diamonds is very fast. Thanks to the stable crystallographic and electron structure of diamond, NV-color centers exhibit very stable electronic spectra, resistant to various perturbations. Their excellent optical and spin properties (paramagnetism) allow one to use different resonance and spintronic methods of and enable precision metrology. Acknowledgements This work was supported by the research grant NATO SPS G5147 and by Polish National Science Centre (NCN) under the Grants No. 2016/22/E/ST7/00102 and 2016/21/B/ST7/01430 and by the Polish National Centre for Research and Development (NCBiR) under the project Technomatrasteg Diamsec 347324. The DS funds of Faculty of Electronics, Telecommunications and Informatics of the Gdansk University of Technology are also acknowledged.

PS2.17  
**Characterization of Frictional Properties of Carbon Onions with Different Molecular Morphology**  
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Carbon onion is an attractive nanoparticle as solid lubricant and abrasive in the realm of mechanical engineering. A large amount of carbon onion nanoparticles can be produced by annealing of nanodiamond or carbon black at temperatures above 1800 degree C. In this process, the molecular morphology of carbon onion largely depends on annealing temperature and the shape of the particles varies from sphere, polyhedron to hollow polyhedron with the temperature. The current study is designed to characterize frictional properties of carbon onions with different particular shape. Carbon onions are prepared by annealing of nanodiamond at 2000, 2400 and 2800 degree C. The morphology of carbon onions are observed by transmission electron microscopy and are confirmed as the spherical, polyhedron and hollow polyhedron nanoparticles. Raman spectroscopy and dynamic light scattering (DLS) are also employed to analyze the chemical microstructures and cohesive property, respectively. Friction measurement is carried out using a ball-on-disc friction tester to examine how the difference of morphology affects the tribological properties of carbon onions. Balls of high carbon chromium bearing steel (SUJ-2) and silicon wafer are used for sliding materials. For illuminating the frictional properties of the carbon onions, the minimum coefficients of friction and the lubrication lives that are sliding distances when friction coefficients increase and then reach 0.1 are measured in vacuum. Raman spectroscopy and DLC reveal that the crystallinity and dispersion of polyhedral carbon onion produced at 2400 degree C are the highest among the carbon onions. The results of friction measurement show that the minimum coefficients of friction for the carbon onions produced at 2000 and 2800 degree C are lower than that of the carbon onion at 2400 degree C, and the lubrication lives of the carbon onions at 2000 and 2800 degree are longer.

PS2.18  
**Soft X-Ray Irradiation Effect on the Hydrogenated SiContaining DLC Films**  
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Hydrogenated diamond-like carbon (H-DLC) films, which contain hydrogen more than 40 %, are expected as solid lubricant for artificial satellite, because they maintain low friction in vacuum. On the other hand, astronomical materials used in low Earth orbit (LEO), where artificial satellites revolve, are required the durable against space environments, which are different from those on the earth, such as, soft X-ray, atomic oxygen, high vacuum and so on. It was founded that none doped H-DLC films were etched by...
atomic oxygen irradiation, but H-DLC films, which included several percent of Si, had durable against atomic oxygen. In this study, irradiation effect on hydrogenated Si-containing DLC (Si-DLC) films by the exposure to soft X-ray, which was another space environment, was investigated. DLC films are generally durable against X-ray exposure. However, desorption of hydrogen in H-DLC films caused by soft X-ray exposure was reported. Therefore, clarification of the effect of soft X-ray exposure on hydrogenated Si-DLC films is important to ensure that hydrogenated Si-DLC films are used in space. To investigate the effect on the hydrogenated Si-DLC films, we exposed such films to synchrotron radiation (SR) in the soft X-ray region and measured several film properties. Hydrogenated Si-DLC films were deposited on Si wafer using an amplitude-modulated radio-frequency plasma-enhanced chemical vapor deposition method. The soft X-ray irradiation of hydrogenated Si-DLC films was carried out at BL06 in the NewSUBARU synchrotron facility of the University of Hyogo. The SR at the BL06 sample stage had a continuous spectrum from the infrared to soft X-ray region less than 1 keV. The SR dose [mA·h] was derived as the product of the ring current [mA] and the exposure time [h]. Elemental compositions of the hydrogenated Si-DLC films were determined by the combination of elastic recoil detection analysis and Rutherford backscattering spectrometry. The atomic ratios of hydrogen, silicon, and carbon of the hydrogenated Si-DLC film before SR irradiation were ≈0.4, ≈0.2 and ≈0.4, respectively. These atomic ratios were not changed after SR exposure. To discuss on variations in the local structure of the hydrogenated Si-DLC film due to the exposure to SR, C K-edge and Si K-edge NEXAFS spectra were measured at BL09A and at BL05A in NewSUBARU, respectively. In the C K-edge NEXAFS spectra of hydrogenated Si-DLC films before SR irradiation, the σ* peak was narrower than that of typical DLC film and shifted to lower energy of about 5 eV due to influence of peak of 289 eV derived σ(C-Si) peak. In addition, the peak intensity of 1s→π* transition at 285.4 eV was weak. After SR exposure, the π* peak intensity increased by the irradiation of 15 mA·h of the soft X-rays dose. On the other hand, the σ* peak became broader and shifted to higher energy. Therefore, C-C bond increased at surface of hydrogenated Si-DLC films by SR exposure. In the Si K-edge NEXAFS spectra of hydrogenated Si-DLC films, the peak of 1846.8 eV derived from SiO2 drastically increased by the irradiation of SR until 800 mA·h dose. However, the intensity of this peak decreased suddenly by the irradiation beyond 1500 mA·h dose. On the other hand, the intensity of the energy range about 1843-1846 eV increased. These results mean that the Si oxidation layer was formed by SR exposure, but the formed Si oxidation layer was deoxidized by the additional exposure to SR. From these experimental results, durable surface layer against X-ray exposure was formed at the surface of hydrogenated Si-DLC films by the irradiation of soft X-ray. These change are considered to be caused by the desorption of hydrogen from the hydrogenated Si-DLC films. Hydrogen atoms are desorbed by excitation due to soft X-ray irradiation, and the remaining carbon atoms bond to each other.

**PS2.19** Bio sensor Applications of the Composites of Carbon Nano forests and Nanoparticles of Strontium Aluminate Doped with Rare-Earth Elements Patsy Y. Arquieta and Oxana V. Kharrisova, Universidad Autónoma de Nuevo León, Monterrey, Mexico.

Currently, new biosensors with fluorescent properties on the basis of carbon allotropes are in development for possible applications in biotechnology area. In this work, the carbon forest-like nanocomposites with strontium aluminate SrAl2O4 doped with rare-earth elements possessing fluorescent properties were prepared via spray pyrolysis. The synthesis was carried out in dry nitrogen atmosphere in the temperature range from 780 to 850°C. The used metal oxides were those of samarium (Sm), europium (Eu), neodymium (Nd), lanthanum (La), cerium (Ce), as well as some their combinations. The deposition of carbon nanotubes was carried out on the optical fibers surface to reach an uniform growth of forest-like carbon nanotubes, adding to its surface the nanoparticles of metal oxides. The formed products were characterized by XRD, Scanning Electron Microscopy (SEM), Transmission Electron Microscopy (TEM), FTIR Spectroscopy, Raman Spectroscopy and UV/visible spectroscopies. Synthesis, properties, structural peculiarities, and applications of nano forests and related nanostructures are discussed, revealing better results with use of lanthanum oxide. The deposited strontium aluminate nanoparticles were found to be in the range of sizes of 20-60 nm being uniformly distributed on the surface of MWCNTs. Possible applications for the formed MWCNTs-supported luminescent composites as persistently luminescent biosensor materials are proposed.

**PS2.20** Nanodiamond Surface Modification and Technology Development of a High Dose Non-Steroidal Anti-Inflammatory Drug Contained in a Medical Patch Whungwoo Kim1, C.K. Rhee2 and A.P. Puneet3; 1 Nuclear Material, Korea Atomic Energy Research Institute, Taejon, Korea (the Republic of); 2-Korea Atomic Energy Research Institute, Taejon, Korea (the Republic of); 3-Institute of Biophysics, Russian Academy of Sciences, Siberian Branch, Krasnoyarsk, Russian Federation.

Detonation nanodiamond (ND) is receiving much attention due to its remarkable mechanical, electrical and thermal properties, facile surface tailoring, narrow size distribution of primary particles and high biocompatibility. The rich surface chemistry of ND, the absence of toxic impurities and small size make ND a promising material for biomedical and technical applications. In this research, potential of ND in drug delivery has been demonstrated many times for a variety of compounds. The most important advantages of ND as a drug delivery vehicle stem from its strong physical adsorption controlled by the surface functional groups as well as a wide surface area of ND that is ideal for conjugating various biochemical substances. A high loading capacity of non-steroidal anti-inflammatory drugs (NSAID) was discussed with using lower concentration of ND.

**PS2.21** Cu-DLC Composite Fabricated by Cold Spray Technique Nana Okimura, Nobuhisa Ata, Naoto Ohtake and Hiroki Akasaka; Tokyo Institute of Technology, Tokyo, Japan.

Diamond-Like Carbon (DLC) film is consisted of sp2 and sp3 hybridized bonding carbon and hydrogen atoms, has high hardness and low friction coefficient. Therefore, DLC films are applied industrial fields for low energy consumption. On the other hand, DLC films can be obtained only as coating. In general, a few μm thick DLC films can only be deposited on the substrate with plasma chemical vapor deposition (CVD) method or physical vapor deposition (PVD) with plasma. Hence we can only obtain the DLC in the shape of thin film. In this research, we focused on cold spray (CS) technique to obtain the DLC contained metal composite. Thick metal films such as “mm” can be formed by colliding solid and plastic deformation of metal particles to substrate at a supersonic velocity by the conventional CS process. We propose that the DLC contained metal composite film with “mm” thick were deposited from the DLC coated metal particles by the cold spray (CS) technique to obtain the low frictional metal thick coating. DLC films was deposited on copper particles with a mean diameter of 20 μm (Cu-HWQ-20; Fukuda Metal Foil & Powder Co., Ltd.) with pulse plasma CVD process. Copper particles was placed on stainless tray of a negative electrode at the vacuum chamber. Acetylene gas was introduced to the vacuum chamber to 3.0 Pa. The applied voltage was maintained at ~3.0 kV with 14.4 kHz, and DLC film was deposited 30 min on copper particles. These DLC coated copper particles used as source materials, the Cu-DLC composite film was fabricated by CS process. Advanced cold gas system (Medicant Co., Ltd.) based on a DIMET 412-K cold spray system (TEIN TC Co., Ltd.) was used as the CS system. A1050 aluminum plates were used as substrates. The surface of aluminum plate was processed by a sand blaster with white alumina (#46, Fuji Manufacturing Co., Ltd.) to increase the surface area for improvement the deposition efficiency. Acceleration gas was air with 0.6 MPa and 723 K. The particle feed rate was 10 g/min. The distance from the nozzle to the substrate surface was 12 mm. The nozzle was scanned 10 times by 50 mm/s. The Cu film was fabricated by the same way from copper particles for comparison. To estimate the introduction DLC into the Cu matrix, the obtained film was analyzed by Raman spectroscopy. Surface of the Cu-DLC composite film was milled to obtain smooth surface, and tribological properties were evaluated by Ball on Disk (Bod) test using SUJ2 balls with 6 mm diameter. Load and rotation speed were 1 N and 400 rpm, respectively. At 20 min in deposition duration, the average of thickness in the obtained Cu-DLC composite film was 130 μm. Raman spectrum of the Cu-DLC composite film showed the broaden peaks of Graphitic and Disorder bands same as DLC films at around 1350 and 1590 cm-1, respectively. Hence, these results indicated that the DLC contained copper composite thick film was deposited from DLC coated copper particles by CS technique. Average of friction coefficient between
the Cu-DLC composite film and SUJ2 ball was 0.41 while that of Cu film was 0.57. Therefore, friction coefficient of the Cu-DLC composite film was 30% lower than that of Cu film. Additionally, the observation of the film surface after BoD test, width of wear tracks on the Cu-DLC composite and Cu films were 450 and 650 nm, respectively. These results indicated the lubricant characteristic was brought to Cu film by introduction of DLC.

**PS2.22**

*Synthesis and Characterization of Highly Biocompatible Graphene Oxide Quantum Dots*  
Joel E. Ortiz-Santiago, Reynaldo Carrasquillo-De Jesus, Vitmary Rivera and Lisandro Cuncl; Universidad del Turabo, Gurabo, Puerto Rico.

Graphene Oxide Quantum Dots (GOQD) is a nanomaterial produced by a strong acid reaction in which carbon-based nanoparticles are exfoliated. GOQD have a size of ca. 10 nm, which have the potential to serve as a fluorescent agent for tumor detection and drug delivery into the brain. Their color depend on their size with bigger nanoparticles emitting lower energy photons. Also, GOQD exhibit high biocompatibility in mammal cells. Our objectives are focused on optimizing the methodology of the synthesis of this material to obtain a higher yield while characterizing their physical and chemical properties. We hypothesized that by making modifications in the synthesis, changing the time as well as the acids used, we can obtain the same results. The material obtained was exposed to a UV Lamp to confirm their fluorescence. A microplate reader was used to characterize their fluorescence using emission wavelengths ranged between 350 and 790 nm, showing a constant fluorescence peak at 550 nm. Raman spectroscopy was used to verify the completion of our synthesis. X-ray Diffraction was used to confirm the structure and purity of the sample, and the Atomic Force Microscopy was used to confirm the particle size. Our results showed that a pure quantum dots and small sizes were achieved and the synthesis lasted an average of 4 hours approximately, reducing the production period from 4 days. These results will help and provide to the scientific community a novel tool for future biomedical applications.

**PS2.23**

*Electronic and Magnetic Properties of Si-NPs-Doped Multwall Carbon Nanotubes*  
Sekhar C. Ray; Physics, University of South Africa, Johannesburg, South Africa.

The electronic structure and magnetic properties of silicon nanoparticles doped multwall carbon nanotubes (MWCNTs) were investigated using C 1s and Si 2p-2s X-ray photoelectron spectroscopy (XPS), ultraviolet photoemission spectroscopy (UPS), Raman spectroscopy and SQUID-measured magnetization M-H loops. The result of XPS indicates that silyl functionalization provides covalent carbon bonding among the graphene sheets and molecular attachment with carbon nanotubes, respectively, thus facilitating rapid and facile electron transport. As a result they are expected to exhibit improved electrical conductivities, moderate thermal conductivity, highly interconnected multiplexed topology with large internal surface areas thus promoting enhanced surface ion adsorption which makes these mesoporous materials viable candidates for use in harvesting thermos-electrochemical energy and energy storage technologies. We used complementary analytical characterization techniques including electron microscopy and tomography, x-ray diffraction, electrical property, Raman spectroscopy and Raman mapping in order to establish microstructure-processing-property correlations.

**PS2.25**

*Graphene-Mediated Surface Enhanced Raman Spectroscopy (G-SERS) and Detection of Biomolecules*  
Sanju Gupta and Alexander Banaszak; Western Kentucky University, Bowling Green, Kentucky, United States.

In this work, we prepare graphene-mediated surface-enhanced Raman scattering (G-SERS) platforms comprising few-layer graphene nanosheets decorated gold nanoparticle for biomedical and bio-nanotechnology.

Raman scattering is surface-sensitive and nondestructive inelastic light scattering spectroscopy technique. SERS, a specialized form of Raman spectroscopy, is useful for rapid and precise identification of small biomolecules and industrially relevant chemical dyes at ultralow concentration. This phenomenon is due to enhanced Raman signals by several orders of magnitude on the SERS-active surfaces. While the key point of SERS technology is the metal nanoparticles, which generates localized surface plasmon resonances in response to laser exposure and the resulting electromagnetic enhancement, controlling interparticle gap, the diameter of the metal nanoparticles and their ratio on graphene supports offer an advance toward sensitive G-SERS platforms via localized hybridization at graphene-metal interface. We have used low temperature thermal reduction technique to produce few-layer functionalized graphene supports and wet chemistry for size tunable gold nanoparticles as cost-effective facile synthesis approaches for G-SERS platforms. Simple and high-throughput arrays (so-called ‘biochips’) are developed by decorating graphene nanosheets with gold nanoparticles as well as sandwiching gold nanoparticle and few-layer graphene for cascaded signal amplification to differentiate nucleotide bases (adenine; A, thymine; T, cytosine; C, guanine; G) and to detect beta-carotene and malachite green chemical dye.

**PS2.26**

*Ultrathin 2D Film Irradiation by Highly Charged Ions Zinetula Z. Insepov1, 2, 3, Ardak Ainabayev2, Abat Zhuldassov3, Aidyn Shaikhov3 and Mititaka Terasawa1; 1 Nuclear Engineering, Purdue University, West Lafayette, Indiana, United States; 2 Nazarbayev University, Astana, Kazakhstan; 3 Condensed Matter, National Research Nuclear University, Moscow, Russian Federation; 2 LASTI, Hiroi, Japan.

Irradiation of 2D ultrathin films by highly charged ions (HCI) offers a shallow modification of theirs surfaces with ability to control density and size of defects by changing fluence of ions and kinetic/potential energies of ions. It is known that in order to get any structural changes in material irradiated by HCI, the 2D films should have as low as possible surface conductivity, in order to realize a Coulomb explosion mechanism of crater formation. By controlling potential and kinetic energy values one can sputter material from topmost surface of irradiated samples, for example, kinetic energy can be regulated to very small amount of few keV, that restrict ions further penetration into more deeper region of irradiated samples, while whole potential energy relaxes onto surface in nanometer volume. That allows avoiding formation of defects in deeper layers, which makes potentially HCI perfect instrument for nanostructuring, cleaning and surface modification for thin films such as graphene, BN or MoS2. However mechanism of defect formation during HCI interaction with 2D ultrathin films is not clear and it requires further investigations [1]. In general HCI is very good for formation few nanometer in diameter defects low conductivity materials. For carbon materials such as HOPG, carbon nanomembranes (CMN), and graphene it shown that high potential energy (charge state ~ q >25) and low kinetic energy (several keV) required to form induced friction type defect in graphene, hillocks in HOPG and nanopores in CMN [2-4]. In this study we used HCI to create defects and investigate their formation in 3D ultrathin films such as graphene, graphene oxide, BN and MoS2 using Raman spectroscopy, AFM and...
graphene is enhanced, effectively suppressing brain tumour growth. Based on its two-dimensional geometry, graphene can penetrate biological matrices. Composites of Carbon nanotube in polymeric matrices have thermal properties. One of the applications of CNTs is a filler in polymeric matrices. Carbon Nanotubes (CNTs) have superior mechanical, electrical and thermal properties. One of the applications of CNTs is a filler in polymeric matrices. Composites of Carbon nanotube in polymeric matrices have favorable electrical properties, which make them useful for applications such as photovoltaic devices and flat-panel displays. However, CNTs have a strong tendency to bundle together and that limits their applications. Therefore, appropriate dispersion process must be applied to use CNT in polymer composites to increase the electrical conductivity at lower CNT concentrations. In this study, an experiment was conducted to study the electrical percolation of CNT added into a polymer matrix. The study aims to show the percolation threshold can be lowered by exfoliating the CNT aggregation and dispersing individual CNTs in the suspension by using high-pressure wet-jet milling process. A commercially available thin MWCNTs produced via catalytic chemical vapor deposition and surfactant were mixed in distilled water at the concentration of 0.5 wt.%. and were pre-dispersed by ultrasonic homogenizer for 1 min. The pre-dispersed CNT fluid was dispersed using high-pressure wet-jet milling (WJM) process at an injection pressure of 50 MPa up to the processing of 100 times. The (2011). Single ion induced surface nanoarchitectures: a comparison between slow highly charged and swift heavy ions, J. Phys.: Condens. Matter. 23, 393001. [4] Ritter, R., Wilhelm, R.A., Stöger-Pollach, M. et al (2013), Fabrication of nanopores in 1 nm thick carbon nanomembranes with slow highly charged ions. Appl. Phys. Lett., 102, 063112.

**PS2.27**

A Novel Graphene-Photosensitizer Complex for Cancer Phototherapy

Si He Su and Jingjing Qiu; 1Mechanical Engineering, California State University Fullerton, Fullerton, California, United States; 2Mechanical Engineering, Texas Tech University, Lubbock, Texas, United States.

Based on its tow dimensional geometry, graphene can penetrate biological barriers for targeted therapy. However, compared to metal nanoparticles, graphene has limited photo to thermal conversion efficiency because of relative low near infrared light (NIR) absorption. Herein, through conjugation with photosensitizers, photo to thermal conversion ability of graphene is enhanced, effectively suppressing brain tumour growth. Specifically, to simulate the heating process inside biological tissue with graphene under NIR irradiation, graphene oxide was embedded in hydrogel and its temperature evolution under irradiation was experimentally and theoretically studied before in vitro and in vivo studies. Both results showed that increasing absorption ability through photosensitizer conjugation was a practical way to improve photo to thermal effects. Moreover, the conjugated graphene-photosensitizer was demonstrated to kill around 80% of U87-MG cancer cells in vitro and supress tumor growth in vivo.

**PS2.28**

Effect of High-Pressure Wet-Jet Milling Process on Reducing the Electrical Percolation Threshold of CNT Polymer Composite Film Using CNT Dispersion

Anas A. Almowarai1, Yoshiyuki Show1, Tetsu Endo1 and Tsubasa Yoshikawa2; 1Electrical and Electronic Engineering, Tokai University, Hiratsuka, Japan; 2Science and Technology, Tokai University, Hiratsuka, Japan.

Carbon Nanotubes (CNTs) have superior mechanical, electrical and thermal properties. One of the applications of CNTs is a filler in polymeric matrix. Composites of Carbon nanotube in polymeric matrices have favorable electrical properties, which make them useful for applications such as photovoltaic devices and flat-panel displays. However, CNTs have a strong tendency to bundle together and that limits their applications. Therefore, appropriate dispersion process must be applied to use CNT in polymer composites to increase the electrical conductivity at lower CNT concentrations. In this study, an experiment was conducted to study the electrical percolation of CNT added into a polymer matrix. The study aims to show the percolation threshold can be lowered by exfoliating the CNT aggregation and dispersing individual CNTs in the suspension by using high-pressure wet-jet milling process. A commercially available thin MWCNTs produced via catalytic chemical vapor deposition and surfactant were mixed in distilled water at the concentration of 0.5 wt.%. and were pre-dispersed by ultrasonic homogenizer for 1 min. The pre-dispersed CNT fluid was dispersed using high-pressure wet-jet milling (WJM) process at an injection pressure of 50 MPa up to the processing of 100 times. The (2011). Single ion induced surface nanoarchitectures: a comparison between slow highly charged and swift heavy ions, J. Phys.: Condens. Matter. 23, 393001. [4] Ritter, R., Wilhelm, R.A., Stöger-Pollach, M. et al (2013), Fabrication of nanopores in 1 nm thick carbon nanomembranes with slow highly charged ions. Appl. Phys. Lett., 102, 063112.

**PS2.29**

Fabrication of Nanocarbon by In-Liquid Plasma and Its Application

Tetsu Endo1, Yoshiyuki Show1, Tsubasa Yoshikawa1 and Anas A. Almowarai1; 1Electrical and Electronic Engineering, Tokai University, Hiratsu, Japan; 2Science and Technology, Tokai University, Hiratsuka, Japan.

Nanocarbons are used as a supporting material of platinum (Pt) catalyst for polymer electrolyte fuel cell (PEFC). Acetylene black, which is a kind of nanocarbon, is a popular supporting material, because it has high surface area and electrical conductivity. The acetylene black is generally formed from vapor phase. In this study, the nanocarbon is synthesized from liquid phase by using the in-liquid plasma method. Moreover, the synthesized nanocarbon is applied to the supporting material of Pt catalyst. A glass beaker with the volume of 50 ml was used as vessel in which the in-liquid plasma is generated. The ethanol or 2-propanol of 40 ml was filled into the beaker as a source substance of the nanocarbon. A pair of carbon rod (glassy carbon) was placed as electrodes in it. The distance of the electrodes was 1 mm. The unipolar pulse voltage of 4 kV was applied between them and generated plasma in the ethanol or 2-propanol. The generated plasma decomposes the ethanol and the 2-propanol molecules and synthesizes nanocarbon in it. The nanocarbon synthesized by the in-liquid plasma method showed aggregates of carbon particles with the diameter of less than 100 nm. When the 2-propanol was used as a source substance, the synthesized rate of the nanocarbon was 1.2mg/min, which was higher than that of the ethanol by 4 times. The nanocarbon synthesized by the in-liquid plasma was applied to a supporting material of platinum (Pt) catalyst for polymer electrolyte fuel cell (PEFC). The Pt particles as a catalyst was formed on the synthesized nanocarbon by the in-liquid plasma method, which was used Pt electrodes, [1]. The fuel cell was assembled with the Pt/nanocarbon catalyst synthesized by the in-liquid plasma method. The fuel cell showed the open voltage of 0.9 V and the maximum power of 65 mW/cm². The above results indicate that the nanocarbon synthesized by the in-liquid plasma works as the supporting material of the Pt catalyst for the fuel cell. Reference [1] Y. Show and Y. Ueno, Nanomaterials 2017, 7, 31; doi:10.3390/nano7020031

**PS2.30**

Fabrication of Pt/CNT Catalyst for Fuel Cell Using CNT Dispersion

Tsubasa Yoshikawa1, Yoshiyuki Show1, Tetsu Endo1 and Anas A. Almowarai1; 1Electrical and Electronic Engineering, Tokai University, Hiratsuka, Japan; 2Science and Technology, Tokai University, Hiratsuka, Japan.

Carbon nanotube (CNT) has high aspect ratio and high specific surface area. Therefore, the CNT is one of candidate supporting materials for platinum (Pt) catalyst in fuel cell, because the Pt catalyst requires to be supported on carbon material with the high surface area supports nanoscale particles. The commercial CNTs are generally an agglomerate with the size of up to 1 mm. Therefore, the effective surface area of the CNT agglomerate is not high comparing with that of individual CNT. It indicates that the CNT agglomerate needs to exfoliate into individual CNTs in order to apply the CNT into the supporting material for platinum (Pt) catalyst in fuel cell. In this paper, the CNT agglomerates are exfoliated by the wet-jet milling method. Our previous study showed the wet-jet milling method forms individual CNTs from the agglomerates and disperses them in the water [1]. This CNT dispersion fluid is stable without sedimentation for a long duration of time. This CNT dispersion fluid is an ideal material as the supporting material of Pt catalyst. The formation of the Pt catalyst on the CNT by the in-liquid plasma was carried out by the following procedure. A glass beaker with the volume of 50 ml was used as vessel in which the in-liquid plasma was generated. A CNT dispersion of 40 ml was filled into the beaker. Two pieces of Pt wire were added as an electrode in the CNT dispersion. The distance of the Pt electrodes was 1 mm. A unipolar pulse voltage of 2.8 kV was applied between them and the plasma was formed in the carbon black dispersion. The generated plasma spatters the surface of the Pt electrodes and disperses Pt particles in the carbon black dispersion. Therefore, Pt particles with the weight of 12 mg were formed on the surface of the CNT in the dispersion by the plasma processing time of 20 min. Polymer electrolyte membrane fuel cells (PEMFC) were fabricated with the Pt catalyst, which were formed on the CNT surface using the in-liquid plasma method. The fuel cell fabricated with the CNT, which was not applied in the in-liquid plasma, showed no output voltage, because no Pt catalyst existed on the
surface of the CNT. The fuel cells fabricated with the Pt particles, which were formed on the CNT surface by the in-liquid plasma method, showed 0.97 V in open voltage. A maximum output power of 3.8W was observed for this fuel cell. The above results indicate that the CNT supports the Pt particles and the Pt on the CNT works as a catalyst for the fuel cell.

Wednesday Morning, May 23, 2018
Room: Doyle/Rees

8:30 AM B3.01
Enhancement of Electronic Properties of Low-Boron Diamond Epilayers After $\text{Ar}_2\text{O}_3$ Etching on HPHT (100) Substrates
Cyrille C. Barbey1, Christine Met-Calfiti1, Nicolas Tranchant1, Samuel Saada1, Jean-Charles Arnault1, Ingrid Stenger1, Verena Züribg1, Lutz Kirstle1, Loto Oluwasayo2 and David Eon2; 1CEA LIST, Gif-sur-Yvette, France; 2Institut Néel, Grenoble, France; 3Fraunhofer Institute for Applied Solid State Physics IAF, Freiburg, Germany; 4Groupe d’Etudes de la Matière Condensée, Versailles, France.

Single crystal diamond behaves excellent skills for power electronic devices like its high breakdown voltage and the elevated mobilities for electrons and holes [1]. The main challenge remains the improvement of the crystalline quality which requires to lower the density of dislocations. Dislocations can originate from the defective subsurface of the HPHT diamond substrates after the mechanical polishing [2]. After threading into the epilayers, these dislocations emerge as pyramidal hillocks [3] affecting the devices electronic performance [4]. The removal of this defective layer is thus primordial to better control the crystalline quality of diamond epilayers. We investigated the effect of the $\text{Ar}_2\text{O}_3$ etching of HPHT (100) Ib Sumitomo substrates on the electronic properties of low boron doped diamond epilayers. This pre-treatment was first optimized tuning the RF-power, the pressure and the $\text{O}_2$ content to measure the etching rate and the RMS roughness. Optimized conditions led to fast etching rates up to 9 $\mu$m/h and to smooth surfaces (RMS roughness from 3.5 to 2 nm on 40x40 $\mu$m$^2$ areas). We performed a comparative study on two half-etched HPHT (100) substrates of different suppliers (Sumitomo Ib and New Diamond Technology Ia). After removal of 10 mm, the efficiency of the $\text{Ar}_2\text{O}_3$ etching was tested by evaluating the crystalline quality using Raman Spectroscopy and High Resolution X-ray Diffraction. The crystalline quality of low boron doped (10$^8$ at/cm$^2$) epilayers, 2 $\mu$m thick, grown simultaneously on the two etched substrates was compared to non-treated substrates by Raman and Cathodoluminescence. The SEM voltage contrast allowed to highlight the threading dislocations on non-pretreated areas and their removal after etching. Electronic properties investigated by Hall measurements show a clear improvement in term of carrier mobility and resistivity (from 3 to 1.7 W/m) on pre-etched area of Ib Sumitomo substrates. This project has received funding from the European Union’s Horizon 2020 Program under Grant Agreement no. 649947 (Greendiamond).

9:00 AM B3.03
A High Current Regime for Schottky-PIN Diamond Diodes
Hathwar1, Maitreya Dutta2, Franz A. Koeck1, Mehdi Saremi1, Srabanti Chowdhury1, Stephen M. Goodnick3 and Robert J. Nemaneich
1Arizona State University, Tempe, Arizona, United States; 2University of California, Davis, Davis, California, United States.

Diamond Schottky-PIN diodes with undoped intrinsic drift layers show very high current densities (>500A/cm$^2$) at low forward current voltage. We present temperature dependent I-V results of Schottky-PIN diodes fabricated on (100) p-type diamond substrates. Examination of the current density vs voltage shows an initial exponential dependence that is followed by a transition to a V$^2$ dependence. As the voltage is increased further the I-V reaches the linear I vs V dependence expected for ohmic limitation by the contact layers. The V$^2$ regime has been predicted for space charge limited current in Schottky diodes and has been described by the Mott-Gurney relation. The high current densities indicate an operational mode that is between that of a vacuum diode and a semiconductor Schottky barrier. In a vacuum diode space charge limited current exhibits a V$^{1/2}$ dependence as described by Child’s law. In a space charge limited Schottky diode, the space charge limited transport is further limited by phonon scattering resulting in a V$^2$ dependence described by the Mott-Gurney relation. A simple model is presented which displays the transitions of the three different regimes (exponential thermionic emission, V$^2$ space charge limited Mott-Gurney, and linear ohmic limited current). Temperature dependent results of the same diamond diode are presented and described in terms of the model. Perhaps the most stunning aspect of this effect is that the diode specific on-resistance ($R_{on}$) decreases as the voltage increases. The results indicate a new mode of operation of diamond power devices where the high carrier mobilities and low phonon scattering support current injection and drift such that the resistance is reduced as the current is increased. This research is supported through the ARPA-E SWITCHES program and the NASA HOTTech program.

9:15 AM B3.04
Charge Transport Characteristic in Diamond pn Diodes
Takehiro Shimokoa, Satoshi Koizumia and Tanaka Manobu;
1National Institute for Materials Science, Tsukuba, Japan; 2High Energy Accelerator Research Organization, Tsukuba, Japan.

Diamond $pn$ diodes have been studied to be utilized as deep ultra violet (DUV) light emitting diode and DUV sensor as well as to the basic research on power electronics applications. We expect the diode can be also applied for radiation detector under harsh environment such as nuclear reactor, accelerator etc. The advantages of $pn$ diodes are operation without
external bias voltage (photovoltaic) and a possibility to adjust sensitivity against radiations in the variation of energy range by doping profile design. In this study, we report transport characteristics of charges in diamond pn diodes created by alpha-particles injection. We formed pseudo-vertical diamond pn diodes. Homoeptaxial $p^-$, $n^-$, and $n^+$ - layers were grown on [111] HPHT type Ib single-crystal diamond substrate by MWPCVD. Mesa structure was formed by reactive ion etching to isolate each diode. Ohmic contacts were formed by EB deposition of Ti/Mo/Au both on the mesa structure of $n^+$-layer and on the $p^-$-layer. A fully depleted layer thickness and a built-in bias estimated by C-V characteristics were respectively 1.2 μm and 4.7 V. We measured alpha-particles from 241Am radioactive source were injected from the $n^-$ contact. Since the energy of alpha-particles is 5.486 MeV and their extinction range in diamond are 13μm, alpha-particles pass through the depletion layer of the diamond pn diode. The diode showed induced charge distribution by alpha-particles injection without external bias voltage (photovoltaic operation). We also evaluated bias dependency of charge collection efficiency (CCE) in the depletion layer. Thirty volts of reverse bias voltage was required for a CCE saturation. Expected electric field strength in the depletion layer was 0.3 MV/cm. Typically, diamond radiation detectors are made of several hundred microns of thick CVD diamond. They show a saturation of CCE at several kV/cm to 10kV/cm of electric field strength. Our sample requires more than ten times of higher electric field strength for the saturation than that of thick diamond detectors. In the case depletion layer thickness is smaller than extinction range of alpha-particles, electric field strength through depletion layer supposed be decreased by transiently increase of space charge density caused by electron-hole pair creation. Regarding as the CCE greater than 30 V of reverse bias voltage, charge multiplication was not observed up to 120 V, which is expected to be 1 MV/cm of electric field strength. We will further study charge multiplication process under higher field strength to extract impact ionization coefficient in diamond pn junction.

9:30 AM B3.05 Fabrication and Testing of High Power Diamond Schottky Diodes up to 1800V

Stephen Zaja 1, Aaron Hardy 2, Timothy P. Hogan 1 and Timothy A. Grotjohn 1; 1Michigan State University, East Lansing, Michigan, United States; 2Fraunhofer USA, East Lansing, Michigan, United States.

Diamond as a semiconductor material offers the promise of electronic devices with higher reverse breakdown voltages, higher operating powers, and higher operating temperatures when compared to silicon based electronics. These improved metrics are possible because of the unique characteristics of diamond such as a high breakdown electric field strength, high hole and electron mobility, and high thermal conductivity. A challenge has been growing epitaxial diamond material in the quantities and qualities needed for high power devices. Much of the past research has focused on understanding the material properties of diamond, and has succeeded in fabricating devices with high reverse voltages and high current densities, but the large area, practical devices have been elusive. More recent research has focused on looking at what is necessary to create these practical devices [1,2]. This talk will focus on the research undertaken to fabricate practical diamond Schottky diodes, and the incremental progress made increasing both the breakdown voltage and the forward current density. The starting point for this work are the results obtained in [3], which achieved a 240V breakdown voltage, and a 300 A/cm² forward current density with 200 μm diameter contacts. In order to achieve higher breakdown voltage, the doping concentration of the lightly boron doped layer is reduced by lowering the diborane level in the feed gas mixture. At the same time, 2% oxygen is added and the deposition temperature is raised to 900°C to maintain high quality epitaxial diamond growth. Vertical Schottky diodes are fabricated with p+- doped substrates to measure the properties of the grown diamond. Comparison is made between growing the p- drift layer on the p+ substrate, and a new technique in which the p- drift layer is grown first, followed by growing the p+ substrate. The diamond seed is then removed through laser cutting and polishing to reveal the p- drift layer. One end result on a 4 mm by 4 mm substrate with 200 μm diameter contacts and a boron doping level of 1 x 10¹⁹ cm⁻³ in the drift layer as measured by CV had a measured breakdown voltage of 1.8 kV, and a forward current density of 300 A cm⁻².


9:45 AM B3.06 Fabrication of Dual-Termination-Planar Diamond Schottky Barrier Diode

Dan Zhao, Zhangcheng Liu, Juan Wang, Jiao Fu, Yan-Feng Wang, Guoqing Shao, Jingwen Zhang, Shuwei Fan, Wei Wang and Hongxing Wang; Xi’an Jiaotong University, Xi’an, China.

Diamond is a promising semiconductor for future high-power and high-temperature applications due to its excellent properties, such as high breakdown field, wide band-gap and high carrier mobility, etc. Schottky barrier diodes (SBDs) with low forward voltage drop at forward bias and low leakage current at reverse bias are required. However, there is a trade-off between the forward voltage drop and the reverse leakage current in the design of conventional SBDs. Therefore, new design concepts are necessary to improve the device performances. It was found that the barrier height of metal contact on oxygen-terminated diamond is lower than that of metal contact on fluorine-terminated diamond. Thus, combining oxygen termination with fluorine termination to fabricate dual-termination SBDs may obtain special properties. In this research, the electrical properties of dual-termination-planar (DTP) Schottky barrier diodes (SBDs) on diamond have been investigated, in which oxygen-terminated area and fluorine-terminated area were obtained by ultraviolet ozone and ICP treatments. These DTP-SBDs obtained the same forward voltage drop as 1 MV/cm of electric field strength. We will further study the design of conventional SBDs.

10:00 AM BREAK

G3: Graphene and 2-D Materials III

Session Chair: Mario Hofmann

Wednesday Morning, May 23, 2018

Room: Agassiz/Fremont

8:30 AM G3.01 Defect Engineering in SnS₂ and MoS₂ for Solar Fuels with Enhanced Conversion Efficiency and Product Selectivity

Li-Chyong Chen; National Taiwan University, Taipei, Taiwan.

Photocatalytic CO₂ conversion to hydrocarbon fuels, the solar fuels, making possible simultaneous solar energy harvesting and CO₂ reduction, is considered a killing two birds with one stone approach to solving the energy and environmental problems. However, the development of solar fuels has been hampered by the low conversion efficiency and lack of product selectivity of the photocatalysts. Here, we present defect engineering (interstitial, substitutional, and vacancy) in chalcogenides as a viable method towards promising photocatalysts for CO₂ reduction reaction (CO₂RR). Specifically, two cases will be illustrated: the carbon-doped SnS₂ (abbreviated as SnS₂-C hereafter) nanosheets and single to few-layer MoS₂ with controlled vacancies by plasma treatment. For the first case, the SnS₂-C nanosheets with a typical layer thickness of ~40 nm were synthesized using an L-cysteine-based hydrothermal process. Compared with undoped SnS₂, the interstitial carbon doping induced microstrain in the SnS₂ lattice, resulting in different photophysical properties. Density functional theory calculations were performed for the formation energy, along with the CO₂ adsorption and dissociation on differently configured SnS₂-C for CO₂RR. Experimentally, the SnS₂-C exhibited a highly effective photocatalytic activity in gas phase with a photochemical quantum efficiency exceeding 0.7 % under visible light, which is ~250 times higher than that of its undoped counterpart, and also a world-record high value reported for inorganic catalyst. For the second case, the MoS₂ single to few layers were prepared by vapor transport deposition, followed by hydrogen plasma post-treatment. With increasing
hydrogen plasma treatment time, we observed a trend of blue-shift in the $A_p$ peak and red-shift in $E_{\text{g}}$ peak in their Raman spectra, implying creation of sulfur vacancies, of which the resultant stoichiometry ratio of Mo/S was further investigated by X-ray photoelectron spectroscopy. In addition, scanning tunneling microscopic images clearly supported that there were missing atoms in the MoS$_2$ layers after hydrogen plasma treatment. Productivity and selectivity of CO2RR were found to be strongly dependent with the different Mo/S ratios of the MoS$_2$ single to few layers. The role and interplay of the defects and the hosting materials as well as their effects on CO2RR will be discussed in this presentation.

8:45 AM G3.02
Solution Giant Gate Graphene FET (G3FET) pH Sensor
Samsul Mohd1, Shaili Falina1, Masataka Hasegawa2, Yoshinori Koga2 and Hiroshi Kawarada1; 1Waseda University, Shinjuku, Japan; 2National Institute of Advanced Industrial Science and Technology (AIST), Tsukuba, Japan.

The use of pristine exfoliated bilayer graphene grown by chemical vapor deposition to fabricate Giant Gate Graphene FET (G3FET) as a pH sensor will be reported. Several reports exist on graphene as pH sensors [1,2] and its increase sensitivity with defects induced methods [3,4]. In this project, we implement a mild anodic oxidation method to retain the pristine graphene condition and non-encapsulated device as pH sensor. Initially the project starts with two different substrates of bilayer graphene on p-type Si and quartz. A large dimension of 10 mm gate width ($W_g$) and 6 mm source drain length ($L_{SD}$) was fabricated hence the designated name for the FET device. G3FET shows a typical graphene FET output characteristics within the range of 0 V to -0.2 V of gate-drain voltage at V of 7. Transfer characteristics of the G3FET for a constant drain–source voltage of -0.15 V for wide range Carmody Buffer Solutions from pH 2 to pH 12 were used to analyze pH sensitivity. The pH sensitivity measured were ±12 mV/pH. Additionally, graphene surface was electrochemically oxidized using cyclic voltammetry method immersed in Carmody Buffer Solution pH 7 with potential region from 0.8 V to 1.3 V. A slight improvement of sensitivity increases up to ±22 mV/pH was attained. Further, we will demonstrate a device without encapsulation by replacing the source and drain with titanium metallization. Via this implementation, we took the advantage of naturally occurring oxide on titanium replacing the encapsulation, hence provide an unsophisticated fabrication process approach. References: 1. P.K. Ang, et al, 'Solution-gated epitaxial graphene as pH sensor', J. Am. Chem. Soc. 130 (2008) 14392–14393. 2. J. Ristein et al., 'Characteristics of solution gated field effect transistors on the basis of epitaxial graphene on silicon carbide', J. Phys.: D Appl. Phys. 43 (2010) 345303. 3. C.X. Lim et al., 'Direct voltammetric detection of DNA and pH sensing on epitaxial graphene: an insight into the role of oxygenated defects', Anal. Chem. 82 (2010) 7387–7393. 4. Mikhail Yu. et al., 'Monitoring of epitaxial graphene anodization', Electrochemica Acta. 238, (2017) 91-98.

9:00 AM G3.03
Enhanced Stability and N-Doping Effect of Al$_2$O$_3$ Passive Layer on MoS$_2$ Field-Effect Transistor-Based DNA Biosensor
Jung Pham1, Jhoain Lopez2, Mei Yang2, Youngwoo Rheem1 and Ashok Mulchandani1; 1Argonne National Laboratory, Lemont, Illinois, United States; 2University of Science and Technology Beijing, Beijing, China; 3Euclid TechLabs, Bolingbrook, Illinois, United States.

Hydrogen terminated diamond field effect transistors (FETs) have attained great attention due to their interesting properties and improved performance. In this work, we report H-terminated diamond FETs using two-dimensional (2D) h-BN as the gate dielectric. The FETs with h-BN and h-BN/Al$_2$O$_3$ as gate dielectrics are fabricated and the device characteristics are compared. We show that incorporation of 2D h-BN with conventional Al$_2$O$_3$ dielectric layer show improved device performance at much lower total dielectric layer thickness and is promising for the development of hydrogen terminated diamond based MISFETs.

9:30 AM G3.05
Carbon Addition in Metal Chalcogenides for Enhanced Performance of the Anode in Lithium-Ion Battery
Kuei-Hsien Chen1,2, Li-Chyong Chen2, Venu Gopal1 and Zeru Syum1; 1Institute of Atomic and Molecular Sciences, Academia Sinica, Taipei, Taiwan; 2Center for Condensed Matter Sciences, National Taiwan University, Taipei, Taiwan.

Metal chalcogenide is an attractive candidate for the anode material in lithium ion battery (LIB). However, the performance and lifetime still need to be improved. Two-dimensional SnS$_2$ grown on nitrogen doped carbon nanotubes (CNTs) becomes an approach to enhance specific capacity and cycling performance of Li-ion batteries. Herein, CNTs were prepared via a microwave plasma-activated chemical vapor deposition (MPECVD) and followed by the low-temperature solvothermal route to deposit uniform tin disulfide (SnS$_2$) nanosheet on the suractant. The resultant hybrid thin film we prepared as the core-shell assembly of SnS$_2$ nanosheet composite around CNTs exhibited a superior electrochemical performance of 1250 mAh/g after 120 cycles compare to the pristine SnS$_2$ of 981mAh/g after 100 cycles. Detailed characterization has been carried out to elucidate the unique architectures of the self-supported SnS$_2$/CNTs and its superior electrochemical performance. Meanwhile, carbon addition to CuZnSnS$_4$ (CZTS) has been demonstrated to be effective in high rate anode material with high capacity. Carbon coated CZTS electrodes were produced via a hydrothermal process with carbon precursor. The CZTS@C anode delivered a capacity of 830 mAh/g at a current density of 100 mA/g, which is much better in stability compared to the pristine CZTS without carbon addition. The excellent performance could be attributed to the high electrical conductivity of the uniform carbon coating. Detailed Raman and HR-TEM analysis have been performed to understand the role of carbon addition.

9:45 AM G3.06 DISCUSSION TIME
10:00 AM BREAK
Establishment of low resistivity n-type diamond formation technique is a great task and important for the electrical device applications. This is caused from deep donor level in the present n-type diamond doped with phosphorus. Hopping conductivity dominated in heavily P-doped sample is a hopeful solution against this problem. For this, we need to dope the concentration exceeding $10^{16}$ cm$^{-3}$. In such heavily doping regimes we face to the problem of significant drop of incorporation efficiency of P atoms from gas phase into diamond layers by CVD doping. We are solving the problem by modifications of CVD machine especially focusing on the gas flow [1]. Additionally we also revealed the influence of substrate off angle on the incorporation efficiency. Finally, we obtained the doping efficiency of P atoms into diamond with more than 5% using low off angled substrates even in heavy doping regime [2]. Recently one of the authors succeeded to grow thick [111] CVD layer on conventional HPHT diamond substrate. The surface of the thick layer exhibits clear step-terrace structure with excellent homogeneity of the morphology. In the present research we deposited heavily P doped diamond on as grown [111] CVD thick layers and characterized the crystalline nature and the electrical properties. [111] thick CVD layers were grown NIMS type microwave plasma CVD system [3] on HTHP Ib diamond (2×2×0.5mm$^3$) with the thickness of 70 μm. Then P-doped diamond thin films were grown on the thick layer using similar NIMS type microwave plasma CVD system designed specially to achieve high doping efficiency of P atoms. The growth conditions for P-doping are, CH$_4$/H$_2$: 0.05 %, PH$_3$/CH$_4$: 1% total gas pressure: 100 Torr at a substrate temperature 900–910 °C. The electrical properties have been characterized by Van der Pauw Hall measurements under AC magnetic field over wide temperature range (RT–873K). Impurity concentrations have been measured by SIMS depth profile analysis. The off angle of [111] thick layer was estimated within 0.5–1° from growth late and doping efficiency of P-doped layer varying with those of our data obtained from off angle experiments [2]. The off angle of diamond substrate, -2.5° shifted to lower off angle after thick layer growth. This is in good agreement with the situation observed in conventional diamond growth that exhibits low off angle area formation parallel to the edge and that expands the width with growth thickness increases. In this case, low off angle area grew wide enough to cover most of sample surface after 70 mm of diamond growth. P concentration of heavy doped layer was 8.7×10$^{19}$ cm$^{-3}$. Hall measurement results showed clear n-type behaviour at high temperature regime and hopping conductivity dominated at lower than 550K. Resistivity was about 47 Ωcm at RT and that is the lowest value ever obtained at P/C: 1% condition of CVD doping. It is confirmed that high crystalline perfection of thick CVD layer clearly helps to obtain high quality P-doped layer. [1] R. Ohtani, T. Yamamoto, S. D. Janssens, S. Yamasaki and S. Koizumi, Appl. Phys. Lett., 105, 232106–1–3 (2014). [2] T. Yamamoto, S.D. Janssens, R. Ohtani, D. Takeuchi and S. Koizumi, Appl. Phys. Lett., 109, 182102–1–5 (2016). [3] T. Teraji, T. Yamamoto, K. Watanabe, Y. Koide, J. Isoya, S. Omond, T. Ohshima, L. J. Rogers, F. Jelezko, P. Neumann, J. Wrachtrup, and S. Koizumi, Phys. Status Solidi A 212 (11), 2365–2384 (2015).
NIKOLAEV, K., BOLDYREV, A., RALCHENKO, V. 1; 1GENERAL PHYSICS

(DFWM) ranging from ~5 nm (R.T) to 1.75 nm (5 K). The thickness and peak at the wavelength of 602 nm with full width at half maximum centers in diamond with PL spectra (T = 5 – 300 K) showing intensive.

Doping from Germane In Situ Produced in Microwave Plasma by Single Crystal and Polycrystalline Diamonds with Ge-V Color Centers


Due to its wide band gap, high thermal conductivity, high carrier mobility and high breakdown field, diamond has been attracting much interest as the potential material of high-frequency high-power electronic device [1-3]. The device requires a high concentration of acceptors or donors, which could be obtained by the methods of doping. There are a great number of works on the doping of diamond. For n-type diamond, the nitrogen is the most common observed donor impurity and usually exists in natural diamond [4]. However, the quite-deep donor level (Eg ≈1.7 eV) is formed between the intermediate of diamond forbidden band, which makes it useless for semiconductor devices at room temperature [5]. As the same group V elements, arsenic is the shallower doping and expected as a more promising substitutional donor candidate [6]. The theoretical works showed that the substitutional arsenic provided the shallower donating level than phosphorus, at 0.4 eV below the bottom of the conduction band [7, 8]. Netherless, there is less common involvement of the arsenic related defects in diamond as far. In this work, the arsenic related defects of diamond were investigated by technology of low temperature photoluminescence, and some new results were presented and discussed. A slice of ultrapure colourless diamond was involved which was synthesized by MPCVD. The (100) surface orientation of the sample was implanted with arsenic ions at 300K, with an energy of 130keV and a dose of 1013 ions/cm2, and then annealed at temperatures of 400C, 800C and 1500C. The Photoluminescence examination was performed by Horiba micro-Raman spectrometers fitted with Linkam liquid nitrogen cooled stages at an excitation wavelength of 532 nm and recorded as a function of temperature in the 100–250K range. Reference [1] M. SCHWANDER, K. PARTES, DIAM. RELAT. PHYS. 20 (2011) 1287. [2] K. W. STEEDS, Z. LI, APPL. PHYS. LETT. 110 (2017) 152101. [3] M. A. PAIN, THURAY, T. TILLOCHER, N. HABKA, MATER. SCI. ENG. B 176 (2011) 1401-1408, [4] K. WANG, J. W. STEEDS, Z. LI, MATER. CHARACTER. 94 (2014) 14-18. [5] M. KASU, M. KUBOVIC, JAP. J. APPL. PHYS. 49 (2010) 110209. [6] A. P. L. BATISTA, F. R. ORNELLAS, SURFACE SCIENCE 641 (2015) 159-165. [7] S. J. SQUE, PHYS. REV. LETT. 92 (2004) 017402. [8] J. P. GOS, P. R. BRIDDON, R. J. EYRE, PHYS. REV. B 74 (2006) 245217.

10:30 AM D1.01

Improving the Lifetime of Ultrananocrystalline Diamond Microelectrodes for Dopamine Detection—Minimizing Surface Fouling via Electrochemical Cycling Prabhu U. Arumugam1, 2, 3, An-Yi Chang1, Gaurab Dutta1 and Shabnam Siddiqui1; 1Center for Biomedical Engineering Rehabilitation Science, Louisiana Tech University, Ruston, Louisiana, United States; 2Institute for Micromanufacturing, Louisiana Tech University, Ruston, Louisiana, United States.

Monitoring of extracellular neurotransmitters on a chronic basis is critical to the understanding and treatment of several brain disorders. Deep Brain Stimulation (DBS) has emerged as a viable alternative treatment method to standard medications and therapeutic intervention. To maximize clinical benefits and reduce side-effects, DBS relies on a closed-loop neurochemical feedback approach to guide modulation of the stimulation parameters required to achieve optimal results. Currently, electrochemical techniques using carbon fiber microelectrodes (CFM) are routinely applied to monitor changes in the levels of key neurotransmitters in the brain. But CFM require frequent chemical etching after use to clean their fouled surfaces and to maintain high sensitivity. This limits their useful lifetime to only few hours in many cases. In this research, we developed 250-μm boron-doped ultrananocrystalline diamond (BDUNCD) microelectrodes to detect neurotransmitters chronically with minimal loss of electrode sensitivity and electron-transfer kinetics. Specifically, we studied the

11:45 AM A2.06

Pre-Treatment Effects for P-Doped Diamond (100) Growth Using Pulsed Mode Deposition Xingye Wang, Franz A. Koeck and Robert J. Nemanich; Arizona State University, Tempe, Arizona, United States.

There is growing worldwide recognition that CVD diamond materials will impact future high-power electronics for applications that include power system distribution, electric vehicles and motor control. Nitrogen, a common impurity in natural diamond, has a covalent bond length (0.74Å) that is similar to diamond (0.77Å), but due to a lattice distortion, N incorporation exhibits a deep donor level at ~1.7 eV below the conduction band minimum. Phosphorus has been considered as another candidate for n-type doping, which has shown a donor level of ~0.6 eV experimentally. Phosphorus doping was initially achieved by incorporation during CVD growth on (111) diamond surfaces. Nevertheless, for practical applications, the growth of phosphorus-doped diamond on (100) surfaces is necessary. In this research, a pulse mode deposition method is employed to grow phosphorus-doped diamond layers on (100) single crystal diamond substrates. Different pre-treatment conditions including the usage of O/H plasma, H-plasma cleaning time and low CH4 plasma time were employed in the growth. The results indicate that with the employment of an initial O/H plasma or H/CH4 plasma, resulted in a higher P-doped diamond growth rate. In addition, a phosphorus doping concentration of ~1×1019 atoms/cm3 was achieved. Acknowledgement: this research supported by a grant from MWE Ltd.
surface biofouling due to dopamine (DA) oxidation and their by-products and the surface chemical fouling due to the application of anodic and cathodic potentials. We integrated the microelectrodes with microfluidics to study the fouling characteristics of BDUNC microelectrodes for the first time using amperometry and fast scan cyclic voltammetry and then develop an in vivo compatible electrochemical cycling-based surface cleaning method. A new understanding of the BDUNC microelectrodes’ properties for chronic DA measurements will be discussed applying voltammetry, scanning electron microscopy, silver deposition imaging and electrochemical impedance spectroscopy techniques.

10:45 AM D1.02
Antibody Modified Boron-Doped Diamond for Ultrasensitive and Label-Free Detection Influenza Virus Robert Bogdanowicz1, Dawid Nizdwozki2, Katarzyna Siuzdak3, Pawel Niedzialkowski4, Michal Sobaszek1, Paulina Weiher5, Miroslaw Sawczak3, Elzbieta Wnuk2, 5, W.A. Goddard III6, Andres Jaramillo-Botero7 and Tadeusz Ossowskii2; 1Faculty of Electronics, Telecommunications and Informatics, Gedan University of Technology, Gdansk, Poland; 2SensDx Ltd, Warsaw, Poland; 3Polish Academy of Sciences, Szewalski Institute of Fluid-Flow Machinery, Gdansk, Poland; 4Faculty of Chemistry, University of Gdansk, Gdansk, Poland; 5Institute of Biotechnology and Molecular Medicine, Gdansk, Poland; 6California Institute of Technology, Pasadena, California, United States.

According to the World Health Organization (WHO), almost 2 billion people each year are infected worldwide with flu-like pathogens including influenza. In this study, we describe a novel universal diamond biosensor, which enables the specific detection of the virus at ultralow concentrations, even before any clinical symptoms arise. The Si/BDD electrodes were synthesized in an MW PA CVD system (Seki Techntron AX5400S, Japan) on p-type Si wafers with (100) orientation. All samples were doped using diborane (B2H6) dopant precursor; [B]/[C] ratio was 10 000 ppm in the plasma resulting in an acceptor concentration of 3×1011 cm−3. The BDD surface was electrochemically functionalized using 4-aminobenzoic acid self-assembled monolayer (SAM), and anti-M1 antibodies were captured onto the SAM. The absorption of the M1 protein onto anti-M1 sites of the electrode change its electrochemical impedance spectra, which is then related to the viral concentration. The multifunctionalization of the BDD electrode surface by antibodies, by electrografting with diazonium salts, creates a novel approach for detection of influenza virus on an excellent detection level. We achieved a limit of detection of 1 fg/ml in saliva buffer for the M1 biomarker, which corresponds to ~10 viruses per sample in 5 mins. The limit of detection LOD = 3×SD/slope equals 0.7 fg. Furthermore, the universality of the assay was confirmed by analyzing different strains of influenza A virus. Modification of BDD electrodes and subsequent attachment of antibodies was confirmed by X-ray photoemission spectroscopy (XPS). The antibody–carboxyl interaction induces selectivity of the system leading to a high packing density of antibodies and electronic performance of sensor are confirmed by density functional theory (DFT) studies. The electrode stability and interference experiments revealed that the shape of the impedance spectra of the modified electrode is preserved after 24h of incubation in PBS buffer. Acknowledgements This work was supported by the Polish National Science Center (NCN) under Grant No. 2014/14/M/ ST5/00715 and 2016/21/B/ST7/01430. The DS funds of the Faculty of Electronics, Telecommunications, and Informatics and the Faculty of Chemistry at the Gdansk University of Technology are also acknowledged. R. Bogdanowicz wants to thank Prof. W. A. Goddard for the invitation and hosting in California Institute of Technology. The Fulbright Commission is acknowledged for financial support of this fellowship. References T. Matsubara, et al., PNAS 113, vol. 32 (2016); p. 8981-8984. D. Nizdwozki, et al., Sci. Rep. vol. 7(1) (2017), p. 15707.

11:00 AM D1.03
Technological Development for Commercialization of Transformational New Generation of Dental Implants Coated with Biocompatible/Corrosion Resistant Ultrananocrystalline Diamond (UNCD) Coating Karam Kang1, Jesus J. Alcantar-Peña2, Daniel Olmedo3, Sergio Renou2, Deborah Tasat4 and Orlando Auicelli1, 3; 1Materials Science and Engineering and Bioengineering, The University of Texas at Dallas, Richardson, Texas, United States; 2LLC Company, Original Biomedical Implants, Richardson, Texas, United States; 3Department of Oral Pathology, School of Dentistry, Universidad Nacional de Buenos Aires, Buenos Aires, Argentina; 4Department of History and Embryology, School of Dentistry, Universidad Nacional de Buenos Aires, Buenos Aires, Argentina; 5School of Science and Technology, National University of San Martin, San Martin, Argentina.

Pure titanium and titanium alloys are widely used in commercial dental implants and other orthopedics. However, these materials can suffer electrochemical corrosion when implanted in the human body, inducing the release of metallic ions/particles from the titanium surface, causing tissue inflammation and implant failure. A novel ultrananocrystalline diamond (UNCD) coating developed and patented by one of the authors (OA) and colleagues exhibit outstanding mechanical, biocompatible and strong resistance to chemical attack by body fluids, as shown previously for UNCD-coated Si microchip implanted in the eye to restore sight to people blinded by retinna degeneration. This presentation focus on describing the R&D performed to develop the technological approach to produce Ti-based dental implants coated with UNCD films using an industrial-type MPCVD large volume coating of dental implants for low cost fabrication. UNCD coatings were produced by flowing an Ar/CH4/H2 gas mixture previously developed to produce the patented UNCD coatings currently in the market in UNCD coated dental implants. UNCD-coated dental implants were not corroded as bare Ti-alloy implants. Histological evaluation of UNCD-coated Ti-alloy samples obtained using an in vivo experimental animal model bone implantation showed extremely good biocompatibility of the coating and osseointegration in the animal bone and NO particles ejection, as it occurs with current commercial Ti-alloy based dental implants. In addition, UNCD-coated cp-Ti and Ti-6Al-4V alloys exposed to artificial saliva (pH 6.5) showed no corrosion. In summary, the R&D to be discussed in this presentation shows the pathway for an industrial-scale process to produce UNCD-coated dental implants for insertion into the market in a foreseeable future.

11:15 AM D1.04
Science and Technology of Tailored Hydrophobic to Super-Hydrophobic/Corrosion-Abrasion Resistant/Biocompatible Micron to Ultrananocrystalline Diamond Coating Surfaces Ana G. Montañá1, 2, Jesus J. Alcantar-Peña2, Pablo Tirado2, 4, Alejando Abraham2, Elida de Obaldia2, 4 and Orlando Auicelli1, 3; 1Departamento de Investigación en Polímeros y Materiales, Universidad de Sonora, Hermosillo, Mexico; 2Department of Materials Science and Engineering, University of Texas at Dallas, Dallas, Texas, United States; 3Department of Bioengineering, University of Texas at Dallas, Dallas, Texas, United States; 2Department of Investigación en Física, Universidad de Sonora, Hermosillo, Mexico; 2Facultad de Ciencia y Tecnología, Universidad Tecnológica de Panamá, Panamá, Panama.

Polycrystalline diamond films with different grain size, ranging from ultrananocrystalline diamond (UNCD/3-5 nm) to nanocrystalline diamond (NCD/10-100s nm) to microcrystalline diamond (MCD/≥1 micron), were grown by the Hot Filament Chemical Vapor Deposition (HFCVD) technique and characterized by Raman spectroscopy, Atomic Force Microscopy (AFM), X-ray Photoelectron Spectroscopy (XPS), and Water Contact Angle (WCA) analysis. The formation of polycrystalline diamond films with grain structures from MCD to UNCD were confirmed by Raman analysis, which showed the characteristic peaks of these films. The difference in grain size was confirmed by calculations based on TEM.
Diffraction patterns. The wettability properties of all polycrystalline diamond films investigated were tailored from as-grown semi-hydrophobic to hydrophilic surfaces by oxygen plasma treatment, and to highly-hydrophobic by CF₄ plasma treatment of flat surfaces, and via synergistic tailoring of surface chemistry and morphology at the micro and nanoscale to super-hydrophobic. Oxygen plasma (30 seconds) treatment of Hydrogen-terminated surface of UNCD film, resulted in -O and -OH surface termination, as revealed by XPS analysis. AFM imaging of the plasma-treated UNCD films revealed no significant change in the surface roughness after either O₂ or CF₄ treatments when they were compared with the surface of the as-grown UNCD films. Nevertheless, as previously stated, a surface-chemistry alteration was confirmed by XPS, which is directly responsible for the change in the wettability behavior. On the other hand, a small increase of the WCA was observed as function of grain size from UNCD to MCD films. This effect provided the bases for exploring an additional process to increase even further the hydrophobicity of polycrystalline diamond film surfaces. Thus, subsequent research discussed in this abstract, revealed that the synergistic complementary effect of 3-D structured + plasma-induced fluorinated surface termination of UNCD, NCD and MCD films resulted in super-hydrophobic surfaces that revealed WCA up to 170 degrees, thus producing the highest super-hydrophobic surface of diamond material demonstrated today.

11:30 AM D1.05
Diamond Scaffolds for Bioengineering Applications Aaqil Rifai1, Elena Pirogova1, Andrew D. Greentree2 and Kate Fox1, 3; 1School of Electrical and Biomedical Engineering, RMIT University, Melbourne, Victoria, Australia; 2ARC Centre of Excellence for Nanoscale BioPhotonics, School of Science, RMIT University, Melbourne, Victoria, Australia; 3Center for Additive Manufacturing, RMIT University, Melbourne, Victoria, Australia.

With increasing frequency of hard tissue replacement and fracture treatment, novel materials are required to provide long term solution. Orthopaedic implants are commonly fabricated using metallic scaffolds, where the biological aspects are a by-product of the metallic interface surrounding the bone or soft tissue. Although metals have proved to be effective, it is important that we investigate alternative biomaterials. Due to the in vivo biocompatibility of carbon, bio-interfacing carbon scaffolds are examined. Nanodiamond is an ideal bio-interfacing material as it provides a platform for bioactivity and osseointegration. To understand the new material, a comprehensive characterisation and interface assessment is undertaken. Additively manufactured titanium samples are first developed using selective laser melting to form three-dimensional scaffolds. The titanium is coated using optimised nanodiamond. Nanodiamond coated selective laser melted titanium scaffolds are examined in a range of biomedical settings to map diamond incorporation with the cellular biocompatibility and bacterial attachment to the scaffold.

As a result, we have altered the nanodiamond material interface to enhance the bioactivity of the implantable scaffold. This facile method of nanodiamond synthesis represents a promising platform for an array of superior bio-interfacial implants.

1:30 PM D2.01
Influence of Embedded Plasmonic Ag Nanoparticles on Photocatalytic Response of Diamond Thin Films Robert J. Hamers, Shuo Li and Jason Bandy; Chemistry, University of Wisconsin-Madison, Madison, Wisconsin, United States.

H-terminated diamond is well known to be an excellent electron emitter when excited with above-band light due to diamond’s unusual property of negative electron affinity. One drawback to diamond is the fact that excitation of electrons to the conduction band requires short-wavelength excitation, <225 nm wavelength, to exceed diamond’s 5.5 eV bandgap. One approach to overcoming this large bandgap is to use diamond-metal heterostructures, as metal with lower work functions can provide a pathway to excitation from the metal valence band to the diamond conduction band. Recently we have investigated another approach to enhancing diamond’s optical properties by embedding Ag nanoparticles into the diamond film. Ag has a lower work function that diamond, while the plasmonic properties of Ag can enhance the optical response and concentrate the electric field. Here we show that incorporation of <50 nm Ag nanoparticles into diamond films significantly increases the photoelectric emission and photocatalytic activity of diamond. We have measured the optical response Ag-embedded diamond films and also measured the electron emission into vacuum and into water. In both cases, electron emission is clearly observed at sub-bandgap wavelengths, and the incorporation of Ag nanoparticles leads to a significant enhancement in photocatalytic yield for the photo-induced reduction of N₂ to NH₃. This reaction has an activation barrier of 3.1 eV, and therefore the ability to produce NH₃ from N₂ in water cannot be accomplished by traditional electrochemical schemes, but requires electrons in water with sufficiently high energy to produce solvated electrons and the solvated hydrogen atom H. Since incorporation of Ag into the film is also accompanied by an increase in graphitic carbon, there are several possible pathways to enhancement of electron yield. In this talk we will discuss some of the possible mechanisms of enhancement and discuss the prospects for enhancement of diamond’s photocatalytic properties using embedded plasmonic nanoparticles.

1:45 PM D2.02
Photochemistry with Diamond Jonathon Barkl, Anna Zaniewski and Robert J. Nemanich; Physics, Arizona State University, Glendale, Arizona, United States.

This project examines the feasibility of conducting photochemistry in the visible light spectrum by utilizing thin diamond films in an aqueous solution. As a semiconductor, diamond is unique due to its wide band gap of 5.5 eV. The unique band structure enables hydrogen terminated diamond to have a negative electron affinity, meaning the conduction band edge is at a higher energy than the resting energy of an electron in vacuum. This property enables the emission of electrons from the surface of the diamond into the aqueous solution, creating an “energy reservoir” that can be used to initiate energy intensive chemical reactions. Previous studies have demonstrated this ability and the subsequent use of the aqueous electrons to induce the reduction of nitrogen to ammonia through utilizing light in the ultraviolet spectrum. This project explores the properties of the diamond films, substrates, and experimental setups in order to conduct the same reduction reaction while using light in the visible spectrum by lowering the effective work function of the diamond such that the energy required to emit electrons is achievable with visible light.
Effects of Deposition Parameters on the Surface Morphology and Wear Performance of Monolayer CVD Diamond Grinding Tools
Xiaotian Shen and Fanghong Sun; School of Mechanical Engineering, Shanghai Jiaotong University, Shanghai, China.

The hot filament chemical vapor deposition technique (HFCVD) is used to fabricate monolayer grinding tools with high-quality diamond grains. The high pressure and high temperature (H-PHT) diamond seeds are dispersed on substrates uniformly by a spin coater machine. Then simultaneous growth of CVD diamonds on both seeds and substrates is employed which anchor the seeds on substrates. An investigation is undertaken to explore the effects of deposition parameters on the growth behavior and wear performance of diamond grains. The seeds are grown with varying amounts of deposition parameters including carbon concentration, reactive pressure, substrate temperature and bias intensity. The morphology and quality of as-grown diamond grains are characterized by the field emission scanning electron microscopy (FESEM), X-ray diffraction (XRD), and Raman spectroscopy. In order to evaluate the grinding performance of the diamond grains, the wear and failure mechanism of grains are tested by grinding of SiC ceramics. The grinding forces are measured and the morphologies of diamond grains as well as SiC ceramics are observed. The results indicate that the growth of nano-diamonds induces the formation of spherical polycrystalline grains, while the growth of large micron-diamonds leads to the formation of cube-octahedral single crystalline grains. Furthermore, surface defects of original seeds are eliminated under a set of optimized parameters, and thus high-quality single crystalline grains with smooth diamond planes can be fabricated. The grinding results demonstrate that the main wear mechanisms of the grains are attritious wear and fracture, while pullouts of grains can be hardly observed. Besides, the wear rates of single crystalline grains are significantly lower than that of the polycrystalline grains.

Diamond Detectors for Uses in a Proton Therapy Beam
Holly Johnson1, 2, Jason Holmes1, Franz Koeck1, Raghuraj Hathwar1, Anna Holly1

Diamond-based proton detector. We acknowledge ARPA-E (Grant DE-AR0000453), National Science Foundation (DMR - 1710551), NASA Space Grant, and the ASU-Mayo Clinic Seed Grant.

Proton beam therapy is a form of cancer treatment that allows us to target and treat cancerous cells using high-energy protons. The protons pass through the skin and tissue and release a majority of their energy at a specific depth; this peak of energy deposition is known as a “Bragg Peak”. In order to only target tumors and avoid affecting healthy cells, it is necessary to have precise knowledge of the beam’s energy and position. However, current silicon-based detectors are damaged by the radiation and need to be replaced often, require frequent calibration, and are susceptible to noise due to its small band gap of 1.14 eV. Diamond has a band gap of 5.45 eV, meaning it is less susceptible to thermal noise and is more robust to radiation damage than silicon. In this project, we demonstrate a diamond-based proton detector. We acknowledge ARPA-E (Grant DE-AR0000453), National Science Foundation (DMR - 1710551), NASA Space Grant, and the ASU-Mayo Clinic Seed Grant.

Controlling Directional Liquid Motion on Diamond and Diamond/β-SiC Composite Films for Microfluidic Devices
Tao Wang; Shenzhen Institutes of Advanced Technology, Chinese Academy of Sciences, Shenzhen, China.

Control of wetting and directed liquid transport is key for microfluidic devices and biosensors. Here, we report a superhydrophobic diamond film and diamond/SiC gradient films synthesized by using a hot filament chemical vapor deposition (HFCVD) technique and its application as robust and chemically inert means to actuate water and hazardous liquids. The wettability of the diamond film was influenced by the topography (roughness). By designing cauliflower like structures combined with micro-/nanodiamond, superhydrophobicity was achieved. For the gradient surface, the diamond/β-SiC ratio of the composite films gradually changed from pure diamond to β-SiC. Water was transported via the gradient from the hydrophobic (hydrogen-terminated diamond) to hydrophilic side (hydroxyl-terminated β-SiC) of the gradient surface. The driving distance and velocity of water was influenced by the surface roughness. The droplet moved a longer distance with a maximum velocity on the nanogradient surface. As diamond and β-SiC are chemically inert, the gradient surfaces can be used to drive hazardous liquids and reactive mixtures, which was signified by the actuation of hydrochloric acid and sodium hydroxide solution. In addition, the length of the gradient is tunable to the anticipated application. We envision that the superhydrophobic diamond and diamond/β-SiC gradient surfaces have high potential as actuator for water transport in microfluidic devices, DNA sensor and implants which induce guided cell growth.
Carbon materials with one or more dimensions in nanoscale exhibit, among others, astonishing mechanical, thermal and electrical properties, combined with extremely high surface areas. Properties such as Young’s modulus in the order of 1 TPa, strength between 50-150 GPa, metallic to semiconducting electrical performance and thermal conductivity up to 3500 W mK⁻¹ are the main reasons behind the constant interest of the scientific community across many disciplines for these different forms of carbon. The properties and performance of these materials are governed by their structure, physical dimensions and geometry. In this review I will focus on the utilization of different forms of nanocarbons to tune the mechanical properties of polymer materials, highlighting the factors that govern the incorporation of nanocarbon fillers in the polymer matrix. Polymers represent a significant class of materials due to their versatility, variety and availability from both natural and synthetic processes. Their numerous applications ranging from structural materials, adhesives, pharmaceuticals and biomedical materials impact significantly both our society and economy. Composite materials in which the main component is polymer and a foreign material is introduced as a filler, represent an efficient and elegant way to tune the performance or even induce new properties to the host polymer material. Here, we will focus on the mechanical properties of polymers and how they are influenced by the incorporation of synthetic nanocarbon fillers. We will categorize these effects by filler geometry and hosting polymer type (synthetic/natural) and explore which parameters control the mechanical reinforcement. The nanocarbon forms we will discuss are nanodiamonds, carbon nanotubes and graphene. Their geometry, surface area and surface chemistry are the key factors to control their dispersion, adhesion, alignment and confinement in a polymer matrix, which ultimately define the level of mechanical reinforcement. Another equally critical factor to achieve control over the mechanical properties of a polymer composite is the fabrication method itself. Modern additive manufacturing technologies have provided alternative methods to design materials that exhibit unique, unprecedented, engineered properties. Utilizing technologies such as stereolithography and two-photon polymerization to produce architectured polymer materials has shown that we can attain previously unexplored performance by design. These architectured polymer materials provide a new exiting platform to study phenomena occurring upon nanofiller incorporation. In this perspective, the host material’s geometry is also a decisive factor for the performance of the composite and by tuning it to approach dimensions close to the ones of the filler, we can utilize filler confinement and alignment to unravel otherwise unattainable mechanical reinforcement levels. In our previous studies we have demonstrated that the new superlubricity mechanism at macroscale by combined uses of graphene mixed with nanodiamonds sliding against diamond-like carbon (DLC) [1]. In particular, we showed that superlow friction regime (the coefficient of friction is 0.004) is observed when graphene patches wrap around the nanodiamonds and form nanoscrolls with reduced contact area sliding against an inconspensurate DLC surface. In the present study, we show that other two dimensional (2D) layered materials such as molybdnum disulfide (MoS₂) is also capable of demonstrating superlubricity through unique tribochemical reaction with carbon leading to formation of onion-like carbon (OLC) at the tribological interface. We have observed that beyond some initial run-in period, the friction comes down to some un-
measurable levels and maintains in that state for a very long period of time, despite the fact that introduced 2D film of MoS$_2$ is only a few nanometer thick. Our detailed experimental and theoretical investigations suggest that formation of OLCs is possible through tribochemical reaction with these 2D materials that could occur at the tribological contact due to high contact pressure. These OLCs behaves in a similar way described earlier in our previous studies [1], providing reduced contact area and incommensurability with respect to the sliding DLC surface leading to superlubricity. We will discuss the detailed mechanism and highlight the similarities and differences with the previously demonstrated superlubricity involving graphene-nanodiamond ensembles. This new discovery broadens the fundamental understanding of frictional behavior of 2D materials beyond graphene and opens a wide range of possibilities for implementing them in mechanical and tribological applications involving static, sliding, and rotating contacts. References: 1. Macroscale Superlubricity Enabled by Graphene Nanoscroll Formation D. Berman, S. A. Deshmukh, S. Sankaranarayanan, A. Erdemir, and Anirudha. V. Sumant Nature Science, 348, 1118-1122, (2015). 2. Operando Tribochemical Formation of A. Deshmukh, S. Sankaranarayanan, A. Erdemir, and Anirudha. V. Sumant in involving static, sliding, and rotating contacts. The formation of BNC$_3$ from molecular sources is also interpreted in terms of concerted intra- and inter-tetrahedral B, N and C displacements. The formation of BNC$_3$, from molecular sources is also briefly discussed.

Density functional theory is used to elucidate the fundamental properties of a hypothetical BNC nano-alloy comprised entirely of covalently linked near-tetrahedral “B-N-C” units. The unique structure and composition is analogous to that of recently synthesized hybrid III-V/IV alloys, such as AlP$_{3}$S, which adopts a silicon-like structure. The Clc1 ground state structure of BNC$_3$, is predicted to be dynamically stable and almost perfectly cubic, with a lattice parameter only slightly larger (~1%) than that of diamond. Its calculated bulk modulus is ~13% smaller than that of diamond, but slightly larger than that of cubic BN. Thermodynamically BNC$_3$, is found to be stable relative to elemental reference states, but metastable relative to disproportionation into cubic BN and carbon (graphite and/or diamond) in analogy with its AlP$_3$S analog. Orientational disordering of the “B-N-C” raises the lattice energy by only ~52 meV/atom, while a pseudo-random BNC$_3$ alloy is found to be considerably less stable (~233 meV/atom). The direct and indirect band gaps of the ordered ground state are predicted to be E$_{\text{opt}1}$ = 6.38 eV and E$_{\text{opt}2}$ = 4.72 eV, about 5% and 8% smaller than their diamond counterparts, respectively. This leads to a moderate increase in the absorption coefficient compared to diamond over the 6-10 eV range, and a ~0.4 eV red shift in the absorption edge. Infrared and Raman spectra obtained using density functional perturbation theory reveal a rich vibrational structure which can be interpreted in terms of concerted intra- and inter-tetrahedral B, N and C displacements. The formation of BNC$_3$, from molecular sources is also briefly discussed.

The low-cost development of high energy lithium ions rechargeable batteries is of considerable technological importance. Sulfur is a promising cathode material for lithium sulfur battery due to its high theoretical capacity (1675 mAh/g). However, Sulfur cathodes generally suffer from fast capacity fading and low coulombic efficiency originating from the dissolution of intermediate discharge products (polysulfides, Li$_2$S) in the electrolyte. The dissolution of polysulfide can cause loss of active sulfur and suppresses its deep lithiation during charge/discharge processes and deteriorates electrochemical performances even at low cycling rates. Therefore, we need to control volume fluctuations of sulfur upon cycling, suppress the dissolution of the sulfur reduction intermediates, and improve ionic and electronic conductivities of sulfur and its various discharge products. An effective way to overcome these challenges is to bind the Li$_{x}$S$_{x}$ species to host materials to suppress the polysulfide shuttle, thus enhancing the cycling stability of Li-S batteries. Adding ferroelectric with large internal field, such as BiFeO$_3$ to the cathode material may help in trapping the resulting polysulfides on repeated cycling. Carbon frameworks are also known to improve the electrical conductivity of sulfur cathodes and trap soluble polysulfides during cycling. In this context, we report an active cathode $S_{x}$-xCx (x=0.5, 0.1 and 0.15) composites combined with 10% of pure phase BiFeO$_3$ powder fabricated by ball-milling technique for lithium sulfur batteries. Highly conductive carbon black powder and BiFeO$_3$ have been dispersed in sulfur to enhance the electrochemical performance of sulfur batteries. The characterization of these nanostuctured composites has been performed by X-ray diffraction (XRD), Field emission scanning electron microscopy (FESEM) and Raman spectroscopy. The electrochemical performance of sulfur composite cathodes has been characterized utilizing SOLATRAN battery tester, while lithium ions intercalated and de-intercalated.

Nanodiamond, Graphene and Carbon Nanotube Enabled High-Capacity and Long Cycling-Life Silicon Based Lithium-Ion Battery Anodes Youhu Tzeng, WeiChih Huang and MinSiang Huang; Electrical Engineering, National Cheng Kung University, Tainan, Taiwan.

Modern needs by electric vehicles and mobile devices for high-capacity and long-cycling-life lithium ion battery rely on innovative battery
Electrodes to be invented. The most commonly applied graphite anode provides only about 400 mAh/g charge storage capacity. Silicon, when fully charged, provides about 4000 mAh/g theoretical charge storage capacity, which is about 10 times that of its graphite counterpart. However, cycling between a fully charged and discharged silicon anode causes the volume of silicon to expand and shrink by as much as about 400%, which may lead to pulverization of silicon and the loss of electrical contacts between breakoff silicon and the current collector of a battery. The increased silicon surface of pulverized silicon reacts with the electrolyte to form solid-electrolyte interphase and caused the limited supply of electrolyte and lithium to be depleted prematurely leading to severe shortening of battery lifetime. Coating of nanodiamond with novel grain-boundary engineered nanostructures, vertically grown nanocarbon/graphene walls, carbon nanotubes and carbon fibers on silicon provides means of increasing physical integrity, chemical inertness, electrical conductivity and multiple-path connectivity of silicon in the anode. In this paper, we will present several excellent means of maintaining charge storage function of silicon anode after a large number of cycles between charged and discharged lithium ion battery. High capacity silicon anode with more than 2000 mAh/g and capable of cycling for more than 100 times almost without any noticeable degradation has been achieved. Materials and electrical characteristics, electrochemical properties, and mass production issues will be discussed.

C3: Diamond Photonics/Spintronics III
Session Chair: Tokuyuki Teraji
Wednesday Afternoon, May 23, 2018
Room: Doyle/Rees

3:30 PM C3.01
Spin Transport in B-Doped Diamond
Ching-Wei Tsao, Xiangbing Jiao, Zhiyu Huang, Tingyong Chen, Quan Qing and Robert J. Nemaniich; Arizona State University, Tempe, Arizona, United States.

Diamond, as a unique form of carbon and a rising star of the next generation of electronic materials, possesses the highest hardness and thermal conductivity and high electron and hole mobilities leading to high-temperature, high-power and radiation-hard electronics where conventional Si-based electronics fail. Significantly, diamond is a proven solid-state platform for spin-based quantum devices. Optically addressable spin of the nitrogen-vacancy (NV) centers in diamond has been used to realize small-scale quantum information processing and quantum sensing under ambient conditions. Furthermore, the NV center has the longest spin coherence time (2 ms) of any solid-state system at room temperature. These properties may enable quantum computing at room temperature while other quantum computing systems such as superconducting Josephson junctions require cryogenic temperatures. However, large scale quantum computing in diamond still faces a major challenge of communication between the spin states of a large number of NV centers. Electron spin transport has been proposed for this purposes. Carbon, a light element with small spin-orbit coupling, is expected to be an ideal spin transport material, where the coherent transport of spin can extend across macroscopic length scales at room temperature. Demonstration of spin transport in diamond has been limited due to difficulties in high purity diamond growth and nanofabrication of diamond. In this project, we fabricate lateral spin-valve structures and Hall bars to characterize spin transport in B-doped diamond. Epitaxial B-doped layers (~50nm thick) were grown on (100) diamond substrates using microwave plasma CVD. Electron beam lithography was used to define conducting bars on the surface and to pattern metal contacts. The devices were characterized at room temperature and at < 10K. Our preliminary results show signatures of spin transport that are observed in heavily doped diamond films. Acknowledgment: this research is supported by grants from the Air Force Office of Scientific Research (FA9550-16-1-0052), the U.S. Department of Energy, Office of Science (SC0012670), and the National Science Foundation (DMR - 1710551).

3:45 PM C3.02
Submicron Single Crystal Diamond Thin Film for Photonics and Quantum Sensing Applications
Kumaravelu Ganesan1, Alastair D. Stacey1, Athavan Nadarajah1, Patrick Salter2 and Steven Prawer1; 1School of Physics, University of Melbourne, Parkville, Victoria, Australia; 2Department of Engineering Science, University of Oxford, Oxford, United Kingdom.

Integrated photonic quantum information processing and sensing devices are of growing interest for a number of applications such as high-performance nonlinear optics, optomechanics, sensing and metrology. To enable applications beyond traditional classical optics, innovative materials are necessary to provide the tools for chip-based quantum information processing. Diamond is a particularly attractive candidate material because of a unique combination of desirable material properties, including a high refractive index, exceptionally high thermal conductivity and high Young’s modulus. High quality, single crystal membranes with low-level impurities and low absorption loss and of acceptable size are a prerequisite to meet the demanding requirements targeting large photonic circuits and sensing devices. In the present work, we addressed two key challenges in order to bring laboratory demonstrations closer to real-world applications; (1) high quality diamond membranes and (2) methods for processing diamond at larger scales. We demonstrate a set of techniques for the fabrication of sub-micron single crystal diamond membrane windows (SCDMW), from single crystal type-IIa diamond seeds. The membrane sizes are up to 3x3 mm and the thickness ranges from 100nm -1mm and are supported by diamond scaffolds for ease of handling and further processing. The optical and mechanical quality of these membranes were tested and proved to be suitable for photonics and quantum sensing applications. We also successfully engineered good quality NV centers using femtosecond laser writing [3] as well as nitrogen implantation techniques. Several characterizations including Raman, photo luminescence and mechanical resonance were carried out to assess the quality of the fabricated diamond membranes. A nanophotonic device, optical ring resonator, was fabricated on one of the membranes. Confocal microscopy and ODMR measurement were performed on the NV centers engineered by a combination of femtosecond laser irradiation and thermal annealing. The fabrication techniques are scalable and offering great prospects as a platform for integrated photonics, quantum information processing and sensing devices. References [1] Piracha, A. H., Ganesan, K. et al. Scalable fabrication of high-quality, ultrathin single crystal diamond membrane windows. Nanoscale, 8(12) (2016). [2] Piracha,A.H., Rath, P., Ganesan, K. et al Scalable Fabrication of Integrated Nanophotonic Circuits on Arrays of Thin Single Crystal Diamond Membrane Windows Nano Letters, 16 (5), pp. 3341-3347 (2016) [3] Chen, Y-C et al Laser writing of coherent colour centres in diamond, Nature Photonics, 11 (2), pp. 77 (2017)

4:00 PM C3.03
Progress Towards a Nitrogen-Vacancy Color Center Laser
Jan Jeske1, Desmond Lau1, Xavier Vidal1, Liam McGuinness1, Philipp Reineck1, David A. Simpson2, Brett Johnson3, Marcus W. Doherty4, Sarah R. Nair5, Andrew Wood6, Ondrej Kitzler2, Rich Mildren2, Jeffrey McCullum3, Fedor Jelezko1, Shinobu Onodera, Takeshi Ohshima4, Thomas Volz2, Jared H. Cole1, Brant C. Gibson2 and Andrew D. Greenstreet4; 1RMIT University, Melbourne, Victoria, Australia; 2Macquarie University, Sydney, New South Wales, Australia; 3Universitat Ulm, Ulm, Germany; 4University of Melbourne, Melbourne, Victoria, Australia; 5Australian National University, Canberra, Australian Capital Territory, Australia; 6National Institutes for Quantum and Radiological Science and Technology, Takasaki, Japan.

The negatively charged nitrogen-vacancy color center is an astounding diamond defect that is finding applications including quantum sensing, quantum cryptography, and quantum information processing [1]. Since at least 1986, it has also been proposed as laser medium [2]. The original motivation was to explore nitrogen-vacancy lasers as a tunable laser source across its broad phonon sidebands from 637nm to around 800nm, however no such laser has yet been realized. More recently, it has been shown that a nitrogen-vacancy laser would provide an alternative approach to readout for a nitrogen-vacancy magnetometer [3]. Because the readout would be coherent, rather than the conventional incoherent readout for optically detected magnetic resonance, enhanced sensitivities are predicted. We recently showed stimulated emission from nitrogen-vacancy...
Design and Fabrication of a Diamond Immersion Metalens for Nanophotonics, AMOLF, Amsterdam, Netherlands; 3Electrical and Computer Engineering, University of Texas at Austin, Austin, Texas, United States; 4Physics, University of Pennsylvania, Philadelphia, Pennsylvania, United States; 5Singh Center of Nanotechnology, University of Pennsylvania, Philadelphia, Pennsylvania, United States.

Quantum emitters such as the diamond nitrogen-vacancy (NV) center are the basis for a wide range of quantum technologies. However, refraction and reflections at material interfaces impede photon collection, and the emitters’ atomic scale necessitates the use of bulky, intricate optical measurement setups that prevent packaging of quantum devices. To overcome these limitations, we present the design and fabrication of a metasurface composed of nanoscale diamond pillars that acts as an immersion objective to collect and collimate the emission of an individual NV center [1]. Excellent agreement between metasurface design and performance can be seen by comparing the 3D finite-difference time-domain simulations and the measured transverse and axial profiles. Photoluminescence (PL) images are collected simultaneously from the metasurface and an oil-immersion objective focused through the backside of the high-pressure, high-temperature diamond substrate. Both images exhibit an NV center at the same lateral position, and the background-subtracted spectra of both paths clearly show the NV zero phonon line at ~10 nm to 100 nm depending on experimental conditions. UV-vis spectra clearly show the plasmonic peaks in good correspondence of SEM. TEM analyses show the boundary between the diamond-Ag nanostructures, which has some voids but generally shows columnar growth of diamond extending radially from the Ag nanoparticle core. Electromagnetic simulation results of the diamond-Ag composites also suggest possible air voids and graphite phases in the structure. The plasma-assisted Ag NPs embedded in diamond is a unique way to impart tunable optical properties to diamond thin films.

4:30 PM C3.05
Design and Fabrication of a Diamond Immersion Metalens for Quantum Emitters Tzu-Yung Huang1, Richard Grote1, Sander Mann2,3, David A. Hopper4,5, Annemarie Exarhos4,5, Gerald Lopez1, Erik Garnett2 and Lee Bassett1; 1Electrical and Systems Engineering, University of Pennsylvania, Philadelphia, Pennsylvania, United States; 2Center for Nanophotonics, AMOLF, Amsterdam, Netherlands; 3Electrical and Computer Engineering, University of Texas at Austin, Austin, Texas, United States; 4Physics, University of Pennsylvania, Philadelphia, Pennsylvania, United States; 5Singh Center of Nanotechnology, University of Pennsylvania, Philadelphia, Pennsylvania, United States.

Quantum emitters such as the diamond nitrogen-vacancy (NV) center are the basis for a wide range of quantum technologies. However, refraction and reflections at material interfaces impede photon collection, and the emitters’ atomic scale necessitates the use of bulky, intricate optical measurement setups that prevent packaging of quantum devices. To overcome these limitations, we present the design and fabrication of a metasurface composed of nanoscale diamond pillars that acts as an immersion objective to collect and collimate the emission of an individual NV center [1]. Excellent agreement between metasurface design and performance can be seen by comparing the 3D finite-difference time-domain simulations and the measured transverse and axial profiles. Photoluminescence (PL) images are collected simultaneously from the metasurface and an oil-immersion objective focused through the backside of the high-pressure, high-temperature diamond substrate. Both images exhibit an NV center at the same lateral position, and the background-subtracted spectra of both paths clearly show the NV zero phonon line at ~10 nm to 100 nm depending on experimental conditions. UV-vis spectra clearly show the plasmonic peaks in good correspondence of SEM. TEM analyses show the boundary between the diamond-Ag nanostructures, which has some voids but generally shows columnar growth of diamond extending radially from the Ag nanoparticle core. Electromagnetic simulation results of the diamond-Ag composites also suggest possible air voids and graphite phases in the structure. The plasma-assisted Ag NPs embedded in diamond is a unique way to impart tunable optical properties to diamond thin films.

4:15 PM C3.04
Synthesis of Plasmonic Ag Nanostructures Embedded in Diamond Films with Tunable Optical Properties Shuo Li, Jason Bandy and Robert J. Hamers; Chemistry, University of Wisconsin-Madison, Madison, Wisconsin, United States.

Diamond is well known for its good mechanical robustness and extreme chemical stability. While diamond often adopts different colors due to defects and/or specific impurities introduced during growth, the integration of plasmonic nanoscale diamond into diamond provide an alternative approach to alter diamond’s color. Nanosized transition metals such as Ag and Au exhibit size- and shape-dependent plasmonic features in the visible region of the spectrum. Here we demonstrate that Ag nanoparticles can be embedded within diamond films by a three-step process: (1) a very thin film of Ag is deposited onto a diamond surface, (2) the Ag film is dewetted into individual nanoparticles, and (3) a second diamond film is grown to encapsulate the Ag nanoparticles. By growing the diamond-Ag-diamond films on quartz substrates, the plasmonic properties of the nanoparticle films can be characterized via transmission optical spectroscopy, as well as visually through the distinct coloration of the diamond films. Cross-sectional SEM of fractured diamond-Ag-diamond structures clearly shows individual nanoparticles with sizes ranging from ~10 nm to 100 nm depending on experimental conditions. UV-vis spectra clearly show the plasmonic peaks in good correspondence of SEM. TEM analyses show the boundary between the diamond-Ag nanostructures, which has some voids but generally shows columnar growth of diamond extending radially from the Ag nanoparticle cores. Electromagnetic simulation results of the diamond-Ag composites also suggest possible air voids and graphite phases in the structure. The plasma-assisted Ag NPs embedded in diamond is a unique way to impart tunable optical properties to diamond thin films.

4:45 PM C3.06
CVD Growth and Characterization of NV Center Probes for Low Temperature Nanoscale Magnetic Imaging Simon A. Meynell, Alec Jenkins, Claire A. McLellan, Susanne Baumann-Venzin, Matthew Pelliccione, Jeff Cady, Preeti Ovartchalyapong, Christopher Reetz and Ania Jayich; Physics, University of California, Santa Barbara, Goleta, California, United States.

The nitrogen vacancy (NV) center in diamond is a highly sensitive atomic defect that can be used to sense sub-microTesla magnetic fields with nanometer-scale resolution. The NV center is a promising candidate for quantum sensing over a broad range of temperatures. In fact, an imaging technique that utilizes a single NV center in a scanning probe geometry has been used to image magnetic order in systems such as vortices in superconductors and magnetic solitons known as skyrmions at both room and low temperature. An important limitation to increasing the sensitivity and spatial resolution of such an NV-based sensor is the quantum decoherence induced by the diamond surface. As the exact origins of this decoherence are presently not well understood, we explore chemical vapor deposition diamond growth techniques with nitrogen delta-doping and NV creation methods which allows us to create samples that are limited only by the surface. These techniques give us the ability to understand the specific decoherence mechanisms with the hopes of eventually surmounting them and approaching the magnetic and spatial resolution necessary to ultimately image a single nuclear spin.

EP3: Innovation and Entrepreneurship Session III
Session Chair: Jeffrey T. Glass
Wednesday Afternoon, May 23, 2018
Room: Doyle/Rees

ICDAT was conceived in my mind some 20 years ago while I was wondering with my father from one academic conference to another. Hearing all the excellent qualities of synthetic diamond I couldn’t help asking myself: If CVD diamond is so useful why isn’t it widely used? ICDAT was founded in 2014. Early days setting up, the biggest challenges were to establish a highly sophisticated infrastructure and recruit multi domains global matter experts. Luckily fund raising was lesser a concern due to family and friend network believing in my dream. Once setup, the initial barrier was to create a focal point and to prioritize applications to generate income and create a viable working business. Analyzing the market, we noticed the “Gorilla” in the marketplace selling diamond material slabs letting the customer decide how to integrate it. This left not much room for competition due to lack of production capabilities and financial backing. We had to find other global partners to have a significant footprint. However, once we started to talk with potential customers we found out that without proper integration, they were receiving only a small portion of the CVD diamond benefits – this was our opportunity! The realization that material creation was an important but still know-how. Our claim to fame is material matching and integration. A slim slice of diamond integrated correctly creates a line of premium products to our
customer. This revelation also led to our business model of partnerships and revenue sharing. Beginning with scanning the field of shining opportunities due to the wide spread industrial options the first stop on the way to glory was reaping the low-lying fruit of the uprising multi-billion-dollar lab grown GEM stone industry. Combining forces with the largest diamond trade body in the Israeli diamond exchange – slowly converting to the next generation of high profit and turnover. This market is supply limited and has a window of opportunity slowly closing on small scale production players. The first necessity was to create a strong branding based on our enterprises relative advantages opening the existing north America market to new horizons. At this point, once we got basic cash flow we can afford going to the real passion and meet the challenge of the industrial world led by microelectronics uprising of high power and frequency applications needing diamond for thermal management. This is done with government support and defense partners to prove the concept and extreme added value. Other preliminary initiatives with global partners are being developed with Medical Equipment manufacturer and Machining tools leader for composite materials. My personal lessons so far: Dare to dream, plan your dream and partner the leaders.
In this paper it is presented the synthesis, characterization and reduction of graphene oxide (GO) for its future application in hybrid or organic solar cells. The GO was prepared by variations of the Tour method [2], we added a different protective agent (HBO₂) that the commonly has been used in the method of Tour (H₃PO₄) and we reduce the oxidation time. The GO’s was synthesized by the oxidation of natural graphite powder (~45 μm with purity of ~85 % wt) obtained from Mina de Sahuaripa (Sonora, México) and procedure is described as follows: for oxidation stage, a mixture of concentrated sulfuric acid and boric acid (H₂SO₄/H₃BO₃) was added to a mixture of graphite powder and potassium permanganate (KMnO₄) producing a slight exotherm. The reaction was stirred for 30-90 min to 20-30 °C and then was heated to 40-55°C and stirred for 1-2 h. For exfoliation stage, deionized (DI) water was added to the suspension and then was heated to 80-90°C and stirred for 15-45 min. The reaction was then finished by adding hydrogen peroxide (H₂O₂ 50%). The resulting product has a brown/yellowish color and was separated by centrifugation from the solution. The resulting GO powders were washed 3-5 times with diluted HCl (20%) and DI water to remove the remnant Mn ions and acid respectively; for each wash, the mixture was centrifuged (6000 rpm for 20-40 min) and the supernatant decanted away. The solid obtained was dried overnight to 50-60°C, obtaining 30-40 mg of product. For reduction stage [3], 100 mg of GO was suspended in DI water and sonicated for 1-2 h, yielding an aqueous GO dispersion. This dispersion was treated with ascorbic acid (30-60 mM) and stirred for 15-24 h to 50-70°C under reflux. The resulting product has a dark color and was separated by centrifugation from the solution. The resulting GO powders were washed 3-4 times with DI water to remove the remnant acids; for each wash the mixture was centrifuged (6000 rpm for 40-60 min) and the supernatant decanted away. The solid obtained was dried overnight to 50-60°C, obtaining 50-60 mg of product. To study the contribution of the reaction conditions to the chemical composition, presence/quantity of functional groups, exfoliation level, number of layers, oxidation and reduction degree, the samples were characterized by different techniques such as UV-Visible spectroscopy, X-ray diffraction (XRD), Scanning Electron Microscopy (SEM), Transmission Electron Microscopy (TEM) and Energy Dispersive X-ray spectroscopy (EDS) [4]. The results of XRD, EDS and UV-Vis reveal that the oxygenated groups that were present have been widely removed, this can be seen reflected in the atomic ratio C/O of rGO (3.7), it increase close to 70% with respect to the GO (1.3), so that almost 50% of the oxygenated groups were removed, but the challenge is remove completely the oxygenated groups remaining and can it apply in photovoltaic solar cells. The designed synthesis strategy was to looking for a simple, easily controlled and an alternative approach for large scale production of graphene oxide (GO) for solar cell applications. This method decreases time of reaction around of 70% than the original Tour method, with the same quality and yields of graphene oxide sheets.

In recent years, nanomaterial-based strategies have emerged as attractive approaches in combating hematological-related diseases, such as thrombosis and malaria. With their unique physicochemical properties and biocompatibility, graphene and its related derivatives, specifically graphene oxide (GO), have been increasingly explored for this purpose. Here, we assess the nano-bio interactions between GO and blood-related entities, such as plasma proteins, blood cells, and malaria parasites, to elucidate the biophysicochemical activity of GO for hematological applications. We first investigate numerous facets of the GO-protein interactions, particularly, protein adsorption, equilibrium binding, and conformational stability. We observe that GO possesses a high loading capacity and affinity for the major blood plasma proteins, including albumin, globulin, and fibrinogen. Also, we note that these nano-bio interactions are protein-specific and may be significantly influenced by the lateral size distribution and concentration of GO. On the basis of the robust biomolecule adsorption on GO and the size- and concentration-dependent nano-bio interactions, we rationally functionalize GO and probe the antithrombotic and antimalarial properties of different GO nanomaterials in order to evaluate their potential in combating hematological disorders. We observe that functionalized GO exhibits antithrombogenic characteristic while pristine GO, regardless of size distribution and concentration, inherently possesses antimalarial activity by inhibiting the invasion of malaria parasites on red blood cells and delaying the maturation of these parasites. We anticipate that this study will offer a broad perspective on the GO-blood interactions and potentially facilitate further exploration into the development of nanotechnology-based strategies for hematological and other biological applications.
Graphene oxide (GO) is obtained by oxidizing graphite powder using modified Hummers' method. It has completely different properties comparing to the graphite powder – it is very hydrophilic and has low electric conductivity. Due to many functional groups present in GO it shows high absorption of the infrared (IR) radiation, especially in the mid-IR region. GO can be reduced by thermal or chemical treatment. Depending on the reduction method reduced graphene oxide (rGO) with controlled content of oxygen can be obtained. After reduction GO becomes more similar to graphite – it is hydrophobic and has good electrical conductivity. Depending on the content of functional groups rGO exhibits different IR shielding properties. Based on the properties of these materials, new polymer composites with polyvinyl alcohol as the matrix were proposed for IR shielding applications. In this work, graphene oxide was reduced by different methods. Thermal (heating in air at 220°C and in nitrogen at 1000°C) and chemical (reduction with hydrazine hydrochloride and L-ascorbic acid) treatments were proposed. The obtained materials were analyzed with FT-IR spectroscopy, elemental analysis and thermogravimetric analysis (TGA) in order to evaluate the reduction degree. The polymer composites with the graphene fillers were prepared by a solution mixing method. Various amounts of GO and rGO (from 0.05 wt% to 5 wt%) were added to the polymers and the properties of the obtained materials were analyzed. The composites were characterized with FT-IR spectroscopy (in attenuated total reflectance – ATR and in transmission mode), optical microscopy, and TGA. Additionally, thermal insulation measurements were performed for the obtained materials. The results show that the properties of the graphene oxide filler strongly influence the infrared shielding properties of the obtained polymer composites. The best IR shielding properties were obtained for the composites where rGO with the lowest oxygen content was used.

Graphene-oxides are functionalized with nitrogen using different N-based precursors and hence studied their electronic structure and magnetic properties. The electronic structure of nitrogen functionalized graphene oxide were investigated using C, O and N 1s X-ray photoelectron spectroscopy (XPS), ultraviolet photoemission spectroscopy (UPS), and their magnetic behaviours are correlated with SQUID-measured magnetization M-H loops. The XPS results indicates that the different nitrogen-based precursors functionalized graphene oxide forms different N-bonding and changes their electronic structure and bonding properties. These change of electronic structure change the magnetic properties drastically. Work function and valence band maximum were estimated from the UPS measurements and are correlated with electronic behaviours of Graphene-oxide. Magnetic studies show that the magnetization is changes due to conversion due to formation of different nitrogen bonded carbon and oxygen. The change in magnetization in graphene-oxide on nitrogen functionalization using different precursors are another routes to tailor the magnetic properties of graphene-oxide for magnetic device applications.

Graphene Oxide with Controlled Content of Oxygen Groups as a Filler for Polymer Composites Used for Infrared Radiation Shielding

Marta Mazurkiewicz-Pawlicka, Makysmilian Nowak, Artur Malolepszy and Leszek Stobinski; Faculty of Chemical and Process Engineering, Warsaw University of Technology, Warsaw, Poland.

Effective heat spreading within a GaN-on-diamond wafer does not solely depend on thermal conductivity of Chemical Vapor Deposition (CVD) diamond, but also the effective thermal boundary resistance \( TBR \) at the GaN/diamond interface. \( TBR \) is a result of phonon mismatch between materials which includes the dielectric adhesion layer used for diamond seeding, and the defective transition region at the dielectric layer/diamond interface, also referred as the nucleation layer, or nano crystalline diamond (NCD) layer. It has been reported that the contribution to the thermal resistance by dielectric adhesion layers is approximately 80 % of the \( TBR \). Moreover, it has also been reported that \( TBR \) is proportional to the thickness of the dielectric adhesion layer. Therefore, the thinnest possible dielectric adhesion layer is desirable for efficient heat dissipation of GaN-on-diamond. One of the biggest challenges of growing diamond on GaN is the etching of the underlying III-Nitride layer due to the harsh CVD diamond growth environment. Therefore, it is necessary to reduce the etching of the protective adhesion layer to ensure a thinnest possible interface layer. Another impact of high temperature diamond growth on nitride semiconductor is excessive thermal stress which may affect the electrical properties of the underlying nitride semiconductor device. In this study, we have demonstrated in-situ SiNx grown by MOCVD at elevated temperature followed by polycrystalline diamond growth without adversely affecting the underlying nitride semiconductor layers. SiNx/GaN(cap)/AlGaN(barrier)/AlN(profile)/GaN(buffer) High Electron Mobility Transistor (HEMT) structures were grown using a custom built cold wall, shower head Metalorganic CVD (MOCVD) system on low-resistivity (40 Ω-m) Si (111) substrates. Using X-ray reflectometry (XRR) the thickness of the SiNx is determined to be ~45 nm, which was also confirmed by Transmission Electron Microscope (TEM) measurement. Very smooth and continuous surface morphology with a root mean square (RMS) roughness of 0.14 nm for 1 μm x1 μm scan area is observed using Atomic Force Microscopy (AFM). Subsequently, seeding of the wafer is performed by spin coating using nano diamond seed suspended DMSO mixed photosresist. Poly crystalline diamond was grown in a Hot Filament CVD (HFCVD) system using 2 % CH\(_4\) in H\(_2\) at 700-750 °C and a chamber pressure of 20.8 torr. Uniform coverage of the diamond is observed by Scanning Electron Microscopy (SEM). Grain size, measured by linear intercept method from SEM, was 950 ± 200 nm.HFCVD grown polycrystalline diamond on AlGaN/GaN HEMT structures is realized using MOCVD grown in-situ SiNx as a dielectric adhesion layer. The interface characteristics of the GaN-SiN-Diamond region, and the
thickness of SiN, after diamond growth, is evaluated by TEM. From TEM observations, in-situ MOCCVD SiN, grown at high temperature (~1000 °C) is found to be two times more resistant to etching of the underlying III-Nitride film during HFCVD diamond deposition than Plasma Enhanced CVD (PECVD) grown SiN. High resolution X-ray Diffraction (HRXRD) reciprocal space mapping (RSM) was performed around both GaN asymmetric (1 1 4) and symmetric plane (0 0 2) to find the stress and composition of the constituent layers before and after the diamond growth. Ultraviolet Raman spectroscopy based stress measurement of the GaN layer was performed before and after the diamond growth. XRD and Raman stress measurements indicated a compressive stress increase of ~0.3 GPa in GaN due to diamond growth. Having a thin, high etch resistant in-situ SiNx as dielectric adhesion layer, with reduced nucleation layer thickness as observed in TEM, this GaN/SiNx/Diamond interface is expected to have reduced TBR.

9:15 AM B4.03
Fabrication of Diamond Field-Effect Transistors on High-Quality Heteroepitaxial Diamond Wafer Using Microneedle Technology

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Diamond semiconductor is expected to be high-power and high-efficient devices owing to its unexceptional physical properties such as high breakdown field strength, high carrier mobility, and highest thermal conductivity. By using NO2 hole doping and low temperature-deposited Al2O3 passivation technologies we achieved, diamond FETs operate stably and reproducibly1. Nevertheless, diamond wide wafers remain an issue. In this work, we demonstrate the operation of diamond FETs on high-quality heteroepitaxial diamond wafers. First, (001) heteroepitaxial diamonds (8x8mm2) were grown on Ir-deposited MgO substrates. Then, the micropattern was formed by Ni deposition and annealing2. Next, epitaxial overgrowth was performed on it and dislocation density was drastically reduced. Microneedles were made on the surface and a diamond bulk layer was grown on it. By using microneedle technology2, the diamond bulk was separated very smoothly during the cooling. Then, both faces were mechanically polished, and the surface underwent chemical-mechanical polishing. The FWHM of (004) rocking curve was as low as 0.07° and the curvature was 0.29 m. These values suggest high-quality heteroepitaxial diamond. Moreover, homoepitaxial diamond was grown on it by CVD. Diamond field-effect transistors were fabricated using NO2 hole doping and low temperature-deposited Al2O3 gate-oxide and passivation layers2 on the heteroepitaxial diamond. The DC output characteristics of diamond FETs with a gate length of 3 um on heteroepitaxial diamond. The drain current at a gate voltage of ~4V reached 91 mA/mm. Its drain current value were at the same level as for that of a conventional homoepitaxial single-crystal layer. In conclusion, we have demonstrated diamond FETs on high-quality heteroepitaxial diamond. The performance of these FETs is as efficient as that on the conventional homoepitaxial diamond layer. The characteristics are expected to improve by optimizing the dimension and condition. References 1. M. Kasu, Jpn. J. Appl. Phys. 56 (2017) 01AA01. 2. H. Aida, S. –W. Kim, K. Ikijiri, Y. Kawamata, A. Sawabe, et al. Appl. Phys. Express 9 (2016) 035504.

9:30 AM B4.04
Electrical Contact Considerations for Diamond Electronics

Franz A. Koeck, Manuneet Kaur and Robert J. Nemanich; Arizona State University, Tempe, Arizona, United States.

The demonstration of diamond devices has substantiated the superior capability of diamond in high power electronics that relied on the preparation of p-type and n-type diamond through boron and phosphorus doping, respectively, and the growth of high purity intrinsic diamond. Practical devices require suitable electrical contacts and their advancement is of ongoing interest. Electrical contacts to p-type diamond are readily achieved with low contact resistance of ~10-5 Ω cm2 reported. [1] Equivalent developments for n-type diamond were challenged by difficulties in the growth of highly P-doped diamond particularly on (100) oriented surfaces where elaborate micro-structuring processes to form (111) facets were suggested. [2, 3] We present an approach for electrical contacts to homoepitaxial, phosphorus doped, n-type, diamond that utilizes an interfacial layer of highly nitrogen doped, nanostructured carbon grown by plasma enhanced CVD (PECVD). This contact strategy was realized in a pin diamond diode for electron source applications. The pin-nano-carbon structure was prepared on HPHT type Iib (111) oriented substrates with intrinsic, n-type, and nano-carbon layer grown in dedicated PECVD systems. The nanostructured nitrogen doped carbon layer was synthesized with a process gas mixture of nitrogen/methane/argon/hydrogen and flow rates of 1000sccm/20sccm/10 cccm/5scm, respectively. A growth rate of ~1μm/hour was achieved using a microwave power of 900W and a chamber pressure of 20Torr with the growth temperature of ~900°C controlled by a substrate heater. Diodes from this pin-nano-carbon structure were prepared by lithography utilizing an aluminum hard mask to etch the 200μm diameter mesa contacted by Ti/Pt/Au metallurgy on the backside of the p-type substrate and top of the nano-carbon layer. The final device was processed in a hydrogen plasma for 5min at a temperature of ~850°C to induce negative electron affinity properties for electron emission. Electric characterization of the diodes commenced in vacuum after annealing at ~600°C for 15min. Observation of exciton light emission indicated bipolar transport where at a forward bias of 14V a current of 0.1A was measured and at 17V its increase to 0.5A corresponded to ~1500A/cm2. Compared to conventional pin diodes, the introduction of the nano-carbon layer enhanced the diode and electron emission current by more than an order of magnitude. Light emission and diode operation at temperatures >750°C indicated superior stability of the electrical contact. The n-type layer was characterized by SIMS communicating a phosphorus incorporation of ~2x1016/cm3 and the nano-carbon layer a nitrogen incorporation of ~5x1017/cm3. Addressing contact limitations to n-type diamond through the growth of moderately P-doped epitayers and highly nitrogen doped nano-carbon layers could provide a preferential approach for electronic devices and we will discuss its viability extended to (100) surfaces. This research was funded by the Department of Energy under grant #DE00014-1713002. [1] Ohmic contacts on p-type homoepitaxial diamond and their thermal stability, Yigang Chen, Masahiko Ogura, Satoshi Yamasaki and Hideyo Okushi, Semiconductor. Sci. Technol. 20 (2005) 860–863 [2] Selective Growth of Buried n+ Diamond on (001) Phosphorus-Doped n-Type Diamond Film, Hiromitsu Kato, Toshiharu Makino, Masahiko Ogura, Norio Tokuda, Hideyo Okushi, and Satoshi Yamasaki, Applied Physics Express 2 (2009) 055502 [3] New Process for Electrical Contacts on (100) N-Type Diamond, Nepli Temahului, Remi Gillet, Vincent Sallet, Francois Jomard, Ekaterina Chikoidze, Yves Dumont, Marie-Amandine Pinault-Thaury, and Julien Barjon, Phys. Status Solidi A 2017, 214, 1700466.

9:45 AM B4.05
Diamond Radiation Detectors for Proton Therapy-Lifetime and Spatial Uniformity

Mengnan Zou1, Tianyi Zhou1, James Distel2, Jen Mengnan Zou; 1 Stony Brook University, New York, United States; 2Los Alamos National Laboratory, Los Alamos, New Mexico, United States; 3Case Western Reserve University, Cleveland, Ohio, United States; 4Brookhaven National Laboratory, Upton, New York, United States.

The most common dosimeters for particle therapy are gas filled ion chambers, which have issues with varied deviation correction according to radiation conditions and inconvenient installation due to their large-volume. One alternative is to construct compact devices from diamond, which is known for its radiation hardness, with high spatial and temporal resolution. To ensure the reliability of dose measurements, tests of the lifetime and spatial uniformity of diamond detectors were performed. We have irradiated several diamond detectors with the high flux 800MeV proton beam at LANSCE (Los Alamos National Laboratory) and the ion beam induced current (IBIC) was real-time monitored for lifetime measurement. Spatial uniformity was confirmed by response maps of irradiated diamond detectors using small non-destructive X-ray beams. During the proton irradiation, an exponential decay in detector response was observed. This was explored further by X-ray beam induced current (XBIC) measurement and SRIM simulations, which reveal that the carbon vacancies introduced from displacement effect act as hole trap centers in the detector. When the carbon vacancy is damaged from displacement effect, the carbon vacancy becomes electrically active and contributes to the detector signal. The detector signal is observed to decrease exponentially over time, which is known as “carbon damage”. During the proton irradiation, an exponential decay in detector response was observed. This was explored further by X-ray beam induced current (XBIC) measurement and SRIM simulations, which reveal that the carbon vacancies introduced from displacement effect act as hole trap centers in the detector. When the carbon vacancy is damaged from displacement effect, the carbon vacancy becomes electrically active and contributes to the detector signal. The detector signal is observed to decrease exponentially over time, which is known as “carbon damage”. The detector signal is observed to decrease exponentially over time, which is known as “carbon damage”.

10:00 AM BREAK
Anwar Siddique1, Jonathan Anderson1, Mohammad Nazari1, Mark Holtz1, 2

mm above the substrate resulting in a surface temperature of 700-720 oC reactor designed for 100 mm wafers. Hot tungsten filaments were placed 6

Diamond nanoparticles developed and optimized on Si substrates, first. Diamond nanoparticles semiconductor. A selective deposition process of CVD diamond was necessary to minimize damage to the GaN and control the selectivity of diamond when growing on nitride semiconductors such as GaN and AlN. In this study, we have demonstrated successful selective area deposition of CVD diamond on GaN and AlN with a lateral resolution as small as 5 µm and without any significant surface damage to the underlying nitride semiconductor. A selective deposition process of CVD diamond was developed and optimized on Si substrates, first. Diamond nanoparticles suspended in dimethyl sulfoxide were mixed with photoresist, and then standard photolithography techniques were employed to pattern a 100 mm Si wafer. Reactive ion etching was performed afterward to increase selectivity. Diamond deposition was carried out in a hot filament CVD reactor designed for 100 mm wafers. Hot tungsten filaments were placed 6 mm above the substrate resulting in a surface temperature of 700-720 °C during diamond deposition. Scanning electron microscopy (SEM) images indicate excellent selectivity and cross wafer uniformity. Ultraviolet micro-Raman spectroscopy indicates the presence of diamond with a small non-diamond carbon (NDC) percentage in the deposited films. The selective seeding technique developed for Si was then used to deposit CVD diamond on metal organic CVD (MOCVD) grown GaN and AlN. Initially, significant etching of the nitride semiconductor was observed by SEM and the selectivity of the diamond was poor. Experiments were conducted that evaluated the impact of the methane concentration during CVD diamond deposition. The methane concentration was varied between 1.5% and 3% to observe changes in the diamond growth rate and its effect on etching of underlying layers. Higher methane concentrations resulted in higher growth rates, quicker surface coverage, and reduced surface etching, however, it also increased the amount of NDC. Based on growth rate, surface etching and NDC data, diamond deposition was performed with 3% methane for its relatively higher growth rate and moderate NDC percentage. However, under these conditions, significant etching of the nitride semiconductor was observed by SEM images and selectivity of diamond was still poor. To mitigate this effect, a thin layer of plasma enhanced CVD (PECVD) SiNx was deposited on the nitride semiconductors before selective seeding and diamond deposition. This resulted in excellent selectivity of the CVD diamond with feature sizes as small as 5 µm across a 100mm wafer. The reduction in damage was confirmed by comparison of X-ray diffraction and Raman spectroscopy data collected before and after diamond deposition, and by SEM images of the final structures. In this presentation, a detailed discussion on the processing of the wafers with characterization results at different stages of the research will be discussed.

Polycrystalline diamond films have been and are investigated due to their unique combination of properties such as high wear resistance, highest hardness relative to any other film, lowest friction coefficient compared with metal and ceramic coatings, chemical inertness, excellent thermal conductivity (~1500 W/K m, close to that of single crystal diamond ~2100 W/K m) perpendicular to the film surface and in the film plane for microcrystalline diamond (~1 µm grain size), tunable electronic properties, and biocompatible properties. This presentation will focus on describing the results from systematic polycrystalline film synthesis research and system development for Bias Enhancement Nucleation and Bias Enhanced Growth (BEN-BEG) to growth ultrananocrystalline diamond (UNCD) films on medium size areas (100 mm diameter) Silicon wafers coated with 40 nm thick Tungsten film to induce denser films. The BEN-BEG process to growth diamond films eliminates the conventional chemical seeding process used today. The studies discussed are focused on understanding the BEN mechanism by varying the BEN time between 0.5 and 2.5 hrs. Following the BEN process, films were grown for 2.0 hrs without bias. A H2 (49%)/CH4 (2%)/Ar (49%) gas mixture was flown in the HFCVD chamber previously evacuated to 2 – 3 x 10-6 Torr. The substrate surface was heated to 650-700 °C via a combination of heat provided by an underlying substrate heater and radiation from an array of ten parallel filaments heated by electronic current to ~ 2300 °C. An electric field was created between the films (bias positively) and the substrate (biased negatively) to attract positively charged CHx+, Ar+, and H+ ions created in plasma in the substrate surface, to induce the BEN and growth of the UNCD films. Computer simulations and experiments showed that electric fields concentrated on the substrate edges initiating the film growth, which propagated towards the center of the substrate, as the insulating UNCD film growth induced electric field displacement towards the uncoated area to finally induce a uniform film growth across the substrate. Evidence of very homogeneous nucleation by BEN appears at 2.0 and 2.5 hrs. However, at 2.5 hrs of BEN, signs of etching of the UNCD film is observed, probably due to long exposure ion bombardment-induced sputtering or ion bombardment-enhanced chemical reaction between H atoms and C atoms on the UNCD film surface, inducing formation of volatile CHx molecules, or a combination of both processes. According to the studies made until now, BEN for 2.0 hrs appears to be the optimum process to grow very dense film across 100 diameter wafer. HRTEM studies show that 2.0 hrs of BEN induce the growth of tungsten carbide layer with crystals orientation (001 and 101), which induce the formation of diamond grains (111), followed by change of diamond grain orientation to (220) and (311). These results show that the BEN process could be used to tailor orientation of UNCD film grains. In addition, it was demonstrated that the HFCVD BEN-BEG process can be used to grow diamond films selectively on electrically conductive patterns produced on insulating substrate surfaces, providing a pathway for fabrication of diamond based devices on SiO2/Si substrates.

High Resolution Selective Area Deposition of Hot Filament Chemical Vapor Deposited Diamond Films on Si, GaN, and AlN

10:30 AM A3.01

10:45 AM A3.02

Fundamentals of Bias Enhance Nucleation/Bias Enhanced Growth of Ultrananocrystalline Diamond Films on Tungsten/Silicon Substrates by Hot Filament CVD for Large Area Application Jesus J. Alcantar-Peña1, 2, Elida de Obaldia1, 3, Jorge Montes1, 3, Karam Kang1, Maria J. Arellano-Jimenez1, Jose E. Ortega Aguilar1, Dainet Berman-Mendoza1, Miguel J. Yacaman4 and Orlando Auciello5; 1Materials Science and Engineering, The University of Texas at Dallas, Richardson, Texas, United States; 2Departamento de Investigación en Física, Universidad de Sonora, Hermosillo, Mexico; 3Facultad de Ciencias y Tecnología, Universidad Tecnológica de Panamá, Panama City, Panama; 4Department of Physics and Astronomy, University of Texas at San Antonio, San Antonio, Texas, United States.
uses a nanosecond-pulsed visible laser to nucleate and propagate a mechanical cleave in a chosen (111) crystal plane, resulting in faces as large as 3.0 mm × 0.3 mm with atomically flat surfaces, negligible miscut angles, and near zero k appendage and loss. We will discuss the underlying physical mechanisms of the process along with potential improvements that will enable the production of millimeter-scale (111)-faceted single-crystal diamond plates for a variety of emerging devices and applications. The (111) crystal plane is the hardest face, making it more resilient to damage and desirable for industrial scale diamond cutting tools. Surface roughness is strongest when the optical polarization axis is aligned along [111]. For this reason, integrating on-chip Raman lasers requires precise crystallographic orientation of the diamond layer to maximize the laser efficiency. High-power electronic devices also benefit from (111) faces, which provide improved donor incorporation efficiency and correspondingly higher mobility. Finally, point defects in SCD that are used as single-photon sources and spin qubits, such as the nitrogen-vacancy and silicon-vacancy centers, have a symmetry axis aligned along [111] directions. Thus, a (I11) face maximizes the interaction with normally-incident light fields and optimizes the photon collection efficiency from these emitters, which is critically important for light-matter quantum interfaces and high-sensitivity magnetometry. In contrast to traditional mechanical cleaving of diamond, laser-nucleated cleaving (LNC) provides the opportunity for precise positioning and control of the cleave propagation. Since k appendage is minimized, LNC may be desirable for faceting diamond gems or cutting tools. Additionally, the LNC process has potential for eliminating plate wedge, which adversely affects diamond photonic devices. LNC will ultimately prove useful for fabricating seed crystals required for improving CVD growth of customized (111)-oriented samples, and for generating (111)-faceted SCD substrates for diamond electronics, photonics, and quantum technologies. [1] S. M. Parks, R. R. Grote, D. A. Hopper, and L. C. Bassett, "Fabrication of (111)-Facet Single-Crystal Diamond Plates by Laser Nucleated Cleaving," arXiv:1712.03882 [cond-mat.mtrl-sci].

11:15 AM A3.04 Fundamentals of Processes Involved in the Synthesis of Electrically Conductive Ultrananocrystalline Diamond Films with Grain Boundary Inserted Nitrogen Atoms Grown by Hot Filament Chemical Vapor Deposition Gerardo Garibaldi1, 2, Jesus J. Alcantar- Peña1, Pablo A. Tirado1, 4, Amanda Gorby, Elida de Obaldía1 and Orlando Auciello1, 2Materials Science and Engineering and Bioengineering, The University of Texas at Dallas, Richardson, Texas, United States; 3Departamento de Investigación en Física, Universidad de Sonora, Hermosillo, Mexico; 4Department of Bioengineering, University of Texas Dallas, Richardson, Texas, United States.

A discussion will be presented on systematic studies focused on investigating the fundamentals of processes involved in the growth of electrically conductive grain-boundary incorporated ultrananocrystalline diamond films named N-UNCD, grown using the Hot Filament Chemical Vapor Deposition (HFCVD) technique. Parameters investigated to develop an optimum process to achieve the highest electrical conductivity in N-UNCD films include a) the flow rate (critical) of each gas in the mixture of gases used to grow the films, b) the filament-to-substrate distance, c) the temperature of the filament (set for all grows at 2300 °C), d) the temperature of the substrate surface (600-650 °C), and e) the substrate material (high conductivity Si and insulating SiO2 (300 nm thick)/Si substrates). Insulating UNCD films were grown first, as control for comparison, using a mixture of Ar (10 sccm)/CH4 (2 sccm)/H2 (20 sccm), which produced films with high sheet resistance (MΩ/sq.), as measured by the four-point probe method. Subsequently, the first N-UNCD film was grown with Ar (10 sccm)/CH4 (2 sccm)/H2 (20 sccm) and N2 (1 sccm) with a filament-to-substrate distance of 10 mm. The UNCD film growth was monitored using optical emission spectroscopy, which revealed uniform film thickness (~250 nm) across 100 mm diameter wafers. Finally, Hall effect measurements were performed to determine the type of electrical behavior (p or n type) in the N-UNCD films. The high conductivity N-UNCD films will be tested integrated on different media, seeking to identify their degree of efficiency for key technological applications as corrosion resistant coatings for encapsulation of electrodes of Li-ion batteries to protect the base material from Li-induced degradation and for high efficiency photovoltaic cells.

11:30 AM A3.05 Boron Doping of Ultrananocrystalline Diamond Films on Silicon Substrates by Thermal Diffusion Pablo A. Tirado1, 2, Jesus J. Alcantar-Peña1, 2, Elida de Obaldía1, 3, Rafael García1 and Orlando Auciello1, 2, 4Departamento de Investigación en Física, Universidad de Sonora, Hermosillo, Mexico; 1Materials Science and Engineering, University of Texas Dallas, Richardson, Texas, United States; 2Facultad de Ciencia y Tecnología, Universidad Tecnológica de Panamá, República de Panamá, Panama; 3Department of Bioengineering, University of Texas Dallas, Richardson, Texas, United States.

The physics and applications of Ultrananocrystalline Diamond (UNCD) films are being investigated due to their unique combination of properties such as high wear resistance, highest hardness relative to any other film, lowest friction coefficient compared with metal and ceramic coatings, chemical inertness, negative electron affinity, low work function, and the high electrical conductivity for boron doped and nitrogen grain boundary incorporated diamond films. The combination of these properties make doped diamond films suitable for many applications like electrodes for water purification, thermionic and field emission devices, and high power electronic devices. Boron doping of UNCD films during growth has the drawback of Boron contamination of the chamber where the film is grown, which can only be used for the growth of B-doped diamond films. This presentation will focus on describing the results from research and development of a novel process for Boron doping large area UNCD films by thermal diffusion after growth, thus eliminating the problem of Boron contamination of the diamond film growth chamber. The research is focused on understanding the chemical, structural and electrical properties of the UNCD films before and after doping with Boron by thermal diffusion. The UNCD films were grown by Microwave Plasma Chemical Vapor Deposition (MPCVD) technique on (1 0 0) Silicon substrates. Afterwards, a 200-nm thick Boron containing film was deposited, as a B source, on the UNCD film’s surface via spin coating, using a commercial Spin on Dopant (SOD) solution (Boroflim 100®). A spinning speed of 3000 rpm and a process time of 20 seconds was used for depositing the SOD film on the UNCD film surface, followed by annealing in an atmospheric oven at 200 °C for 20 minutes in order to evaporate any excess solvent from the SOD film. The diffusion process was carried in a Jefirst 200 Rapid Thermal Processor (RTP) in a low oxygen atmosphere at 800 °C, 900 °C, and 1000 °C for 180s. Successive chamber evacuations and purges with 1500 sccm of N2 were performed to minimize O2 content in order to avoid the C-based UNCD film being etched by oxygen at the high temperatures needed for Boron diffusion. Once the diffusion process was over, the UNCD films were ultra-sonically cleaned with acetone, methanol and isopropanol in order to remove any remaining Spin on Dopant film from the surface. The boron doping and as deposited films were characterized by Raman, XRD, XPS and Hall effect measurements. Raman and XRD characterizations were done to confirm that there was no induced graphitization or damage in the films during the diffusion process, while XPS, and Hall effect characterizations were carried to confirm the boron doping and the change in electrical properties (sheet resistance, charge carrier concentration) during the diffusion process. This new process to produce B-doping of UNCD films can in principle be extended to NCD ad MCD films to explore the development of a new generation of diamond based electronics.
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